

RAA215300

High Performance 9-Channel PMIC Supporting DDR Memory, with Built-In Charger and RTC

The RAA215300 is a high-performance, low-cost 9-channel PMIC designed for 32-bit and 64-bit MCU and MPU applications. It supports DDR3, DDR3L, DDR4, and LPDDR4 memory power requirements. The internally compensated regulators, built-in Real-Time Clock (RTC), 32kHz crystal oscillator, and coin cell battery charger provide a highly integrated, small footprint power solution ideal for System-On-Module (SOM) applications. A spread spectrum feature provides an ease-of-use solution for noise-sensitive audio or RF applications.

The RAA215300 has six high-efficiency buck regulators and three LDOs to provide a complete power system. The internal device registers and EEPROM can configure and optimize the RAA215300 for different application requirements, for example, power sequences, output voltages, and switching frequencies. Dynamic Voltage Scaling (DVS) and Sleep modes are supported.

The RAA215300 is available in an 8x8mm, 0.5mm pitch thermally enhanced 56-lead QFN package and is specified for operation across a -40°C to 105°C ambient and -40°C to 125°C junction temperature range.

Features

- Input operating voltage range: 2.7V~5.5V
- 6 synchronous buck regulators (supporting 5A, 3.5A, 2x1.5A, 1A, 0.6A), with settable V_{OUT}
- 3 LDOs (supporting 2x300mA, 50mA), with bypass mode, and settable V_{OUT}
- Dedicated VTTREF for DDR memory
- Auto PFM/PWM, FPWM and ultrasonic modes, with selectable PWM f_{SW}
- Built-in 32kHz crystal oscillator (with bypass), RTC, and coin cell/supercapacitor battery charger
- DVS and sleep modes
- Internally compensated
- Spread spectrum
- I²C serial interface (up to 1MHz)
- Pb-free (RoHS compliant)

Applications

- MCU/MPU/SoC consumer and industrial power
- FPGA system power
- Building/factory automation system power

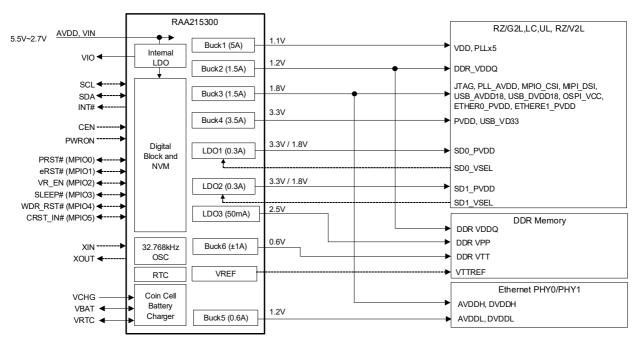


Figure 1. Typical Application Diagram - MPU Power

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1. Overview

1.1 Block Diagram

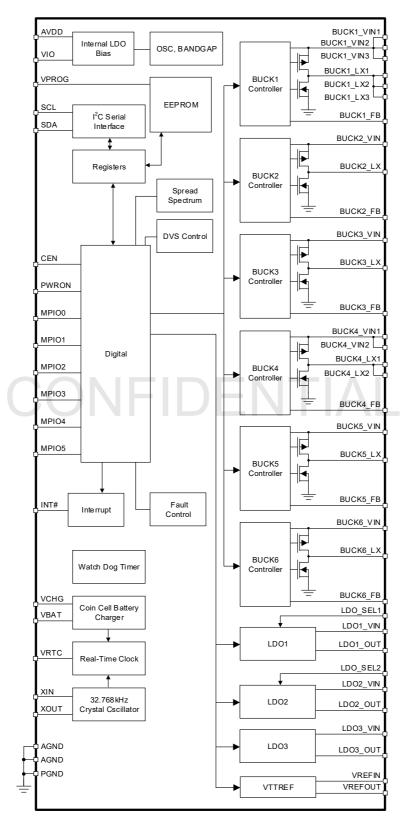
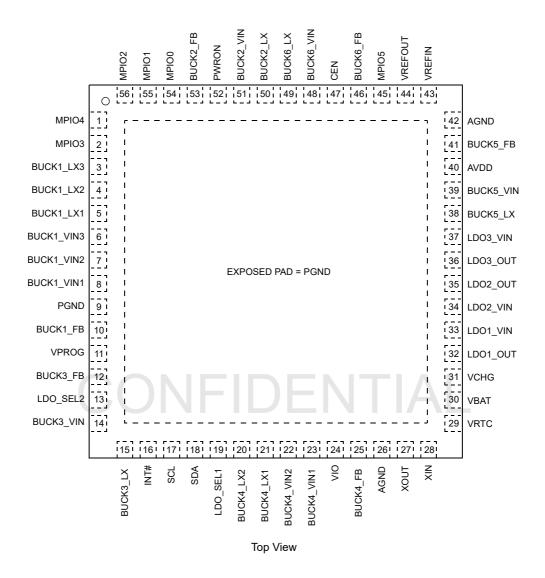


Figure 2. Block Diagram

2. Pin Information

2.1 Pin Assignments



2.2 Pin Descriptions

Pin Number	Pin Name	Туре	Description
1	MPIO4 ^[1]	Input/Output	Multiple general purpose input-output 4
2	MPIO3 ^[1]	Input/Output	Multiple general purpose input-output 3
3	BUCK1_LX3	Output	Buck1 switch node
4	BUCK1_LX2	Output	Buck1 switch node
5	BUCK1_LX1	Output	Buck1 switch node
6	BUCK1_VIN3 ^[2]	Power	Buck1 supply
7	BUCK1_VIN2 ^[2]	Power	Buck1 supply
8	BUCK1_VIN1 ^[2]	Power	Buck1 supply
9	PGND	Ground	Power ground

Pin Number	Pin Name	Туре	Description
10	BUCK1_FB	Input	Buck1 feedback
11	VPROG	Power	High voltage supply input for EEPROM programming. Connect to ground in typical application.
12	BUCK3_FB	Input	Buck3 feedback
13	LDO_SEL2	Input	Logic input. Select LDO2 output voltage.
14	BUCK3_VIN ^[2]	Power	Buck3 supply
15	BUCK3_LX	Output	Buck3 switch node
16	INT#	Output	Interrupt output, open-drain, active low. It can also be configured as clock signal output in Frequency Output (FOUT) mode of the RTC.
17	SCL	Input	I ² C serial clock
18	SDA	Input/Output	Bidirectional I ² C serial data
19	LDO_SEL1	Input	Logic input. Select LDO1 output voltage.
20	BUCK4_LX2	Output	Buck4 switch node
21	BUCK4_LX1	Output	Buck4 switch node
22	BUCK4_VIN2[2]	Power	Buck4 supply
23	BUCK4_VIN1[2]	Power	Buck4 supply
24	VIO	Output	Internal 1.8V LDO output
25	BUCK4_FB	Input	Buck4 feedback
26, 42	AGND	Ground	Analog and digital ground
27	XOUT	Output	Crystal oscillator output. Connect to ground if not used.
28	XIN	Input	Crystal oscillator input. Connect to ground if not used.
29	VRTC	Power	Real-time clock (RTC) power supply. An output that provides power to the RTC and is generated internally from the higher of VBAT and VCHG.
30	VBAT	Power	Charger output to coin cell battery or supercapacitor, or RTC input supply when running from coin cell battery or supercapacitor. If not used, connect to GND.
31	VCHG	Power	Input Supply for VIO LDO, Coin cell battery charger and RTC input power. AVDD, VCHG, and BUCKx_VINx must be the same voltage.
32	LDO1_OUT	Output	LDO1 output
33	LDO1_VIN	Power	LDO1 supply
34	LDO2_VIN	Power	LDO2 supply
35	LDO2_OUT	Output	LDO2 output
36	LDO3_OUT	Output	LDO3 output
37	LDO3_VIN	Power	LDO3 supply
38	BUCK5_LX	Output	Buck5 switch node
39	BUCK5_VIN ^[2]	Power	Buck5 supply
40	AVDD	Power	Analog and digital supply. AVDD, VCHG, and BUCKx_VINx must be the same voltage.
41	BUCK5_FB	Input	Buck5 feedback
43	VREFIN	Input	Input to VTTREF block. Note: Pin has a 1MΩ (typical) internal resistor to GND.



Pin Number	Pin Name	Туре	Description
44	VREFOUT	Output	Output from VTTREF block, with value equal to (VREFIN/2). Used as reference for VTT.
45	MPIO5 ^[1]	Input/Output	Configurable multiple purpose input-output 5
46	BUCK6_FB	Input	Buck6 feedback
47	CEN	Input	Chip enable, active high
48	BUCK6_VIN ^[2]	Power	Buck6 supply
49	BUCK6_LX	Output	Buck6 switch node
50	BUCK2_LX	Output	Buck2 switch node
51	BUCK2_VIN ^[2]	Power	Buck2 supply
52	PWRON	Input	Regulator output enable
53	BUCK2_FB	Input	Buck2 feedback
54	MPIO0 ^[1]	Input/Output	Configurable multiple purpose input-output 0
55	MPIO1 ^[1]	Input/Output	Configurable multiple purpose input-output 1
56	MPIO2 ^[1]	Input/Output	Configurable multiple purpose input-output 2
-	EPAD	Ground	Exposed thermal pad. Power ground. All regulator PGNDs are internally downbonded to the EPAD.

- 1. See Multi Purpose I/O for pin function mapping.
- 2. All buck supplies (BUCKx_VINx) = AVDD = VCHG.



3. Specifications

3.1 Absolute Maximum Ratings

CAUTION: Do not operate at or near the maximum ratings listed for extended periods of time. Exposure to such conditions can adversely impact product reliability and result in failures not covered by warranty.

Parameter	Minimum	Maximum	Unit				
Voltage (to PGND unless otherwise stated)							
BUCKx_VINx, AVDD, VCHG	-0.3	6	V				
VBAT	-0.3	6	V				
BUCKx_FB	-0.3	6	V				
BUCKx_LXx	-0.3	6	V				
BUCKx_LXx ^[1]		6.7	V				
AGND, PGND	-0.3	0.3	V				
VPROG	-0.3	24	V				
All other pins	-0.3	6	V				

^{1. ≤20}ns duration

3.2 ESD Ratings

ESD Model/Test	Rating	Unit
Human Body Model (Tested per JS-001-2017)	±2	kV
Charged Device Model (Tested per JS-002-2018)	±500	V
Latch-Up (Tested per JESD78E; Class 2, Level A)	100	mA

3.3 Thermal Information

Thermal Resistance (Typical)	θ _{JA} (°C/W) ^[1]	θ _{JC} (°C/W) ^[2]
56LD, 8x8mm QFN Package	23	0.7

θ_{JA} is measured in free air with the component mounted on a high-effective thermal conductivity test board with direct attach features. See TB379.

^{2.} For θ_{JC} , the case temperature location is the center of the exposed metal pad on the package underside.

Parameter	Minimum	Maximum	Unit
Maximum Junction Temperature (T _J)		+150	°C
Maximum Storage Temperature Range (T _S)	-65	+150	°C
Pb-Free Reflow Profile		see TB493	

3.4 Recommended Operation Conditions

Voltages referred to PGND unless otherwise stated.

Parameter	Minimum	Maximum	Unit
Ambient Operating Temperature Range (T _A)	-40	+105	°C
Operating Junction Temperature (T _J)		+125	°C
BUCKx_VINx, AVDD, VCHG	2.7	5.5	V
VBAT	1.8	5.5	V
MPIOx	-	5	V
CEN, PWRON	-	5	V
VPROG	0	23	V
SCL, SDA	0	3.3	V

3.5 Electrical Specifications

Parameter	Symbol	Test Conditions ^[1]	Min ^[2]	Тур	Max ^[2]	Unit		
Input Supply	nput Supply							
AVDD Input Operating Range	AVDD _{OP}	AVDD = VCHG = BUCKx_VINx	2.7	5	5.5	V		
BUCK Input Operating Range	BUCK _{OP}	BUCKx_VINx	2.7	5	5.5	V		
LDO Input Operating Range	LDO _{OP}	LDOx_VIN	2.7	3.3	5.5	V		
VCHG Input Operating Range	VCHG _{OP}	AVDD = VCHG = BUCKx_VINx	2.7	5	5.5	V		
VCHG Falling Slew Rate ^[3]	VCHG _{FALL}	To ensure POR operation of RTC do not exceed the maximum falling slew rate. AVDD = VCHG = BUCKx_VINx			5	V/ms		
	$AVDD_{UVLO_R}$	Rising threshold		2.3		V		
AVDD Undervoltage	AVDD _{UVLO_F}	Falling threshold		2.1		V		
Lockout Threshold	AVDD _{UVLO_HYS}	AVDD _{UVLO_HYS} = AVDD _{UVLO_R} ₋ AVDD _{UVLO_F}		200		mV		
AVDD Undervoltage		Falling AVDD, 2.7V setting		2.7				
Power Down	9	Falling AVDD, 3.0V setting		3.0		V		
Threshold		Falling AVDD, 4.25V setting		4.25				
AVDD Undervoltage Power Down Threshold Accuracy	AVDD _{UVPD_ACC}	Falling AVDD	-3		3	%		
AVDD Undervoltage Power Down Threshold Hysteresis	AVDD _{UVPD_HYS}	AVDD _{UVPD_HYS} = AVDD _{UVPD_R} ₋ AVDD _{UVPD_F}		100		mV		

Parameter	Symbol	Test Conditions ^[1]	Min ^[2]	Тур	Max ^[2]	Unit
AVDD UVPD Delay	AVDD _{UVPD_DLY}	Falling AVDD		100		μs
Operating Bias Curren	t		1	l	1	I
{SHUTDOWN} Supply Current	I _{SHDN_AVDD}	Current into AVDD, CEN = LOW, T _A = 25°C		<1	7	μA
{SHUTDOWN} Supply Current	I _{SHDN_VCHG}	Current into VCHG, VBAT < VCHG CEN = LOW, T _A = 25°C		400	950	nA
RTC Battery Supply Current	I _{BAT}	VBAT = 3V, AVDD = VCHG = 0V. RTC is enabled in 0x6C[6]. Internal oscillator is enabled in 0x07[6] with external crystal.		400		nA
		VBAT = 3V, Shipping mode (RTC is disabled in 0x6C[6])		120		
{STANDBY} Supply Current	I _{OP_STANDY}	Total input current. CEN = HIGH, AVDD > UVLO, PWRON = LOW. RTC off.		360	470	μΑ
{ACTIVE} Supply Current	I _{OP_ACTIVE}	Total input current. CEN = HIGH, AVDD > UVLO, PWRON = HIGH All bucks enabled, auto PFM/PWM mode, no load, not switching. All LDOs enabled, no load. RTC on. I ² C on and idle, MPIOx static.	IA	3.2	4.8	mA
RTC State Supply Current	lop_rtc	Total input current, VBAT. VBAT = 3.3V, BUCKx_VINx = AVDD = VCHG = 0V, RTC is enabled and clocking, FOUT is enabled at INT#			5	μА
VIO LDO						
VIO LDO Output Voltage	VIO _{OUT}	Not in dropout, no external loading	1.62	1.8	1.96	V
VIO LDO Current Capability	VIO _{IOUT_RNG}	Additional external loading ^[4]		20		mA
VIO LDO Current Limit	VIO _{ILIM}	VIO = 90% * VIO _{OUT}	24		41	mA
VIO Load Transient Response	VIO _{LOAD_TR}	Step: 0 to 20mA in 1µs Step: 20mA to 0 in 1µs	-3		3	%
VIO LDO Power-Good Rising Threshold	VIO _{PGOOD_Rise}	VIO rising. Percentage of VIO _{OUT}	-10	-5	-2	%
VIO LDO Power-Good Falling Threshold	VIO _{PGOOD_Fall}	VIO falling. Percentage of VIO _{OUT}	-15	-10	-7	%
VIO LDO Power-Good Threshold Hysteresis	VIO _{PGOOD_HYS}	VIO _{PGOOD_HYS} = VIO _{PGOOD_Rise} - VIO _{PGOOD_Fall}		5		%

Parameter	Symbol	Test Conditions ^[1]	Min ^[2]	Тур	Max ^[2]	Unit
EEPROM	l					
EEPROM Endurance	EE _{ENDR}	Programming cycles	1000			Cycles
Loading EEPROM Data to Registers at Power-On	t _{EE_LOAD}	AVDD valid. CEN = HIGH			10	ms
EEPROM Programming Cycle Time	t _{EE_WRITE}	Total time for writing customer banks		216	238	ms
BUCK1 (5A) Components as describ	ed in Recommended Ex	cternal Components. Additional application	on details in	Buck1.		
Buck1 Output Voltage Target Resolution	BK1 _{RES}			4		bits
Buck1 Output Voltage Range	BK1 _{OUT}	BUCK1_FB	0.8		1.5	V
Buck1 Output Voltage Step	BK1 _{STEP}	BUCK1_FB		50		mV
Buck1 Output Voltage DC Accuracy	BK1 _{ACC}	BUCK1_FB. PWM operation, I _{OUT} = 5mA, V _{OUT} = 1.1V	-1		1	%
Buck1 Output Voltage Ripple FPWM	BK1 _{RIP_FPWM}	I _{OUT} = 100mA, FPWM mode	IA	10		mVpp
Buck1 Maximum Output Current Capability ^[5]	BK1 _{IOUT_MAX}		5			А
Buck1 Output Load Regulation	BK1 _{LOAD_REG}	FPWM, VOUT = 1.1V, Over I _{OUT} = 100mA to 5A range		±0.1		%
Buck1 Output Line Regulation	BK1 _{LINE_REG}	FPWM, BUCK1_VINx = $4.5V \leftrightarrow 5.5V$, VOUT = $1.1V$, $I_{OUT} = BK1_{IOUT_MAX}$		±0.1		%
Buck1 Peak Efficiency	BK1 _{EFF}	Peak efficiency, L = default, BK1 _{FSW} set to default ^[6] , maximum V _{OUT}		92	-	%
		BUCK1_FB. Slow setting enabled	35	50	65	Ω
Buck1 Discharge Resistance	BK1 _{RDCHG}	BUCK1_FB. Medium setting enabled	26	37.5	49	Ω
		BUCK1_FB. Fast setting enabled	17.5	25	32.5	Ω
Buck1 High-Side MOSFET Current Limit	BK1 _{ILIM_HS}	PWM operation, sourcing (supplying)	6.1	7	7.7	А
Buck1 Low-Side	BK1 _{ILIM_LS}	PWM operation, sourcing (supplying)		7.5		_
MOSFET Current Limit	BK1 _{ILIMNEG}	FPWM mode, sinking (receiving)		-0.7		Α

Parameter	Symbol	Test Conditions ^[1]	Min ^[2]	Тур	Max ^[2]	Unit
			3.6	4.6	5.6	
Buck1 High-Side	DIZ4	Docietar cettable values [5]	4.4	5.4	6.4	,
Overcurrent Warning Threshold Range	BK1 _{IHC}	Register settable values ^[5]	4.7	5.7	6.7	A
			5.1	6.1	7.1	
Buck1 High-Side Overcurrent Warning Threshold Accuracy	BK1 _{IHC_ACC}	default BK1 _{IHC} setting	-1		+1	А
Buck1 PWM Switching Frequency	BK1 _{FSW}	FPWM mode, 1.11MHz (default) setting		1.11		MHz
Buck1 PWM Switching Frequency Accuracy	BK1 _{FSW_ACC}	FPWM mode, I _{OUT} = 0mA, default frequency	-10		+10	%
Buck1 Soft-Start Slew Rate Range	BK1 _{SS_SR_RNG}	BUCK1_FB	0.5	1	4	ms
Buck1 Shutdown Slew Rate Range	BK1 _{SHTDN} _ SR_RNG	BUCK1_FB	0.5	1	4	ms
Buck1 DVS Slew Rate Range	BK1 _{DVS_SR_RNG}	BUCK1_FB. Applies to both DVS up and down ramps.	2	8	16	mV/μs
Buck1 High-Side PMOS On-resistance	BK1 _{RDSON_HS}	BUCK1_VINx to BUCK1_LXx, I _{LX} = -150mA	IA	40		mΩ
Buck1 Low-Side NMOS On-Resistance	BK1 _{RDSON_LS}	BUCK1_LXx to PGND, I _{LX} = 150mA		28		mΩ
BUCK2 (1.5A) Components as describ	ed in Recommended Ex	cternal Components. Additional application	on details in	Buck2.	•	
Buck2 Output Voltage Target Resolution	BK2 _{RES}			4		bits
Buck2 Output Voltage Range	BK2 _{OUT}	BUCK2_FB	1.1	-	1.85	٧
Buck2 Output Voltage Step	BK2 _{STEP}	BUCK2_FB		50		mV
Buck2 Output Voltage DC Accuracy	BK2 _{ACC}	BUCK2_FB. PWM operation, I _{OUT} = 5mA, V _{OUT} = 1.2V	-1	-	1	%
Buck2 Output Voltage Ripple FPWM	BK2 _{RIP_FPWM}	I _{OUT} = 100mA, FPWM mode		10	-	mVpp
Buck2 Maximum Output Current Capability ^[5]	BK2 _{IOUT_MAX}		1.5			А
Buck2 Output Load Regulation	BK2 _{LOAD_REG}	FPWM, VOUT = 1.2V, Over I _{OUT} = 100mA to 1.5A range		±0.15		%
Buck2 Output Line Regulation	BK2 _{LINE_REG}	BUCK2_VINx = $4.5V \leftrightarrow 5.5V$, VOUT = $1.2V$, $I_{OUT} = BK2_{IOUT_MAX}$		±0.15		%

Parameter	Symbol	Test Conditions ^[1]	Min ^[2]	Тур	Max ^[2]	Unit
Buck2 Peak Efficiency	BK2 _{EFF}	Peak efficiency, L = default, BK2 _{FSW} set to default ^[6] , maximum V _{OUT}		90		%
		BUCK2_FB. Slow setting	35	50	65	
Buck2 Discharge Resistance	BK2 _{RDCHG}	BUCK2_FB. Medium setting	26	37.5	49	Ω
		BUCK2_FB. Fast setting	17.5	25	32.5	
Buck2 High-Side MOSFET Current Limit	BK2 _{ILIM_HS}	PWM operation, sourcing (supplying)	2.27	2.5	2.78	A
Buck2 Low-Side	BK2 _{ILIM_LS}	PWM operation, sourcing (supplying)		3		Α
MOSFET Current Limit	BK2 _{ILIMNEG}	FPWM mode, sinking (receiving)		-0.66		Α
Buck2 PWM Switching Frequency	BK2 _{FSW}	FPWM mode, 0.769MHz (default) setting		0.769		MHz
Buck2 PWM Switching Frequency Accuracy	BK2 _{FSW_ACC}	FPWM mode, I _{OUT} = 0mA, default frequency	-10		+10	%
Buck2 Soft-start Slew Rate Range	BK2 _{SS_SR_RNG}	BUCK2_FB	0.5	1	4	ms
Buck2 Shutdown Slew Rate Range	BK2 _{SHTDN} _ SR_RNG	BUCK2_FB	0.5	1	4	ms
Buck2 DVS Slew Rate Range	BK2 _{DVS_SR_RNG}	BUCK2_FB. Applies to both DVS up and down ramps.	2	8	16	mV/μs
Buck2 High-Side PMOS On-Resistance	BK2 _{RDSON_HS}	BUCK2_VINx to BUCK2_LXx, I _{LX} = -150mA		120		mΩ
Buck2 Low-Side NMOS On-Resistance	BK2 _{RDSON_LS}	BUCK2_LXx to PGND, I _{LX} = 150mA		70		mΩ
BUCK3 (1.5A) Components as describ	ed in Recommended Ex	xternal Components. Additional application	on details in	Buck3.	•	
Buck3 Output Voltage Target Resolution	BK3 _{RES}			4		bits
Buck3 Output Voltage Range	BK3 _{OUT}	BUCK3_FB	1.8		3.3	V
Buck3 Output Voltage Step	BK3 _{STEP}	BUCK3_FB		100		mV
Buck3 Output Voltage DC Accuracy	BK3 _{ACC}	BUCK3_FB. PWM operation, I _{OUT} = 5mA, V _{OUT} = 1.8V	-1		1	%
Buck3 Output Voltage Ripple FPWM	BK3 _{RIP_FPWM}	I _{OUT} = 100mA, FPWM mode		10		mVpp
Buck3 Maximum Output Current Capability ^[5]	BK3 _{IOUT_MAX}		1.5			А

Parameter	Symbol	Test Conditions ^[1]	Min ^[2]	Тур	Max ^[2]	Unit
Buck3 Output Load Regulation	BK3 _{LOAD_REG}	FPWM, VOUT = 1.8V, Over I _{OUT} = 100mA to 1.5A range		±0.1		%
Buck3 Output Line Regulation	BK3 _{LINE_REG}	BUCK3_VINx = $4.5V \leftrightarrow 5.5V$, VOUT = $1.8V$, $I_{OUT} = BK3_{IOUT_MAX}$		±0.1		%
Buck3 Peak Efficiency	BK3 _{EFF}	Peak efficiency, L = default, BK3 _{FSW} set to default ^[6] , maximum V _{OUT}		92		%
		BUCK3_FB. Slow setting	35	50	75	
Buck3 Discharge Resistance	BK3 _{RDCHG}	BUCK3_FB. Medium setting	26	37.5	49	Ω
		BUCK3_FB. Fast setting	17.5	25	32.5	
Buck3 High-Side MOSFET Current Limit	BK3 _{ILIM_HS}	PWM mode, sourcing (supplying)	2.12	2.5	3	А
Buck3 Low-Side	BK3 _{ILIM_LS}	PWM operation, sourcing (supplying)		3		А
MOSFET Current Limit	BK3 _{ILIMNEG}	FPWM mode, sinking (receiving)		-0.55		
Buck3 PWM Switching Frequency	BK3 _{FSW}	FPWM mode, 1.54MHz (default) setting	ΊΛ	1.54		MHz
Buck3 PWM Switching Frequency Accuracy	BK3 _{FSW_ACC}	FPWM mode, I _{OUT} = 0mA, default frequency	-10		+10	%
Buck3 Soft-Start Slew Rate Range	BK3 _{SS_SR_RNG}	BUCK3_FB	0.5	1	4	ms
Buck3 Shutdown Slew Rate Range	BK3 _{SHTDN} _ SR_RNG	BUCK3_FB	0.5	1	4	ms
Buck3 DVS Slew Rate Range	BK3 _{DVS_SR_RNG}	BUCK3_FB. Applies to both DVS up and down ramps.	2	8	16	mV/μs
Buck3 High-Side PMOS On-Resistance	BK3 _{RDSON_HS}	BUCK3_VINx to BUCK3_LXx, I _{LX} = -150mA		93		mΩ
Buck3 Low-Side NMOS On-Resistance	BK3 _{RDSON_LS}	BUCK3_LXx to PGND, I _{LX} = 150mA		57		mΩ
BUCK4 (3.5A) Components as describe	ed in Recommended E	external Components. Additional application	on details in	Buck4.		
Buck4 Output Voltage Target Resolution	BK4 _{RES}			4		bits
Buck4 Output Voltage Range	BK4 _{OUT}	BUCK4_FB 0.8V, 0.85V, 0.9V, 0.95V, 1V,1.05V, 1.1V, 1.15V, 1.2V, 1.5V, 1.6V 1.8V, 1.85V, 2.2V, 2.5V and 3.3V	0.8		3.3	V
Buck4 Output Voltage DC Accuracy	BK4 _{ACC}	BUCK4_FB. PWM operation, I _{OUT} = 5mA, V _{OUT} = 3.3V	-1		1	%

Parameter	Symbol	Test Conditions ^[1]	Min ^[2]	Тур	Max ^[2]	Unit
Buck4 Output Voltage Ripple FPWM	BK4 _{RIP_FPWM}	I _{OUT} = 100mA, FPWM mode		15		mVpp
Buck4 Maximum Output Current Capability ^[5]	BK4 _{IOUT_MAX}		3.5			А
Buck4 Output Load Regulation	BK4 _{LOAD_REG}	FPWM, VOUT = 3.3V, Over I _{OUT} = 100mA to 3.5A range		±0.1		%
Buck4 Output Line Regulation	BK4 _{LINE_REG_3V3}	BUCK4_VINx = $4.5V \leftrightarrow 5.5V$, VOUT = $3.3V$, $I_{OUT} = BK4_{IOUT_MAX}$		±0.1		%
Buck4 Peak Efficiency	BK4 _{EFF}	Peak efficiency, L = default, BK4 _{FSW} set to default ^[6] , maximum V _{OUT}		95		%
		BUCK4_FB. Slow setting	35	50	65	
Buck4 Discharge Resistance	ance BK4 _{RDCHG} B	BUCK4_FB. Medium setting	26	37.5	49	Ω
		BUCK4_FB. Fast setting	17.5	25	32.5	
Buck4 High-Side MOSFET Current Limit	BK4 _{ILIM_HS}	PWM operation, sourcing (supplying)	4	4.5	5	А
Buck4 Low-Side	BK4 _{ILIM_LS}	PWM operation, sourcing (supplying)	IA	5		_
MOSFET Current Limit	BK4 _{ILIMNEG}	FPWM mode, sinking (receiving)		-0.675		Α
Buck4 PWM Switching Frequency	BK4 _{FSW}	FPWM mode, 1.54MHz (default) setting		1.54		MHz
Buck4 PWM Switching Frequency Accuracy	BK4 _{FSW_ACC}	FPWM mode, I _{OUT} = 0mA, default frequency	-10		+10	%
Buck4 Soft-Start Slew Rate Range	BK4 _{SS_SR_RNG}	BUCK4_FB	0.5	1	4	ms
Buck4 Shutdown Slew Rate Range	BK4 _{SHTDN} _ SR_RNG	BUCK4_FB	0.5	1	4	ms
Buck4 DVS Slew Rate Range	BK4 _{DVS_SR_RNG}	BUCK4_FB. Applies to both DVS up and down ramps.	2	8	16	mV/μs
Buck4 High-Side PMOS On-Resistance	BK4 _{RDSON_HS}	BUCK4_VINx to BUCK4_LXx, I _{LX} = -150mA		60		mΩ
Buck4 Low-Side NMOS On-Resistance	BK4 _{RDSON_LS}	BUCK4_LXx to PGND, I _{LX} = 150mA		30		mΩ
BUCK5 (0.6A) Components as describe	ed in Recommended E	xternal Components. Additional application	on details in	Buck5.		
Buck5 Output Voltage Target Resolution	BK5 _{RES}			3		bits
Buck5 Output Voltage Range	BK5 _{OUT}	BUCK5_FB	1.2	-	3.3	V

Parameter	Symbol	Test Conditions ^[1]	Min ^[2]	Тур	Max ^[2]	Unit
Buck5 Output Voltage DC Accuracy	BK5 _{ACC}	BUCK5_FB. PWM operation, I _{OUT} = 5mA, V _{OUT} = 1.8V	-1		1	%
Buck5 Output Voltage Ripple FPWM	BK5 _{RIP_FPWM}	I _{OUT} = 100mA, FPWM mode		15		mVpp
Buck5 Maximum Output Current Capability ^[5]	BK5 _{IOUT_MAX}		0.6			А
Buck5 Output Load Regulation	BK5 _{LOAD_REG}	FPWM, VOUT = 1.2V, Over I _{OUT} = 100mA to 600mA range		±0.1		%
Buck5 Output Line Regulation	BK5 _{LINE_REG}	BUCK5_VINx = $4.5V \leftrightarrow 5.5V$, VOUT = $1.2V$, $I_{OUT} = BK5_{IOUT_MAX}$		±0.1		%
Buck5 Peak Efficiency	BK5 _{EFF}	Peak efficiency, L = default, BK5 _{FSW} set to default ^[6] , maximum V _{OUT}		94		%
		BUCK5_FB. Slow setting	35	50	65	Ω
Buck5 Discharge Resistance	BK5 _{RDCHG}	BUCK5_FB. Medium setting	26	37.5	49	
		BUCK5_FB. Fast setting	17.5	25	32.5	
Buck5 High-Side MOSFET Current Limit	BK5 _{ILIM_HS}	PWM operation, sourcing (supplying)	0.9	1	1.1	А
Buck5 Low-Side	BK5 _{ILIM_LS}	PWM operation, sourcing (supplying)		1.4		
MOSFET Current Limit	BK5 _{ILIMNEG}	FPWM mode, sinking (receiving)		-0.55		A
Buck5 PWM Switching Frequency	BK5 _{FSW}	FPWM mode, 1.54MHz (default) setting		1.54		MHz
Buck5 PWM Switching Frequency Accuracy	BK5 _{FSW_ACC}	FPWM mode, I _{OUT} = 0mA, default frequency	-10		+10	%
Buck5 Soft-start Slew Rate Range	BK5 _{SS_SR_RNG}	BUCK5_FB	0.5	1	4	ms
Buck5 Shutdown Slew Rate Range	BK5 _{SHTDN} _ SR_RNG	BUCK5_FB	0.5	1	4	ms
Buck5 DVS Slew Rate Range	BK5 _{DVS_SR_RNG}	BUCK5_FB. Applies to both DVS up and down ramps.	2	8	16	mV/μs
Buck5 High-Side PMOS On-Resistance	BK5 _{RDSON_HS}	BUCK5_VINx to BUCK5_LXx, I _{LX} = -150mA		220		mΩ
Buck5 Low-Side NMOS On-Resistance	BK5 _{RDSON_LS}	BUCK5_LXx to PGND, I _{LX} = 150mA		105		mΩ
BUCK6 (±1A) VTT Mode. Components	s as described in Recon	nmended External Components. Addition	nal application	on details i	n Buck6.	ı
Buck6 Output Voltage VTT Mode	BK6 _{OUT_VTT}	BUCK6_FB. DDR JEDEC spec. DDR VTT output		VREF OUT		V

Parameter	Symbol	Test Conditions ^[1]	Min ^[2]	Тур	Max ^[2]	Unit
Buck6 Output Voltage DC Accuracy	BK6 _{ACC}	BUCK6_FB. FPWM mode, I _{OUT} = 5mA, V _{OUT} = 1.8V	-1		1	%
Buck6 Output Total Accuracy VTT Mode	BK6 _{ACC_TOT}	BUCK6_FB.DC + Ripple + Transient. FPWM mode, over line/load/temp. VOUT = 0.6V I _{OUT} -1A → +1A at 2.5A/µs	-30		30	mV
Buck6 Output Voltage Ripple FPWM	BK6 _{RIP_FPWM}	I _{OUT} = 100mA, FPWM mode		30		mVpp
Buck6 Maximum Output Current	BK6	VTT mode. Source (supply) current for DDR VTT	1			А
Capability ^[5]		VTT mode. Sink (receive) current from DDR VTT	1			А
Buck6 Output Load Regulation	BK6 _{LOAD_REG}	FPWM, VOUT = 0.6V, Over I _{OUT} = 100mA to 1A range		±0.1		%
Buck6 Output Line Regulation	BK6 _{LINE_REG}	$\begin{aligned} & BUCK6_VINx = 4.5V \leftrightarrow 5.5V, \\ & VOUT = 0.6V, \\ & I_{OUT} = BK6_{IOUT_MAX} \end{aligned}$		±0.1		%
Buck6 Peak Efficiency	BK6 _{EFF}	Peak efficiency, L = default, BK6 _{FSW} set to default ^[6] , FPWM mode, VOUT = 0.6V	IΔ	76		%
	OOI.	BUCK6_FB. Slow setting	35	50	65	
Buck6 Discharge Resistance	BK6 _{RDCHG}	BUCK6_FB. Medium setting	26	37.5	49	Ω
		BUCK6_FB. Fast setting	17.5	25	32.5	
Buck6 High-Side MOSFET Current Limit	BK6 _{ILIM_HS}	FPWM mode, sourcing (supplying), VTTREF_EN = 1	2.4	2.75	3.2	A
Buck6 Low-Side MOSFET Current	BK6 _{ILIM_LS}	FPWM mode, sourcing (supplying), VTTREF_EN = 1		3.25		A
Limit	BK6 _{ILIMNEG}	FPWM mode, sinking (receiving), VTTREF_EN = 1		-2.3		
Buck6 PWM Switching Frequency	BK6 _{FSW}	FPWM mode, 0.667MHz (default) setting		0.667		MHz
Buck6 PWM Switching Frequency Accuracy	BK6 _{FSW_ACC}	FPWM mode, I _{OUT} = 0mA, default frequency	-10		+10	%
Buck6 Soft-start Slew Rate Range	BK6 _{SS_SR_RNG}	BUCK6_FB	0.5	1	4	ms
Buck6 Shutdown Slew Rate Range	BK6 _{SHTDN} _ SR_RNG	BUCK6_FB	0.5	1	4	ms
Buck6 DVS Slew Rate Range	BK6 _{DVS_SR_RNG}	BUCK6_FB. Applies to both DVS up and down ramps.	2	8	16	mV/μs
Buck6 High-Side PMOS On-Resistance	BK6 _{RDSON_HS}	BUCK6_VINx to BUCK6_LXx, I _{LX} = -150mA		125		mΩ

Parameter	Symbol	Test Conditions ^[1]	Min ^[2]	Тур	Max ^[2]	Unit
Buck6 Low-Side NMOS On-Resistance	BK6 _{RDSON_LS}	BUCK6_LXx to PGND, I _{LX} = 150mA		75		mΩ
LDO1 and LDO2 (300m Components as describe	-	cternal Components. Additional application	on details in	LDO1/2.		
LDO12 Output Voltage Range	LDO12 _{OUT}	LDO1_OUT, LDO2_OUT 0.8V, 0.9V,1.2V, 1.5V, 1.8V, 2.5V, 3.0V, 3.3V	0.8		3.3	V
LDO12 Output Voltage DC Accuracy	LDO12 _{ACC_H}	I _{OUT} = 1mA and 300mA LDO _{OUT} = 2.5V to 3.3V	-3		3	
	LDO12 _{ACC_M}	I _{OUT} = 1mA and 300mA LDO _{OUT} = 1.5V to 1.8V	-4		4	%
	LDO12 _{ACC_L}	I _{OUT} = 1mA and 300mA LDO _{OUT} = 0.8V to 1.2V	-5		5	
LDO12 Maximum Output Current Capability	LDO12 _{IOUT}	LDO1_OUT, LDO2_OUT. External load, sourcing (supplying)	300			mA
LDO12 Output Current Limit	LDO12 _{ILIM}	LDOx_OUT = 10% below regulation target (less positive voltage). LDO1/2 is not expected to operate at this current level continuously.	IA	500		mA
		Rising threshold is a percentage of the programmed LDO output voltage	-15	-10	-5	
LDO12 Power-Good	LDO12 _{PGOOD}	Falling threshold is a percentage of the programmed LDO output voltage	-21	-15	-10	%
		Hysteresis	4	5	6	
LDO12 Load Transient	LDO12 _{LOAD}	Step: 60mA → 240mA in 1A/µs Step: 240mA → 60mA in 1A/µs	-3		3	%
		VOUT = 2.5V to 3.3V range, I _{OUT} = 1mA to 300mA ^[5]	-1		1	
LDO12 Load Regulation	LDO12 _{LOAD_REG}	VOUT = 1.8V, I _{OUT} = 1mA to 300mA	-1.25		1.25	%
		VOUT = 0.8V, I _{OUT} = 1mA to 300mA ^[5]	-2.5		2.5	
LDO12 Line Regulation	LDO12 _{LINE_REG}	LDOx_VIN = 2.7V ↔ 5.5V, VOUT = 1.8V, I _{OUT} = 300mA	-2		2	%
PSRR	LDO12 _{PSRR}	vs. LDOx_VIN, AVDD. DC to 100kHz, C _{OUT} = default, LDOx_VIN = LDOx_OUT + 0.3V (Not in dropout)			-40	dB
1 ONK	LDO 12PSRR	vs. LDOx_VIN, AVDD. 100kHz to 2MHz, C _{OUT} = default, LDOx_VIN = LDOx_VOUT + 0.3V (not in dropout)			-20	uD

Parameter	Symbol	Test Conditions ^[1]	Min ^[2]	Тур	Max ^[2]	Unit
Bypass Mode ON-Resistance	LDO12 _{RDSON}	I _{OUT} = 100mA		0.33	0.5	Ω
LDO12 Dropout Voltage	LDO12 _{DROPOUT}	I _{OUT} = LDO12 _{IOUT(max)}			300	mV
		LDOx_OUT. Slow setting	35	50	65	
LDO12 Discharge Resistance	LDO12 _{RDCHG}	LDOx_OUT. Medium setting	26	37.5	49	Ω
		LDOx_OUT. Fast setting	17.5	25	32.5	
LDO3 (50mA) Components as describ	ed in Recommended Ex	cternal Components. Additional application	on details in	LDO3.		
LDO3 Output Voltage Range	LDO3 _{OUT}	LDO3_OUT 0.8V, 0.9V,1.2V, 1.5V, 1.8V, 2.5V, 3.0V, 3.3V	0.8		3.3	V
LDO3 Output Voltage DC Accuracy	LDO3 _{ACC_H}	I _{OUT} = 1mA and 50mA LDO _{OUT} = 2.5V to 3.3V	-3		3	
	LDO3 _{ACC_M}	I _{OUT} = 1mA and 50mA LDO _{OUT} = 1.5V to 1.8V	-4		4	%
	LDO3 _{ACC_L}	I _{OUT} = 1mA and 50mA LDO _{OUT} = 0.8V to 1.2V	-5		5	
LDO3 Maximum Output Current Capability	LDO3 _{IOUT}	LDO3_OUT. External load, sourcing (supplying)	50			mA
LDO3 Output Current Limit	LDO3 _{ILIM}	LDO3_OUT = 10% below regulation target (less positive voltage). LDO3 is not expected to operate at this current level continuously.		80		mA
		Rising threshold is a percentage of the programmed LDO output voltage	-15	-10	-5	
LDO3 Power-Good	LDO3 _{PGOOD}	Falling threshold is a percentage of the programmed LDO output voltage	-21	-15	-10	%
		Hysteresis	4	5	6	
LDO3 Load Transient	LDO3 _{LOAD}	Step: 1mA → 50mA in 1A/µs Step: 50mA → 1mA in 1A/µs	-3		3	%
LDO3 Load		V _{OUT} = 2.5V to 3.3V range, I _{OUT} = 1mA to 50mA ^[5]	-1		1	
Regulation	LDO3 _{LOAD_REG} V	V _{OUT} = 1.8V, I _{OUT} = 1mA to 50mA	-1.5		1.5	- % -
		V _{OUT} = 0.8V, I _{OUT} = 1mA to 50mA ^[5]	-3		3	
LDO3 Line Regulation	LDO3 _{LINE_REG}	LDO3_VIN = 2.7V ↔ 5.5V, VOUT = 1.8V,I _{OUT} = 50mA		1	2	%

Parameter	Symbol	Test Conditions ^[1]	Min ^[2]	Тур	Max ^[2]	Unit
LDO3 PSRR	1003	vs. LDO3_VIN, AVDD. DC to 100kHz, C _{OUT} = default, LDOx_IN = LDO3_OUT + 0.3V (not in dropout)			-40	dB
LDOS FSKK	LDO3 _{PSRR}	vs. LDO3_VIN, AVDD. 100kHz to 2MHz, C _{OUT} = default, LDOx_IN = LDO3_OUT+ 0.3V (not in dropout)			-20	uБ
LDO3 Bypass Mode ON-Resistance	LDO3 _{RDSON}	I _{OUT} = 10mA		1.3	1.8	Ω
LDO3 Dropout Voltage	LDO3 _{DROPOUT}	I _{OUT} = LDO3 _{IOUT(max)}			300	mV
		LDO3_OUT. Slow setting	35	50	65	
LDO3 Discharge Resistance	LDO3 _{RDCHG}	LDO3_OUT. Medium setting	26	37.5	49	Ω
		LDO3_OUT. Fast setting	17.5	25	32.5	
VTTREF Components as describ	ed in Recommended Ex	cternal Components. Additional application	on details in	VTTREF.		
VREFIN Input Operating Range	VREFINOP	IEIDENIT	1.1		1.8	٧
VREFIN Undervoltage Lockout Threshold	VREFIN _{UVLO_F}	Falling VREFIN	0.72	0.78	0.84	V
VREFIN Undervoltage Lockout Hystersis	VREFIN _{UVLO_HYS}	VREFIN _{UVLO_R} = VREFIN _{UVLO_F} + V REFIN _{UVLO_HYS}		20		mV
VREFIN UVLO Falling Delay	t _{VREFIN_UVLO_} F_DLY	Falling VREFIN		1		ms
VREFOUT Output Range	VREFOUT _{RNG}	VREFOUT = buffered version of VREFIN/2	0.55		0.9	V
VREFOUT Output	VDEFOLIT	sourcing (supplying)	10			A
Current	VREFOUT _{IOUT}	sinking (receiving)	10			mA
VREFOUT Output	VDEFOLIT	sourcing (supplying)	22	40	58	A
Current Limit	VREFOUT _{ILIM}	sinking (receiving)		40		mA
\/DEEQLIT	VREFOUT _{ACC_AC}	VTTREF_EN = 1 DDR JEDEC spec	0.49* VREFIN	0.5* VREFIN	0.51* VREFIN	V
VREFOUT Accuracy	VREFOUT _{ACC_DC}	VTTREF_EN = 1 DDR JEDEC spec	-0.01* VREFIN		0.01* VREFIN	V
		VREFOUT. Fast setting		50	65	
VREFOUT Discharge Resistance	VREFOUT _{RDCHG}	VREFOUT. Medium setting		75	97	Ω
. 130,044,100		VREFOUT. Slow setting		100	130	
		1	1	l .	ı	

Parameter	Symbol	Test Conditions ^[1]	Min ^[2]	Тур	Max ^[2]	Unit
Charger				0:0 "		
Components as describ	ed in Recommended Ex	kternal Components. Additional applicatio	on details in	Coin Cell E	Battery Cha	rger.
VCHG Operating Voltage Range	VCHG _{OP}		2.7	5	5.5	V
VBAT Charging Voltage Termination Range	VBAT _{RNG}	sets VBAT voltage to automatically disable charger operation	1.8	3.3	3.3	٧
VBAT Charging Voltage Termination Step	VBAT _{STEP}	VBAT		100		mV
VCHG Headroom	VCHG _{HD}	Input voltage headroom. VCHG needs to be above VBAT + VCHG _{HD} to make the charger operate at the programmed charge current	300			mV
VRTC Voltage Hysteresis	VRTC _{HYS}	Threshold for VRTC supply switching to being derived from VCHG (rather than VBAT), VCHG rising above VBAT + VBAT _{HYS}		50		mV
Charge Current Setting Range	VBAT _{IOUT}	VBAT. 60μA (default) setting	20	60	60	μΑ
Charge Current Accuracy	VBAT _{IOUT_ACC}	VBAT	-20		20	%
RTC						
Components as describ	ed in Recommended Ex	kternal Components. Additional application	on details in	Real-Time	Clock.	
VBAT Operating Voltage Range	VBAT _{OP}	Battery backup mode	1.8	3.3	5.5	V
VRTC Operating Voltage Range	VRTC _{OP}	Generated internally from higher of VCHG or VBAT	1.8	5	5.5	٧
Oscillator Frequency	RTC _{FREQ}			32.768		kHz
Oscillator Duty Cycle	RTC _{DUTY}			50		%
I ² C		1	ı	1	1	
7-bit Slave Address	I2C _{ADDR_MAIN}	Access to non-RTC related registers. 7-bit uniquely programmable in EEPROM	1	12	7F	
Range	I2C _{ADDR_RTC}	Access to RTC related registers. 7-bit uniquely programmable in EEPROM	1	6F	7F	- Hex
SCL Clock Frequency	f _{SCL}	Supports standard 100kHz, 400kHz, 1MHz	-	-	1	MHz
		I .	1	•		

Parameter	Symbol	Test Conditions ^[1]	Min ^[2]	Тур	Max ^[2]	Unit		
Logic I/O		,	<u>'</u>		1			
Operating Input Voltage Range	V _{OP_EN}	CEN, PWRON	0		5.5	V		
	V _{OP_MPIO}	MPIOx	5.5	V				
	V _{OP_I2C}	SCL, SDA 0			5.5	V		
	V _{OP_LDOSEL}	LDO_SEL1, LDO_SEL2		5.5	V			
	V _{IH_EN}	CEN, PWRON	1.2			V		
HIGH 1 Input Voltage	V _{IH_MPIO}	MPIOx	1.2			V		
Threshold	V _{IH_I2C}	SCL, SDA	1.2			V		
	V _{IH_LDOSEL}	LDO_SEL1, LDO_SEL2, in {ACTIVE}				V		
	V _{IL_EN}	CEN, PWRON			0.4	V		
LOW 0 Input Voltage	V _{IL_MPIO}	MPIOx			0.4	V		
Threshold	V_{IL_I2C}	SCL, SDA			0.4	V		
	V _{IL_LDOSEL}	LDO_SEL1, LDO_SEL2, in {ACTIVE}			0.4	V		
	V _{EN_HYS}	CEN, PWRON	150			mV		
	V _{MPIO_HYS}	MPIOx	150			mV		
Input Hysteresis	V _{I2C_HYS}	SCL, SDA 150		150		mV		
	V _{LDOSEL_HYS}	LDO_SEL1, LDO_SEL2, in {ACTIVE}		150		mV		
	I _{L_EN}	CEN, PWRON. CEN = 5.5V, PWRON = 5.5V ^[7]	-3.5		3.5			
Input Leakage Current	I _{L_MPIO}	MPIOx. MPIOx = $5.5V^{[7]}$	-3.5		3.5	μΑ		
	I _{L_I2C}	SDA, SCL SDA = SCL = 5.5V	-1		1			
	I _{L_LDOSEL}	LDO_SELx, LDO_SELx = 5.5V ^[7]	-3.5	3.5				
Low Level Output	V _{OL_MPIO}	MPIOx as output, open-drain. Pull up to 1.8V, sinking 2mA			0.4			
Voltage	V _{OL_SDA}	SDA. Pull up to 1.8V, sinking 2mA			0.4	V		
	V_{OL_INT}	INT#. Pull up to 1.8V, sinking 2mA			0.4			
High Level Output Voltage	V _{OH_MPIO}	MPIOx as full CMOS output, sourcing 2mA	s full CMOS output, sourcing 1.2					

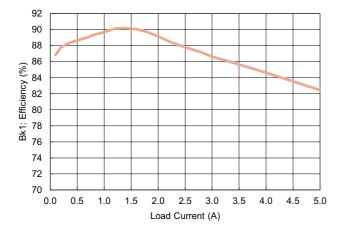
Parameter	Symbol	Test Conditions ^[1]	Min ^[2]	Тур	Max ^[2]	Unit
Protections						
Output Overvoltage Protection Threshold	DV.	BUCKx_FB rising. Percentage of output voltage target setting (Bucks 1, 2, 3)	6	8.5	11	
	BK _{OVP_R}	BUCKx_FB rising. Percentage of output voltage target setting (Bucks 5 and 6)	6	8.5	12.5	
	DIV	BUCKx_FB falling. Percentage of output voltage target setting (Bucks 1, 2, 3)	4	6.5	9	
	BK _{OVP_F}	BUCKx_FB falling. Percentage of output voltage target setting (Bucks 5 and 6)	3	6.5	9	%
	BK _{OVP_HYS}	BK _{OVP_HYS} = BK _{OVP_R} - BK _{OVP_F} . Percentage of output target setting. (Bucks 1, 2, 3, 5, and 6)		2		
	BK4 _{OVP_R}	BUCK4_FB rising. Percentage of output voltage target setting	5	10	15	
	BK4 _{OVP_F}	BUCK4_FB falling below BK _{OVP} . Percentage of output target setting	4_	8.5	13	
	BK4 _{OVP_HYS}	BK4 _{OVP_HYS} = BK4 _{OVP_R} - BK4 _{OVP_F} . Percentage of output target setting.		1.5		
Output Undervoltage Protection Threshold	BK _{UVP_R}	BUCKx_FB rising. Percentage of output voltage target setting. (Bucks 1, 2, 3, 5, and 6)	-8	-5.5	-2	
	DIA	BUCKx_FB falling. Percentage of output target setting. (Bucks 1, 2, 3)	-13	-11	-8	
	BK _{UVP_F}	BUCKx_FB falling. Percentage of output target setting. (Bucks 5 and 6)	-13	-11	-6	
	BK _{UVP_HYS}	BK _{UVP_HYS} = BK _{UVP_R} - BK _{UVP_F} . Percentage of output target setting. (Bucks 1, 2, 3, 5, and 6)		5.5		%
	BK4 _{UVP_R}	BUCK4_FB rising. Percentage of output voltage target setting.	-12	-7	-2.5	
	BK4 _{UVP_F}	BUCK4_FB falling. Percentage of output target setting.	-18	-13	-8	
	BK4 _{UVP_HYS}	BK4 _{UVP_HYS} = BK4 _{UVP_R} - BK4 _{UVP_F} . Percentage of output target setting.		6		

Parameter	Symbol	Test Conditions ^[1]	Min ^[2]	Тур	Max ^[2]	Unit
Output Fault Deglitch Time	^t FLT_DEGLITCH	Deglitch time from fault event to INT# assertion for unmasked faults, including: BUCK OV and UV, LDO PGOOD, Thermal Warning and Shutdown.	0.8	1	1.2	ms
High Current Warning Deglitch Time	tHC_DEGLITCH	Buck1 high current warning		100		μs
Thermal Shutdown Threshold	T _{SHDN}	Junction temperature rising. Thermal shutdown asserted.	- 1 1/5 130 145			°C
	T _{SHDN_HYS}	Junction temperature falling below T _{SHDN} . Thermal shutdown de-asserted.		30		°C
Thermal Warning Threshold	T _{WARN}	Junction temperature rising. Thermal warning asserted. 120°C setting	110 120 130		°C	
	T _{WARN_HYS}	Junction temperature falling below T _{WARN} Thermal warning de-asserted.			°C	
Timing		•			•	
PWRON Deglitch Time	tpwron_deglitch	IEIDENIT	' I A	100		μs
MPIOx Deglitch Time	t _{MPIO_DEGLITCH}	HII)HNI	IA	1.5		μs

- 1. All the C_{OUT} listed in Test Condition are nominal values (not derated), unless stated as derated or effective. For details on the recommended components, see External Component Selection.
- 2. Parameters with MIN and/or MAX limits are 100% tested at +25°C, unless otherwise specified. Temperature limits established by characterization and are not production tested.
- 3. Follow this supply timing to ensure correct timekeeping of the RTC.
- 4. When a MPIOx is configured as full CMOS output, the sourcing current comes from VIO.
- 5. Compliance to datasheet limits is established by one or more methods: production test, characterization, and/or design.
- 6. At light loads, switching frequency is lower than the setting.
- 7. There is an internal $2M\Omega$ pull-down resistor at each of the following pins: CEN, PWRON, MPIOx, and LDO_SELx.

4. Typical Performance Graphs

AVDD = VCHG = BUCKx_VINx = 5V, BUCK1_FB = 1.1V, BUCK2_FB = 1.2V, BUCK3_FB = 1.8V, BUCK4_FB = 3.3V, BUCK5_FB = 1.2V, BUCK6_FB = 0.6V, CEN = HIGH, PWRON = HIGH, $T_A = +25^{\circ}$ C, unless otherwise stated. Refer to the RTKA215300DE0000BU BOM for the components used in the following measurements.



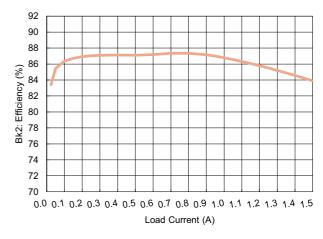
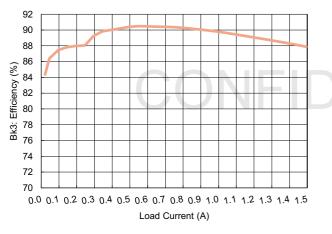


Figure 3. Buck1 Efficiency in Auto PFM/PWM mode

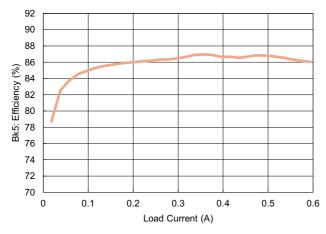
Figure 4. Buck2 Efficiency in Auto PFM/PWM mode



98 96 94 Efficiency (% 92 90 88 86 Bk4: 84 82 80 2.0 3.5 0.0 0.5 1.0 1.5 2.5 3.0 Load Current (A)

Figure 5. Buck3 Efficiency in Auto PFM/PWM mode

Figure 6. Buck4 Efficiency in Auto PFM/PWM mode



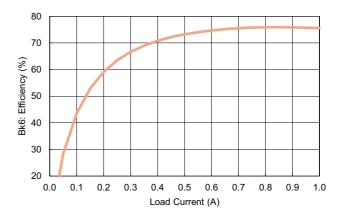


Figure 7. Buck5 Efficiency in Auto PFM/PWM mode

Figure 8. Buck6 Efficiency in VTT configuration (FPWM mode)

5. Serial Interface

The RAA215300 includes a standard I²C serial interface. The 2-wire interface links one or more Masters and uniquely addressable Slave devices. The Master generates clock signals and is responsible for initiating data transfers. The serial clock is on the SCL line and the serial data (bidirectional) is on the SDA line. The RAA215300 supports clock rates up to 1MHz (Fast mode plus) and is downward compatible with standard 100kHz (Standard mode), and 400kHz (Fast mode) clock rates.

The SDA and SCL lines must be HIGH when the bus is free (not in use). An external pull-up resistor (typically $1k\Omega$ to $4.7k\Omega$ depending on clock speed, pull-up voltage, and bus capacitance) or current source is required for SDA and SCL.

The I²C interface is not functional until VIO_PGOOD is high. See VCHG, VBAT, and VRTC for more details.

5.1 I²C General Operation

5.1.1 Data Validity

The data on the SDA line must be stable (clearly defined as HIGH or LOW) during the HIGH period of the clock signal. The state of the SDA line can only change when the SCL line is low (except to create a START or STOP condition). The voltage levels used to indicate a logical 0 (LOW) and logical 1(HIGH) are determined by the $V_{\rm IL}$ and $V_{\rm IH}$ thresholds, respectively, see Electrical Specifications.

5.1.2 START and STOP Condition

All I²C communication begins with a START condition (indicating the beginning of a transaction) and ends with a STOP condition (signaling the end of the transaction).

A START condition is signified by a HIGH-to-LOW transition on the serial data line (SDA) while the serial clock line (SCL) is HIGH. A STOP condition is signified by a LOW-to-HIGH transition on the SDA line while SCL is HIGH. See timing specifications in Electrical Specifications.

The Master always initiates START and STOP conditions. After a START condition, the bus is considered busy. After a STOP condition, the bus is considered free. The device supports repeated STARTs, where the bus remains busy for the continued transaction(s).

5.1.3 Byte Format

Every byte on SDA must be 8 bits in length. After every byte of data sent by the transmitter, there must be an Acknowledge bit (from the receiver) to signify that the previous 8 bits were transferred successfully. Data is always transferred on SDA with the most significant bit (MSB) first. If the data is larger than 8 bits, it can be separated into multiple 8-bit bytes.

5.1.4 Acknowledge (ACK)

Each 8-bit data transfer is followed by an Acknowledge (ACK) bit from the receiver. The ACK bit signifies that the previous 8 bits of data were transferred successfully (master-slave or slave-master).

When the Master sends data to the Slave (for example, during a WRITE transaction), after the 8th bit of a data byte is transmitted, the Master tri-states the SDA line during the 9th clock. The Slave device acknowledges that it received all 8 bits by pulling down the SDA line, generating an ACK bit.

When the Master receives data from the Slave (for example, during a data READ transaction), after the 8th bit is transmitted, the Slave tri-states the SDA line during the 9th clock. The Master acknowledges that it received all 8 bits by pulling down the SDA line, generating an ACK bit.



5.1.5 Not Acknowledge (NACK)

A Not Acknowledge (NACK) bit is generated when the receiver does not pull down the SDA line during the acknowledge clock (that is, the SDA line remains HIGH during the 9th clock), indicating to the Master that it can generate a STOP condition to end the transaction and free the bus.

A NACK bit can be generated for various reasons, for example:

- After an I²C device address is transmitted, there is NO receiver with that address on the bus to respond.
- The receiver is busy performing an internal operation (for example, reset or recall) and cannot respond.
- The Master (acting as a receiver) needs to indicate the end of a transfer with the Slave (acting as a transmitter).

5.1.6 Device Address and R/W Bit

After a valid START condition, the first byte sent in a transaction contains the 7-bit Device (Slave) Address plus a direction (R/W) bit (Device Address Byte). The Device Address identifies which device (of up to 127 addresses on the I²C bus) the Master wishes to communicate with.

After a START condition, the device monitors the first 8 bits received (Device Address byte), and checks for its 7-bit Device Address in the MSBs. If it recognizes the correct Device Address, it ACKs and becomes ready for further communication. If it does not see its Device Address, it sits idle until another START condition is issued on the bus.

Note: The 8th bit (LSB) of the Device Address byte indicates the direction of transfer, READ or WRITE (R/W). A 0 indicates a WRITE operation - the Master transmits data to the RAA215300 (receiver). A 1 indicates a Read operation - the Master receives data from the RAA215300 (transmitter).

5.2 Device Communication Protocol

5.2.1 7-bit Device Addresses

The RAA215300 employs two 7-bit I²C device/slave addresses. One address accesses settings related to the RTC function (RTC Slave Address) - default address **0x6F** (1101111x). Another address accesses the remainder of the device settings (Main Slave Address) - default address **0x12** (0010010x). The LSB is a direction bit, which can be 0 for a WRITE or 1 for a READ, which is not part of the unique 7-bit I²C device address.

Both addresses are programmable in EEPROM with possible values in the range 0x01~0x7F. The two slave addresses can be the same value for single slave address access to the register space.

5.2.2 Register Size

All the device registers contain 8-bit (byte) data. The data is latched-in after the 8th bit (LSB) is received. If a partial data byte is received, that byte is ignored, but any previously acknowledged bytes are accepted.

5.2.3 I²C Write Operation

A Write operation consists of the master sending a START condition, followed by a valid device address byte (R/W bit set to 0), a Register Address Byte, Data Byte, and a STOP condition. After each byte, the device responds with an ACK. The I²C protocol supports burst writing (automatic incrementing of address pointer). After every successfully transmitted data byte, the device automatically increments the internal register address, so subsequent data bytes are written to sequentially incremental register locations. The master must send a STOP condition after sending at least one full data byte and receiving the associated ACK. If a STOP is issued in the middle of a data byte, the Write for that byte is not performed. The basic write transaction structure is shown in Figure 9.





Figure 9. 1-Byte Write to Register M

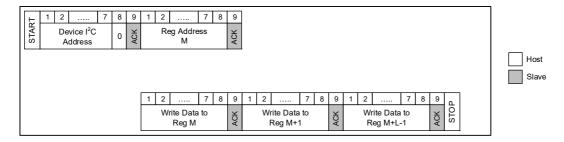


Figure 10. L-Byte Sequential Data Write Starting at Register M

5.2.4 I²C Read Operation

The master sends a START condition, followed by a valid device address byte (R/W bit set to 0), a register address byte, a second (repeated) START, and a valid device address byte (R/W bit set to 1). After each of the three bytes, the device responds with an ACK. The device then transmits data bytes back to the master, and the master ACKs after each byte. The master terminates the Read operation by issuing a NACK and sending a STOP condition.

After every successfully transmitted data byte, the device automatically increments the internal register address, so data bytes are sent out from sequential register locations.

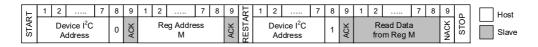


Figure 11. 1-Byte Read to Register M

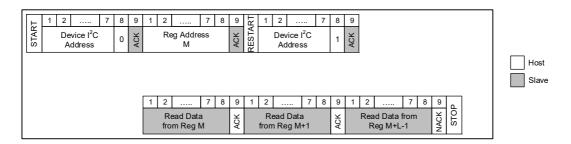


Figure 12. L-Byte Sequential Data Read Starting at Register M

5.2.5 I²C Timing

The timing specifications of the I²C I/O from the I²C specification are shown in Figure 13 and Table 1. The I²C controller provides a slave I²C transceiver capable of interpreting I²C protocol in Standard, Fast, and Fast-mode plus modes.

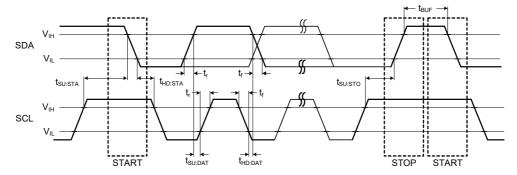


Figure 13. I²C Timing Definitions

Table 1. I²C Timing Characteristics

Parameter	Symbo	Standard Mode		Fast Mode		Fast Mode Plus		Unit
		Min	Max	Min	Max	Min	Max	
SCL Clock Frequency	f _{SCL}	0	100	0	400	0	1000	kHz
Hold Time (repeated) START Condition	t _{HD:STA}	4.0	-	0.6	-	0.26	-	μs
LOW Period of the SCL Clock	t_{LOW}	4.7	-	1.3	-	0.5	-	μs
HIGH Period of the SCL Clock	t _{HIGH}	4.0)	0.6	A	0.26	-	μs
Set-Up Time for a Repeated START Condition	t _{SU:STA}	4.7	-	0.6	-	0.26	-	μs
Data Hold Time ^[1]	t _{HD:DAT}	0	-	0	-	0	-	μs
Data Set-Up Time	t _{SU:DAT}	250	-	100	-	50	-	ns
Rise Time of SDA and SCL	t _r	-	1000	0	300	-	120	ns
Fall Time of SDA and SCL ^{[2][3]}	t _f	-	300	20 x (V _{DD} /5.5V)	300	20 x (V _{DD} /5.5V)	120	ns
Set-Up Time for a STOP Condition	t _{SU:STO}	4.0	-	0.6	-	0.26	-	μs
Bus Free Time Between a STOP and START Condition	t _{BUF}	4.7	-	1.3	-	0.5	-	μs
Capacitive Load for Each Bus Line	C _b	-	400	-	400	-	550	pF
Pulse Width of Spikes that must be Suppressed by the Input Filter	t _{SP}	-	-	0	50	0	50	ns
Input Capacitance for each SDA and SCL	C _i	-	10	-	10	-	10	pF

^{1.} t_{HD:DAT} is the data hold time that is measured from the falling edge of SCL, applies to data in transmission and the acknowledge.

^{2.} V_{DD} = External pull-up voltage.

^{3.} In Fast mode Plus, fall time is specified the same for both output stage and bus timing. If series resistors are used, designers should allow for this when considering bus timing.

5.3 Unimplemented Registers

All register addresses that are defined in the register map ACK write commands and return data to read commands that address them. Unimplemented registers address ACK write commands but data is ignored, and returns a fixed value of 0x00 to read commands.

6. Registers and EEPROM

The RAA215300 features both volatile (RAM/registers) and non-volatile (EEPROM) memory. The volatile value of each register can be set by writing data to the appropriate register using the selected interface, or it can be recalled and loaded from the integrated EEPROM.

When the device enters into {READ_EE}, digital logic loads the pre-programmed EEPROM data into the volatile register space. When all data is loaded successfully, the device does not reload EEPROM data again unless there has been a power cycle, CEN toggle, or software reset command. See Operating {States} and Transition Conditions.

Volatile register data can be written or read back on the fly, as fast as the I²C interface can support.

6.1 EEPROM

The RAA215300 integrates high endurance EEPROM to store all IC configurations. The EEPROM is capable of 1000 plus endurance cycles and 10yrs at 85C of data retention.

6.1.1 Writing to the EEPROM

EEPROM programming is initiated through a control byte register. When setting the write bit to 1 in the control byte (0xFF), all the related non-volatile register data are copied to EEPROM on the subsequent I²C STOP condition. During the EEPROM programming cycle time, the device is internally busy and NACKs to any interface commands, however the buck, LDO outputs, and other IC operations are not halted during the programming time.

When the programming cycle completes, the stored EEPROM data is automatically read back into the register. This provides a way for the host to validate successful programming by reading back the register(s) and comparing it with the value(s) intended to be programmed. If values match, programming was successful. However, if the register data reverts to the previous stored EEPROM value, the EEPROM values were not successfully updated.

6.1.1.1 EEPROM Banks

The RAA215300 EEPROM is partitioned into eight separate banks. All customer banks are (re)programmed each time an EEPROM programming operation commences. For details about each register and bits, see the Register Map.

6.1.1.2 **EEPROM Programming Voltage**

When programming the EEPROM, the minimum voltage requirement must be met:

VPROG ≥ 21V

If the condition is not met, the EEPROM programming operations are not successful. If there was insufficient EEPROM programming or reading voltage, the NVM_Error_Latched and EE_Error_Latched bits are set to 1. The fault flags do not affect the power-on sequencer.

6.1.1.3 Step-by-step EEPROM Programming Instructions

- 1. The device should be in {STANDBY} or onward.
- 2. Write/set up all the required register values (volatile).
- 3. Apply sufficient EEPROM programming cycle voltage to VPROG, see EEPROM Programming Voltage. *Note:* This step can occur before Step 2.



- 4. Set the write bit in the control byte write register address 0xFF[1] = 1. On the subsequent I^2C stop condition, the EEPROM programming cycle commences.
- 5. The system must wait for the maximum t_{EE_WRITE} time to elapse before attempting further interface activity with RAA215300, or making any changes to the supplies as the device is internally busy with programming operations.

6.1.2 Recalling the EEPROM

There are two ways to load EEPROM data to the device volatile registers:

- Automatic Recall: Occurs Operating (States) and Transition Conditions.
- Manual/Software Recall: Issue an I²C reset command to the control byte (register 0xFF).

When the EEPROM is being loaded to the registers, the device is internally busy and NACKs to any I²C commands. When all data is loaded successfully, the RAA215300 does not reload the data unless there has been a new power cycle, toggle of CEN, or software recall command.

6.1.2.1 Valid EEPROM Data Check

During the initial automatic recall, the device provides a safety mechanism to effectively stall the power-on process (sequencer) before any blocks become enabled, and output sequencing starts if it is determined that the EEPROM data has not been programmed or checked by the host. This is accomplished by putting the device into {FAULT_OUT}, which allows the system host to first read back by I²C and initially program the EEPROM data loaded to the registers or confirm loaded data are valid for the application. This helps prevent any undesirable application system behavior. The host can verify this event occurred by reading the fault registers and observing if the NVM_Error_Latched fault and Valid_EE_Data latched fault bits are set to 1. This feature is not enabled if registers 0xD9 - 0xDD are all at zero value.

If the register and/or EEPROM data needs to be changed after the host checks any required register data, the host can make the necessary programming changes. When correct register data is set, the host should clear the NVM_Error_Latched fault by writing 1 to it, which clears both NVM_Error_Latched and Valid_EE_Data bits and releases the device to continue the power-on as determined by PWRON and configuration register settings. This gives the host authority to validate the register settings and specifically control when the device is allowed to start the system.

When the required RAA215300 settings are fixed and programmed to EEPROM (that is, the host no longer needs to validate the data at each power-on), programming register EEPROM_ID_1 or EEPROM_ID_2 to any non-zero value in EEPROM authorizes that the EEPROM data is valid. Therefore, the device no longer enters {FAULT_OUT} and awaits host intervention at subsequent power-on events. *Note:* Reprogramming register EEPROM_ID_1 and EEPROM_ID_2 back to 0x00 value causes the device to enter {FAULT_OUT} at future power-on events.

6.2 EEPROM Error Correction

Data stored in EEPROM is protected by error correction codes (ECC), which allows a single bit error in a given memory bank to be corrected. Each EEPROM bank is covered by its own error correction code.

When a bank of EEPROM is programmed, the error correction code for that bank is automatically generated internally and stored in the same bank. When the EEPROM is recalled, the error correction code is checked, and a correctable (single bit) error is automatically corrected.

Should a single bit correction occur, the EE_Bank#_ECC_Corrected status flag and NVM_Error_Latched bit are set. INT# is asserted. The device still transitions states normally to start up. The host can clear the NVM_Error_Latched fault by writing 1 to it, which clears both NVM_Error_Latched and EE_Bank#_ECC_Corrected bits and de-asserts the INT# output. Two-bit errors in any bank are detected and reported as uncorrectable errors by setting the INT# interrupt event, NVM_Error_Latched bit, and EE_Bank#_ECC_Error status flags. The device ignores the other control inputs (such as PWRON) and enters



{FAULT_OUT}. The host should clear the NVM_Error_Latched fault by writing 1 to it, which clears both NVM Error Latched and EE Bank# ECC Error bits and releases the device to continue the power-on sequence.

6.2.1 ECC Bank Detail Bits

Each RAA215300 memory bank has dedicated ECC bank detail fault bits to uniquely report if a given bank had either an uncorrected, or corrected ECC error occur. These bits do not affect IC operation, they are simply used to provide additional information in the event of ECC operation.

When an ECC error is uncorrected for a given bank # (that is, EEPROM EE_Read_Error interrupt event occurs), a corresponding detail status bit (EE_Bank#_ECC_Error) is set to 1. The EE_Bank#_ECC_Error status bits can be cleared by writing 1 to the NVM Error Latched bit.

When an ECC error is corrected for a given bank #, a corresponding detail status bit (EE_Bank#_ECC_Corrected) is set to 1. The bit(s) can be cleared by the host by writing 1 to the NVM_Error_Latched bit.

7. Power Supplies

The RAA215300 requires one input power supply to power everything. To describe various usage of the power supply, it is helpful to give it various names, but all named parts must be connected together by the PCB. AVDD and VCHG are defined in Pin Descriptions. The input power supply provides power to all voltage regulators, and these connections have various names defined in Pin Descriptions. Connection to the IC is made at many physical locations, identified by name, and each location must have dedicated decoupling capacitance.

7.1 Internal LDO (VIO)

An LDO rejects noise from the VCHG supply and provides a quiet and stable internal supply, VIO, for interface logic.

The LDO is output-compensated and requires a minimum of 1.2µF effective output capacitance, placed close to the VIO pin. See External Component Selection and Device Specific Layout Guidelines.

VIO is enabled as soon as AVDD exceeds its UVLO rising threshold. VIO power-good (VIO_PGOOD) is monitored only after EEPROM is read. The timeout period starts as soon as the FSM enters {WAIT_FOR_VIO}. The timeout period is set by a 2-bit register. See {WAIT_FOR_VIO}.

A register bit is assigned to mask or unmask the VIO_PGOOD signal from INT#. Another register bit shows the status of the VIO power-good fault. When asserted, this fault flag is latched and does not clear automatically. It can only be cleared by writing 1 to the register, hardware reset, or input power cycle.

The VIO LDO is capable of supporting an additional external load of up to 20mA continuously.

7.2 VCHG, VBAT, and VRTC

VRTC is an output that provides power to the RTC. VRTC is generated internally from the higher of VBAT and VCHG. If RTC is used, Renesas recommends placing a capacitor footprint between VRTC and AGND. The capacitor is not populated by default. If RTC is not used, leave VRTC open.

VCHG is the power supply for the coin cell charger and the internal LDO VIO. VCHG must be connected to AVDD, allowing I²C to be operational when the RTC is in battery mode while AVDD remains above its UVLO falling threshold (for example, AVDD = 2.7V, VBAT = 3V). Given that the input thresholds of the I²C signals depend on the VIO supply, which is derived from VCHG, the I/Os are effectively disabled when VIO_PGOOD is LOW (invalid). This could occur when CEN is LOW (the main IC is shut down) if AVDD is below its UVLO level, or when the VIO LDO is powering up.

VBAT can be connected to a coin cell battery or a supercapacitor. VBAT is selected to supply VRTC when VCHG falls below the VBAT voltage - entering battery mode operation. When VCHG rises above (VBAT + VBAT_{HYS}), the system selects VCHG to supply VRTC.



8. Operating (States) and Transition Conditions

The RAA215300 has a finite-state machine (FSM) to execute transitions between various operational states. The following describes those states and the conditions for transitions.

8.1 {RESET}

If AVDD is below its UVLO falling threshold in any state or CEN = LOW in {STANDBY} or {FAULT_OUT}, the device enters {RESET}. In {RESET}, the digital circuit is held in reset, and if CEN = LOW, the device is powered down. When AVDD is above its UVLO rising threshold and CEN = low, the device is in the SHUTDOWN condition.

8.2 {READ_EE}

When AVDD is above its UVLO rising threshold and CEN = HIGH, EEPROM values are read into the registers. When EEPROM reading/loading is successfully completed, the device sets the NVM_Read_Complete latched flag and then transitions to {WAIT FOR VIO}.

Note: There is an error correction system (1-bit error correction and 2-bit error detection) that checks the EEPROM loads correct data. If EE_Bankx_ECC_Error or Valid_EE_Data errors are detected, the state machine sets the NVM_Error_Latched flag bit. If this occurs, the part ignores control inputs (for example, PWRON) and enters {FAULT_OUT}. See Valid EEPROM Data Check and EEPROM Error Correction.

8.3 {WAIT FOR VIO}

{WAIT_FOR_VIO} follows successful {READ_EE}. Providing that AVDD is valid and that CEN is high, on entry to {WAIT_FOR_VIO}, a programmable timer (VIO Timeout) starts, and monitoring of VIO_PGOOD begins. If VIO_PGOOD is asserted before the timer expires, the FSM transitions to {STANDBY} before the end of the timeout period. If VIO_PGOOD is not asserted when the timer expires, the FSM transitions to {FAULT_OUT}.

8.4 {STANDBY}

In {STANDBY}, MPIOx (if configured as inputs) and PWRON are responded to. The I²C interface becomes operational as well. When PWRON is asserted, the FSM enters {STANDBY EXIT}.

8.4.1 {STANDBY EXIT}

The FSM stays in this state until a timer expires (typically around 80µs). When the timer expires, the FSM enters {STANDBY_TO_ACTIVE}.

8.4.2 {STANDBY TO ACTIVE}

In {STANDBY_TO_ACTIVE}, the output rails are turned on if enabled in the register settings, and MPIOx is asserted if configured as outputs in the register settings. MPIOx can also be configured to inputs that control regulator output power-on timing. See Power-ON for details.

8.4.3 {ACTIVE TO STANDBY}

In {ACTIVE}, if PWRON is de-asserted, the FSM transitions to {ACTIVE_TO_STANDBY}. The FSM enters {STANDBY} when the outputs complete the programmed power-off sequence.

8.5 {ACTIVE}

When the output rails and MPIOx complete the programmed power-on sequence, the FSM enters {ACTIVE}.



8.6 {IORESET}

There are three possible causes of the device entering {IORESET}:

- CRST IN# is asserted when CRST Fault EN = LOW
- The watchdog timer expires when WD_PD_EN = LOW
- WD RST EN = HIGH; or Warm Reset = HIGH

The MPIOx reset outputs are asserted immediately. See Warm and Cold Reset for details. While in this state, if PWRON is de-asserted, the device transitions to {ACTIVE_TO_STANDBY}.

8.6.1 {IORESET_TO_ACTIVE}

When reset is complete, the reset register bit is cleared automatically and the device enters {IORESET_TO_ACTIVE}. While in {IORESET_TO_ACTIVE}, if PWRON is de-asserted, the FSM enters {ACTIVE_TO_STANDBY}.

8.7 {SLEEP}

{SLEEP} is a mode of operation with selectable alternative power rails settings. Different output voltages may be set, and the buck regulators can each be set to a different operating mode.

While in {ACTIVE}, if SLEEP# is asserted or the SLEEP_State_EN bit is HIGH, the FSM enters {ACTIVE_TO_SLEEP}.

8.7.1 {ACTIVE TO SLEEP}

There are two output voltage settings for each rail - one for {ACTIVE} and one for {SLEEP}. When entering {SLEEP}, the voltage transitions to {SLEEP} settings following the power-off sequence. If the voltage settings are different for the two states, the voltages ramp up or ramp down according to the programmed DVS slew rate. When slewing of all output voltages completes, the FSM enters {SLEEP}.

8.7.2 {SLEEP TO ACTIVE}

While in {SLEEP}, if SLEEP# is de-asserted or the SLEEP_State_EN bit is LOW, the FSM transitions to {SLEEP_TO_ACTIVE} following the power-on sequence. If the voltage settings are different for the two states, the voltages ramp up or ramp down according to the programmed DVS slew rate. When all output voltage changes complete, the FSM enters {ACTIVE}.

8.8 {FAULT_OUT}

If a fault condition occurs, the FSM enters {FAULT_OUT} after completing the power-off sequence (see Device Monitors, Warnings, and Protections). Depending on the fault type and configured response, the device may turn off all outputs in {FAULT_OUT}. INT# is pulled LOW if not masked from that particular fault. If CEN = LOW, the device enters {RESET}. To exit {FAULT_OUT} and enter {STANDBY}, the fault condition(s) must cease, and all latched fault bits must be cleared by writing 1 to the fault register bit(s).

If the latched fault bit is cleared before all the outputs have finished turning off, the power-up sequence can begin with some outputs already enabled. This behavior can be avoided if necessary by ensuring that there is sufficient delay before clearing the latched fault bit. Alternatively, the cold reset function (Warm and Cold Reset) can be triggered immediately before clearing the latched fault bit to ensure that the power-down sequence completes before powering up again.



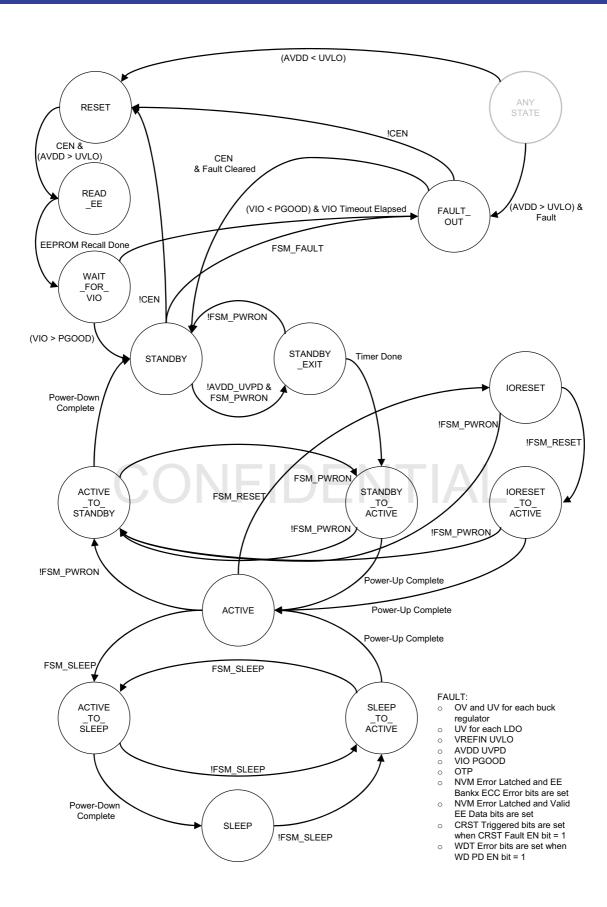


Figure 14. State Diagram

9. Functional Blocks and Application Information

9.1 Chip Enable

The device chip enable (CEN) is an active high, level-sensitive input. When asserted (HIGH), it provides a whole chip enable signal, and when de-asserted (LOW), it disables the device, and all outputs are tri-stated. CEN supports being tied to AVDD. See Electrical Specifications for pin capability.

When asserted, the internal bias circuits power up and check to see if AVDD is above the UVLO threshold. CEN going low in any state where outputs are active causes a sequenced power-down, and a transition to {STANDBY}, then onward to {RESET}.

When the power-off sequence is triggered by CEN going low, a shutdown period starts when the last output is powered off. The shutdown period is set by the maximum Tshutdown setting of the output rails. At the end of the shutdown period, the FSM transitions to {STANDBY} and then {RESET}, which means the on-chip active discharge circuit stops working, and the output capacitors discharge by the external load current.

9.2 PWRON

Power-on (PWRON) is a configurable input offering with an on/off switch or push button support. PWRON polarity is configurable in both on/off switch and push-button mode. When configured as an on/off switch, the input is an active high or low (depending on the polarity setting) level-sensitive input. When configured as a push-button input, the input must be asserted low or high (depending on the polarity setting) for a programmable long duration (in seconds) to internally set the PWRON signal. The supported periods are 1s, 1.5s, 2s, and 3s. A long push button is required for initiating each of the power-on and power-off sequences.

When the internal PWRON signal is asserted, the FSM enters {STANDBY_EXIT}, then onwards to {STANDBY_TO_ACITVE} where it enables the regulators and starts the power-on sequence following the configurations loaded from EEPROM. When the internal signal is de-asserted, all the regulators are powered down, and the MPIOx outputs are asserted following the sequence configured in the register settings.

9.3 Multi Purpose I/O

The RAA215300 includes a set of multiple purpose inputs/outputs (MPIO0~5) with programmable functionalities.

If configured as either a Reset Output, External VR EN Output, or External VR power-good Input, during power-on/off each MPIOx has a power-on/off delay, which is set in MPIOx Power-On and MPIOx Power-Off registers. The power-on and power-off delay can be programmed from 0 to 127ms. The polarity, type, and function of each MPIOx can be configured independently by the MPIOx_Config registers. Each MPIOx can be set to either active low or active high using the register bit MPIOx_Invert. Each MPIOx can be set to general purpose input/output or a specific function. The supported functions for each pin are shown in Table 2. When an MPIOx is set as a general purpose input, its status is read from the MPIO_Input_Status register. When an MPIOx is set as a general purpose output, it can be set to LOW or HIGH using the MPIO_I2C_Output register.

When an MPIOx is set to output, four different types can be selected from register bits MPIOx_Type[1:0]: high impedance, open-drain NMOS output, open-drain PMOS output, or full CMOS output. When set to an open-drain NMOS output, the MPIO needs to be pulled up to an external voltage higher than the VIH threshold through a resistor, but within its allowable operating range. When set to open-drain PMOS output, the MPIO needs to be pulled down to GND through a resistor. When set to full CMOS output, the MPIO does not need an external pull-up voltage as it is pulled up to VIO internally.

It is acceptable to have multiple MPIOx configured with the same function.

The MPIOx configuration registers (0x8A - 0x8F) can be locked by the MPIO Config Lock bit to prevent the user from accidentally changing the MPIOx configurations. When this bit is set to 1, the registers at 0x8A - 0x8F are locked, which means that writing to those registers is ignored. The values in those registers can still be read back. After being set to 1, this bit cannot be set back to 0 until POR.



See the pin mapping shown in Table 2.

Table 2. MPIOx Supported Functions

Function	Туре	MPIO0	MPIO1	MPIO2	MPIO3	MPIO4	MPIO5
Unused MPIOx Pin	-	Yes	Yes	Yes	Yes	Yes	Yes
External VR PGOOD Input	Input	Yes	Yes	Yes	Yes	Yes	Yes
Input to I ² C Register	Input	Yes	Yes	Yes	Yes	Yes	Yes
PGOOD Output	Output	Yes	Yes	Yes	Yes	Yes	Yes
Reset Output	Output	Yes	Yes	Yes	Yes	Yes	Yes
External VR EN Output	Output	Yes	Yes	Yes	Yes	Yes	Yes
Output to I ² C Register	Output	Yes	Yes	Yes	Yes	Yes	Yes
32kHz Clock (32K_CLK)	Output	-	-	Yes	-	-	-
SLEEP#	Input	-	-	-	Yes	-	-
WDT_RST#	Input	-	-	-	-	Yes	-
CRST_IN#	Input	-	-	-	-	-	Yes

9.3.1 Unused MPIOx Pin

If an MPIO is not used, Renesas recommends setting the respective MPIO Type to Disabled (high impedance) and MPIO Function to Disabled in EEPROM. Any MPIO can be disabled. When disabled, it is high-impedance.

If the user does not want to program EEPROM when an MPIO is not used, the MPIO that is configured as an output can be left floating. The MPIO that is configured as an input needs to be connected to a known voltage to ensure it is in the de-assertion state.

9.3.2 External VR PGOOD Input

Any MPIO can be set to perform this function. When asserted, this signal pauses the power-on or power-off sequence timing of the RAA215300, providing a way to sequence the RAA215300 with an external regulator. The expected External VR PGOOD Input delays are set by the applicable MPIO power-on and power-off delays. Only the outputs with delay settings that are larger than the External VR PGOOD Input MPIO delay setting (relative to PWRON) are affected by the assertion or de-assertion of this MPIO input signal.

During power-on, when PWRON is asserted, the External VR PGOOD Input is expected to be asserted by the host within the delay time set in the MPIO Power-On register. If External VR PGOOD Input is not asserted before the MPIO delay expires, the power sequence pauses and waits for the signal to toggle. The delay timers of the outputs start to count when PWRON is asserted and are paused when the External VR PGOOD Input MPIO delay timer expires. When this input is asserted by the host, the power sequence continues. If External VR PGOOD Input is asserted before the MPIO delay expires, the outputs are not paused.

During power-off, when PWRON or CEN is de-asserted, the External VR PGOOD Input is expected to be de-asserted within the delay time set in the MPIO Power-Off register. If External VR PGOOD Input is not de-asserted, the power sequence pauses and waits for the signal to toggle. The delay timers of the outputs start to count when PWRON or CEN is de-asserted and are paused when the External VR PGOOD Input MPIO delay timer expires. When External VR PGOOD Input is de-asserted by the host, the power sequence continues. If External VR PGOOD Input is de-asserted before the MPIO delay expires, the outputs are not paused.

When only one MPIO is set to the External VR PGOOD Input function, the power-on or power-off delay of each output is calculated using Equation 1 where t_x is the delay setting of the output, T is the time when the External VR

PGOOD Input is asserted or de-asserted after PWRON is asserted or de-asserted, and t_{MPIO} is the delay setting of the External VR PGOOD Input.

(EQ. 1)
$$t_{delay} = t_x + max(0, T - t_{MPIO})$$

When multiple MPIOs are set to the External VR PGOOD Input function, the power-on or power-off delay of each output is calculated using Equation 2.

(EQ. 2)
$$t_{delay} = t_x + max(0, T_y - t_{MPIOy}, ..., T_N - t_{MPION})$$

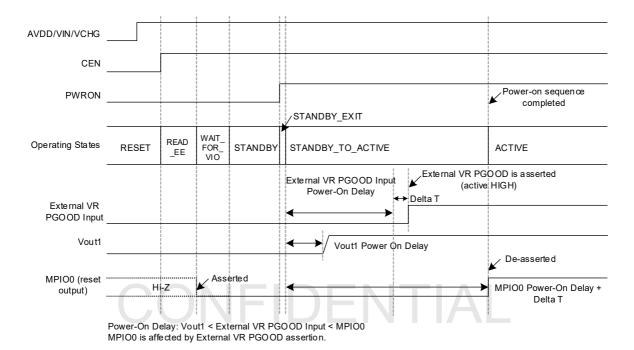


Figure 15. Power-On Example - External VR PGOOD Input

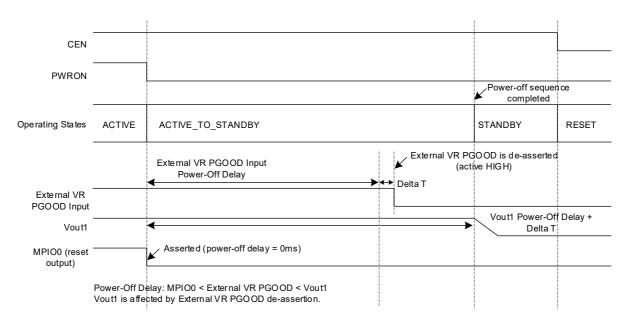


Figure 16. Power-Off Example - External VR PGOOD Input

9.3.3 Input to I²C Register

Any MPIO can be set to support this function. When an MPIO is set to this function, it is a general-purpose input. Its status can be read from the MPIO Input Status register.

9.3.4 PGOOD Output

Any MPIO can be set to support this function. The MPIOx can each be configured to assert PGOOD dependent on the internal power-good signal of a selected rail, or the logical AND of all enabled buck and the power-good signals of the LDO rails. An internal PGOOD signal is asserted when the output voltage is above the PGOOD threshold. PGOOD assertion during power-on signifies the rising threshold has been met, and the soft-start sequence is complete.

When an MPIO is set as a PGOOD output, the MPIO Power-On Delay register bits [3:0] are used to set which regulator output is used for the PGOOD output. In this case, Bits [6:0] in this register are no longer used as a power-on delay.

Note: If any buck or LDO regulator is disabled, and PGOOD output is set to **AND of all regulators PGOOD**, the PGOOD signal is not asserted during power-on. In this case, the PGOOD output needs to be set to another regulator PGOOD.

9.3.5 Reset Output

Any MPIO can be set to support this function. The reset output provides a system reset signal. There can be more than one reset output required in the system, including processor reset (PRST#) and eMMC reset (eRST#). Multiple MPIO can be configured as reset outputs.

The reset output is asserted as soon as the EEPROM recall is completed. During power-on when PWRON is asserted, the reset output is de-asserted after the delay time set in the MPIOx Power-On register. During power-off when CEN or PWRON is de-asserted, the reset output is asserted after the delay time set in the MPIOx Power-Off register.

9.3.6 External VR EN Output

Any MPIO can be set to support this function. This output can be used as an enable signal to control an external regulator power-on/off. It should be configured such that when asserted by RAA215300 the signal enables the external regulator, and when de-asserted it should disable the external regulator.

Any MPIOx with this function is initially de-asserted as soon as the EEPROM recall is completed. During power-on when PWRON is asserted, the VR_EN Output is asserted after the delay time set in the MPIOx Power-On register. During power-off when CEN or PWRON is de-asserted, the VR_EN is de-asserted after the delay time set in the MPIOx Power-Off register.

9.3.7 Output to I²C Register

Any MPIO can be set to support this function. The MPIOx can be asserted HIGH or LOW with software control by setting the related bit in the register.

9.3.8 32kHz Clock (32K_CLK)

Only MPIO2 supports this function. The function provides a driven clock signal output for external devices. The clock frequency is programmable with a maximum setting of 32.768kHz, which is the RTC crystal oscillator frequency. The RTC needs to be enabled by the RTC_EN bit to output this clock signal. If the user does not have an external pull-up voltage, the MPIO2 needs to be configured as a Full CMOS output.

When this function is selected, the MPIO2 Power-Off Delay register Bits [3:0] are used to select the clock frequency. In this case, Bits [6:0] in this register are no longer used as a power-off delay. See the Register Map.



9.3.9 SLEEP#

Only MPIO3 supports this function. This is an edge-triggered, hardware control input to control switching the device between {SLEEP} and {ACTIVE} operating states. The RAA215300 transitions from {ACTIVE} to {SLEEP} (through {ACTIVE_TO_SLEEP}) when SLEEP# is asserted, and transitions from {SLEEP} to {ACTIVE} (through {SLEEP TO ACTIVE}) when SLEEP# is de-asserted.

When MPIO3 is set to other functions, the sleep/active state can be controlled by software using the SLEEP_State_EN bit to control {SLEEP} mode entry/exit. When SLEEP State EN bit = 1, the device transitions to {ACTIVE_TO_SLEEP}, and when SLEEP_State_EN bit = 0, the device transitions to {SLEEP_TO_ACTIVE}. The hardware input and software bit control have a logical OR relationship, see Table 3. To maintain hardware control, the bit should be kept at 0, whereas to maintain bit (software) control the hardware input must internally de-assert the signal (0) as determined by the MPIO3 Invert configuration.

SLEEP# State	SLEEP_State_EN bit setting (0x6C[7])	Selected Operating State
When configured active LOW, MPIO	3_Invert = Active low	
LOW (1)	0	{SLEEP}
LOW (1)	1	{SLEEP}
HIGH (0)	0	{ACTIVE}
HIGH (0)	1	{SLEEP}
When configured active HIGH, MPIO	3_Invert = Active high	
HIGH (1)	0	{SLEEP}
HIGH (1)	1 - 1	{SLEEP}
LOW (0)	0	{ACTIVE}
LOW (0)		{SLEEP}

Table 3. {SLEEP}<->{ACTIVE} Mode Control

9.3.10 WDT RST#

Only MPIO4 supports this function. This is a falling edge triggered input signal. When the watchdog timer is enabled, this signal is used to reset it before the timer expires. If the watchdog timer is disabled, this signal is ignored. See Watchdog Timer for the details.

9.3.11 CRST IN#

Only MPIO5 supports this function. The CRST_IN# input is edge triggered and acts as a hardware reset signal. When the MPIO5_Invert = Active LOW, the signal is asserted on the falling edge of MPIO5. When MPIO5 Invert = Active HIGH, the signal is asserted on the rising edge of MPIO5. The minimum pulse width requirement is 1.5µs (typical) because of internal de-glitching and synchronization to the internal clock. This signal is only valid in {ACTIVE} or {SLEEP}.

When CRST IN# is asserted:

- If currently in {SLEEP}, the RAA215300 enters {ACTIVE}. The device does not enter {SLEEP} until the reset cycle has been completed or the related latched fault has been cleared.
- The CRST_Triggered Latched and CRST_Triggered Live fault bits are set. INT# is pulled LOW if not masked.
- The following occurs if the CRST_Fault_EN bit = Disabled:
 - The RAA215300 enters (IORESET). Any MPIOx configured as reset outputs are asserted immediately.
 - When CRST_IN# is de-asserted by the host, the reset outputs are de-asserted following the configured power-on sequence. The CRST_Triggered fault bits cannot be cleared until CRST_IN# is de-asserted.
- The following occurs if the CRST Fault EN bit = Enabled:



- Any MPIOx configured as reset outputs are asserted and the output rails are shut down following the power-off sequence configured in the register settings. RAA215300 enters {FAULT_OUT}.
- If the latched fault bit is subsequently cleared, the device transitions to {STANDBY}.

Note: Assertion of CRST_IN# is latched until the Sequencer FSM reaches {IORESET}. If CRST_IN# is asserted in {ACTIVE_TO_STANDBY} or {STANDBY_TO_ACTIVE}, the FSM can not reach {IORESET} at that time. The next time the FSM reaches {ACTIVE}, it can act on the latched CRST_IN# assertion, and jumps to {IORESET}.

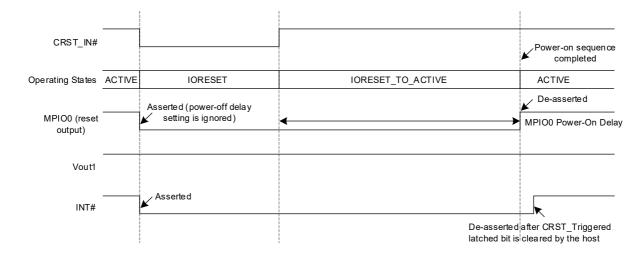


Figure 17. Example of CRST_IN# Operation - CRST_FAULT_EN = Disabled

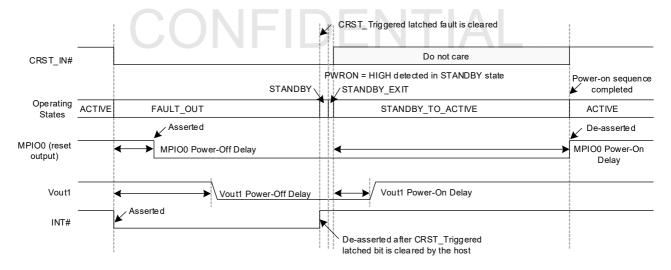


Figure 18. Example of CRST_IN# Operation - CRST_FAULT_EN = Enabled

9.3.12 Alternative Decodes for MPIOx functions

When an MPIO is configured as a PGOOD output, 32K_CLK, or Watchdog Timer Reset (WDT_RST#), the respective MPIOx Power-On Delay or MPIOx Power-Off Delay register bits settings are changed to a different set of decodes which works for this particular function. In this case, Bits [6:0] in this register are no longer used as power-on or power-off delay. See Table 4 for details.

MPIOx and Configured Function	Register Bits	Alternative Settings for the Register Bits
MPIO0 configured as PGOOD output	MPIO0 Power-On Delay register Bits [3:0]	Set which regulator is used for PGOOD output at MPIO0
MPIO1 configured as PGOOD output	MPIO1 Power-On Delay register Bits [3:0]	Set which regulator is used for PGOOD output at MPIO1
MPIO2 configured as PGOOD output	MPIO2 Power-On Delay register Bits [3:0]	Set which regulator is used for PGOOD output at MPIO2
MPIO2 configured as 32K_CLK	MPIO2 Power-Off Delay register Bits [2:0]	Set frequency for the 32K_CLK signal
MPIO3 configured as PGOOD output	MPIO3 Power-On Delay register Bits [3:0]	Set which regulator is used for PGOOD output at MPIO3
MPIO4 configured as PGOOD output	MPIO4 Power-On Delay register Bits [3:0]	Set which regulator is used for PGOOD output at MPIO4
MPIO4 configured as Watchdog Timer Reset	MPIO4 Power-Off Delay register Bits [3:0]	Set timeout period for the WDT
MPIO5 configured as PGOOD output	MPIO5 Power-On Delay register Bits [3:0]	Set which regulator is used for PGOOD output at MPIO5

Table 4. Alternative Decodes for MPIOx Functions

9.4 Watchdog Timer

The WDT starts when the device reaches {STANDBY_TO_ACTIVE}, and is disabled again when the device reaches {STANDBY}. The function can be enabled/disabled in EEPROM.

The WDT feature can be used to detect a system boot-up failure. The function of MPIO4 needs to be set to WDT_RST# and the WD_EN bit needs to be set to 1 to enable this feature. MPIO4 Power-Off register Bits [3:0] are used to set the timeout period when MPIO4 is set to WDT_RST#. Register bits WD_PD_EN and WD_RST_EN are used to set the device behavior when the WDT feature is enabled.

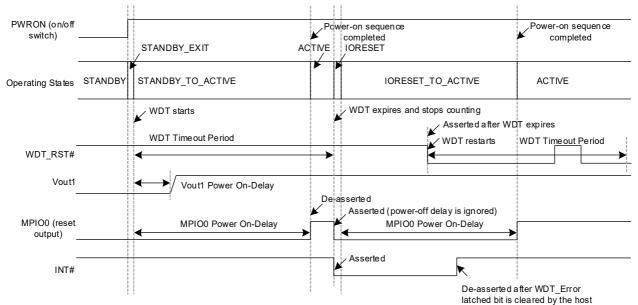
The WDT_RST# input needs to be asserted by the host to reset the timer before it expires. If the watchdog timer expires, the RAA215300 takes the following steps:

- 1. If currently in {SLEEP}, the RAA215300 enters {ACTIVE} through {SLEEP TO ACTIVE}.
- 2. The WDT_Error_Latched and WDT_Error_Live fault bits are set. INT# is pulled LOW if not masked.
- 3. The following occurs if the WD RST EN bit = Enabled, WD PD EN bit = Disabled:
 - a. Any MPIOx configured as reset outputs are asserted immediately. The reset outputs are then de-asserted automatically following the power-on sequence.
 - b. The WDT stops counting when the WDT_Error fault bits are set. It does not start counting until WDT_RST# is asserted by the host. The WDT_Error fault can only be cleared by writing 1 after WDT_RST# is asserted and before the WDT expires again, or after PWRON is de-asserted.
- 4. The following occurs if the WD PD EN bit = Enabled:
 - a. Any MPIOx configured as reset outputs are asserted and the output rails are shut down following the power-off sequence configured in the register settings.
 - b. The WDT stops counting when the WDT_Error fault bits are set. It does not start counting until the WDT Error bit is subsequently cleared by writing 1. The WDT Error fault cannot be cleared until the



power-off sequence finishes and the device enters {FAULT_OUT}. When the fault is cleared, the WDT starts counting (restarts power-on sequence).

Note: If both WD_PD_EN and WD_RST_EN are set to be enabled, the WD_PD_EN bit has higher priority and WD_RST_EN is ignored.



Note: The WDT_Error latched fault can only be cleared by writing 1 to it after a falling edge at WDT_RST# and before the WDT expires again, or after PWRON is de-asserted.

Figure 19. Example of WDT_RST# Operation - WD_RST_EN bit = Enabled, WD_PD_EN bit = Disabled

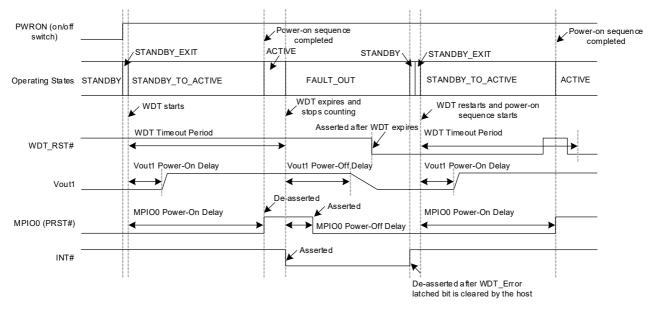


Figure 20. Example of WDT_RST# Operation - WD_PD_EN bit = Enabled

9.5 Power Sequencing

The power sequencing starts when PWRON is asserted in {STANDBY} and the device transitions to {ACTIVE}. The RAA2153000 regulators and MPIOx power-on delays are configured in the EEPROM.

The output voltage of each rail is monitored after it completes soft-start. If there is an undervoltage or overvoltage condition detected, the PGOOD output (if any MPIO is configured to this function) is de-asserted and the device enters {FAULT_OUT} (if these faults are configured to shut down the device).

9.5.1 Power-ON

The power-on delays for all rails are independently programmable from 0~127ms, with a 1ms step. All timing is based on entry to {ACTIVE}.

Each rail has a programmable startup slew rate.

9.5.2 Power-OFF

The power-off delays for all rails are independently programmable from 0~127ms, with a 1ms step. All timing is based on entry to {ACTIVE}.

Each rail has a programmable shutdown slew rate.

9.5.2.1 I²C Trigger Power-Off

The device includes a feature to trigger sequenced power-off operations triggered by an I²C command. Triggering requires sending a specific 8-bit key to the I2C_Trigger_Power_Off_Key bits.

This function is intended for use when the device is configured in long-push button mode, see PWRON.

The following are examples of power-on and power-off sequences in various configurations.

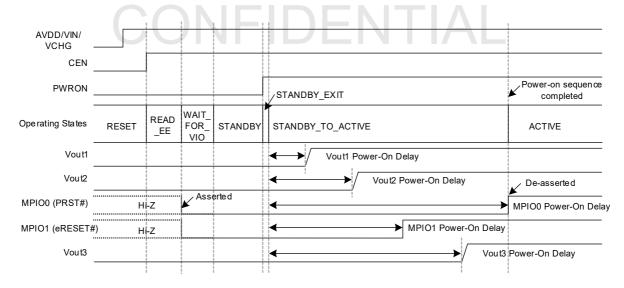


Figure 21. Typical Power-On Example - PWRON as On/Off Switch

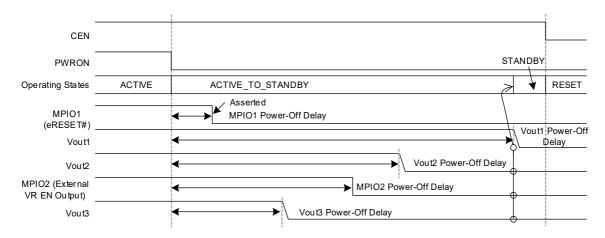


Figure 22. Typical Power-Off Example - PWRON as On/Off Switch

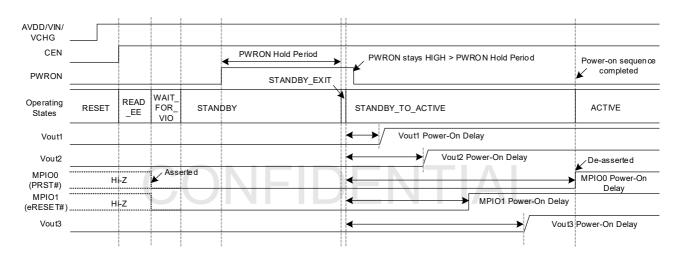


Figure 23. Typical Power-On Example - PWRON as Long Push Button

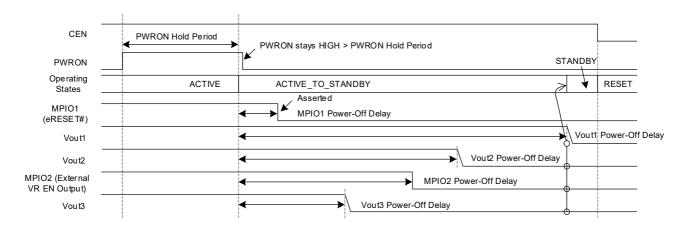


Figure 24. Typical Power-Off Example - PWRON as Long Push Button

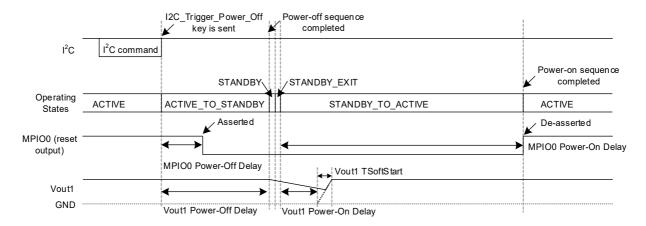


Figure 25. I²C Triggered Power-Off - PWRON = HIGH. PWRON as On/Off Switch, Active HIGH

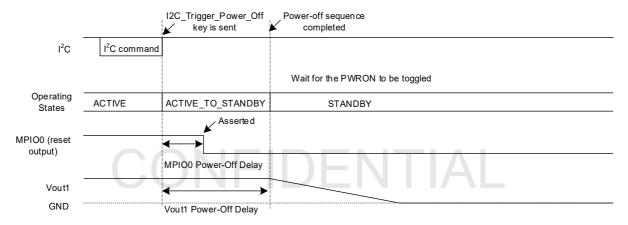


Figure 26. I²C Triggered Power-Off - PWRON = LOW. PWRON as Long Push Button, Active HIGH

9.6 Warm and Cold Reset

The RAA215300 features two types of software-controlled reset functions for controlling the application system (warm reset and cold reset). These resets can be separately triggered by setting the related volatile register bit to 1. Warm and cold reset bits should not be set simultaneously. When the selected reset operation is completed, the bit is automatically cleared to 0 in the volatile register.

The warm reset register bit is used to generate a system reset only. It does not recycle the RAA215300 output power rails. When triggered, the MPIO configured as reset outputs are asserted immediately. The reset signals are then de-asserted following the power-on timing set in their respective MPIOx Power-On Delay register. The LDO SELx status may be changed because of the processor being reset, and the device responds accordingly.

The cold reset register bit generates a system reset and recycles the output power rails. When triggered, the MPIO configured as reset outputs are asserted following their power-off delay settings, and the output rails power down following their programmed sequence settings. When power-down completes, the FSM enters {STANDBY}. After a programmable delay set by the Cold Reset Delay register bits, the output rails are restarted based on their programmed sequence settings. The reset signals are then de-asserted following the power-on timing set in the respective MPIOx Power-On Delay register.

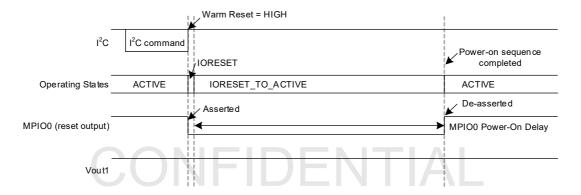


Figure 27. Warm Reset Operation

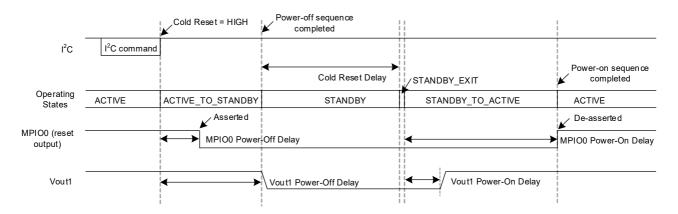


Figure 28. Cold Reset Operation

9.7 Output Discharge

There are four programmable options for the discharge of the buck rails:

- Set the regulator into Forced PWM (FPWM) mode and ramp down the reference following the programmed slew rate.
- Set the regulator into PFM/PWM mode and ramp down the reference following the programmed slew rate.
- Discharge the output rails using programmable discharge resistors. This option disables the regulator, turns the
 discharge switch on, and ramps down the reference following the programmed slew rate.
- Discharge the output rails using programmable discharge resistors. This option disables the regulator and turns the discharge switch on without ramping down the reference first providing a simple RC discharge rate.

There are two programmable options for the discharge of the LDO rails:

- Discharge the output rails using programmable discharge resistors. This option disables the regulator, turns the
 discharge switch on, and ramps down the reference following the programmed slew rate.
- Discharge the output rails using programmable discharge resistors. This option disables the regulator and turns
 on the discharge switch without ramping down the reference first providing a simple RC discharge rate.

During startup, there is no active discharge. Discharge functionality is disabled until after the state machine reaches {ACTIVE} or {ACTIVE_TO_STANDBY}. Active discharge is disabled in {RESET}.

Note: In VTT mode, check that the DDR manufacturer's recommendations are achieved during the discharge of VDDQ (typically Buck2) and VTT (Buck6).

9.8 DVS

The RAA215300 employs dynamic voltage scaling (DVS) to optimize power and efficiency in the system. The DVS features programmable DVS ramp-up/down slew rates for each rail that are applied when the output voltage(s) are changed. The common usage is to change the output voltages between {ACTIVE} and {SLEEP}. Exiting {SLEEP} often occurs to handle a real-time request; therefore, a fast slew rate is often required.

DVS is also used when changing the output voltage during {ACTIVE}. When the new output voltage is written into the register, the DVS block slews the output voltage to the new target based on the programmed rate.

Figure 29 illustrates the DVS between {ACTIVE} <-> {SLEEP} state transitions with delays.

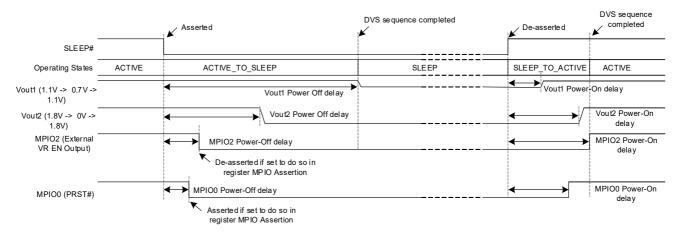


Figure 29. {ACTIVE} <-> {SLEEP} DVS Transition Example

Note: Not all DVS rate setting options (primarily the faster rate options) for the buck and LDO rails may be attainable in certain application configurations and conditions. DVS settings program a target for the rate of change of output voltage. The maximum rate of increase for the output voltage is limited by current limit, load current, and load capacitance. The maximum rate of decrease for the output voltage is limited by load current and

load capacitance. The maximum and minimum rates of increase and decrease in the output voltage can be less than the DVS setting.

9.9 Real-Time Clock

The RTC is functionally the same as the Renesas ISL1208 RTC.

9.9.1 Clock

The RTC is a low-power real-time clock with timing and crystal compensation, clock/calendar, power fail indicator, periodic or polled alarm, intelligent battery backup switching, and battery-backed user SRAM. The oscillator uses either an external, low-cost 32.768kHz crystal or an external clock IC. The real-time clock tracks time with separate registers for hours, minutes, and seconds. The clock format can be set to either AM/PM or 24-hour. There are calendar registers for the date, month, year, and day of the week. The calendar is accurate until 2099, with automatic leap year correction.

The RTC clock/calendar portion is fully operational from 1.8V to 5.5V. See VCHG, VBAT, and VRTC for more details.

The accuracy of the real-time clock depends on the external 32.768KHz crystal or clock IC. The RAA215300 provides on-chip crystal compensation networks to adjust load capacitance to tune the crystal oscillator frequency. See Oscillator Frequency Accuracy for details.

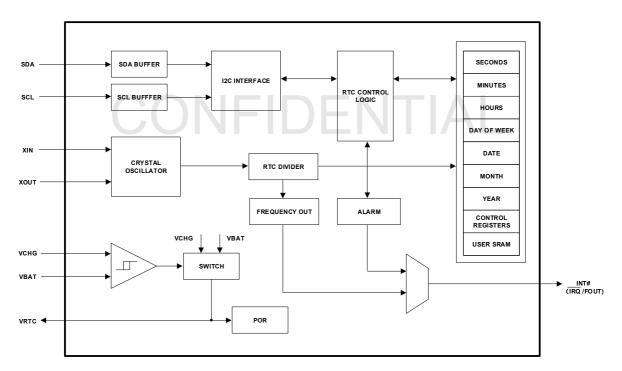


Figure 30. RTC Block Diagram

Note: To activate the RTC, the host must first set the RTC EN bit = 1 and the WRTC bit = 1. If using an external crystal, the XTOSCB bit needs to be set at 0 to enable the crystal oscillator. If using an external clock signal, set the XTOSCB bit as 1 to disable the crystal oscillator. Then, the date and time registers can be set accordingly, and the RTC is clocking and maintaining time. The clock does not increment until at least 1 byte is written to the clock/calendar registers.

INT# is a multi-functional output that can issue an interrupt or frequency signal. The function is selected by frequency out (FO) control bits. In interrupt mode, if an alarm condition occurs, the Interrupt Request (IRQ) is sent to the host processor. In Frequency Output (FOUT) mode, the output is a clock signal at a frequency generated from the crystal frequency.

The I²C interface is not functional if VIO PGOOD is low. See VCHG, VBAT, and VRTC for more details.

9.9.2 Alarm

The flexible alarm of the RTC can be set to any clock/calendar value for a match. For example, every minute, every Tuesday, or at 5:23 AM on March 21. The alarm status is available by checking the Status Register, or the device can be configured to provide a hardware interrupt using INT#. A backup power input (VBAT) allows the device to be powered by a battery or supercapacitor with an automatic switchover between VCHG and VBAT.

The alarm compares the alarm registers with the RTC registers. As the RTC advances, the alarm is triggered when a match occurs. The alarm is enabled by the ALME bit. There are two alarm modes: single-event mode and periodic interrupt mode.

Single-event mode is enabled by setting the ALME bit to 1, the IM bit to 0, and the FO[3:0] bits to 0000. This mode detects a one-time match between the alarm registers and RTC registers. When this match occurs, the interrupt request (IRQ) is sent to the host processor. The ALM bit is set to 1, and the INT# output is pulled low and remains low until the ALM bit is reset.

The periodic interrupt mode allows for repetitive or recurring alarm functionality. This mode is enabled by setting the ALME bit to 1, the IM bit to 1, and the FO[3:0] bits to 0000. There is an alarm each time there is a match of the alarm time and present time. Therefore, there is an alarm as often as every second (if only the nth second is set) or as infrequently as once a year (if at least the nth month is set). During Periodic Interrupt Mode, INT# is pulled low for 250ms, and the alarm status bit (ALM) is set to 1.

Note: The ALM bit can be reset by writing 0 to it or cleared by a valid read operation in the auto reset mode. The alarm function can be enabled/disabled during battery backup mode using the FOBATB bit.

9.9.3 Frequency Output

A clock signal related to the oscillator frequency can output from INT# or MPIO2.

FOUT from INT# is enabled by setting FO[3:0] bits to a non-zero value. The frequency is selected using the I²C bus. See Table 5.

FOUT from INT# (Hz) FO₃ FO₂ F01 FO₀ n 1/2 1/4 1/8 1/16 1/32

Table 5. Frequency Selection of FOUT at INT#

If enabled, a clock signal is outputted from MPIO2(see Table 6). For detailed information about MPIO2 frequency output, see 32kHz Clock (32K_CLK).

Table 6. Frequency Selection of Clock Signal at MPIO2

MPIO2 Power-Off Delay[2:0]	MPIO2 (Hz) - MPIO2 configured as 32K_CLK
000	32768
001	16384
010	8192
011	4096
100	2048
101	1024
110	512
111	256

9.9.4 General Purpose User SRAM

The RTC has 2 bytes of user SRAM, which continue to operate in battery backup mode. However, the I²C bus is disabled if VCHG falls below the AVDD UVLO falling threshold.

9.9.5 Power Control Operation

There are two power supply inputs for the RTC circuit (VCHG and VBAT). The RAA215300 contains internal circuitry to automatically switch over to the backup battery when the main VCHG supply fails and switches back from the battery to VCHG when the main supply recovers. See VCHG, VBAT, and VRTC for details.

9.9.6 Power Failure Detection

The RAA215300 has a Real-Time Clock Failure (RTCF) bit to indicate total power failure. The RTCF bit is read-only and is set to 1 if the RTC has powered up after the failure of both VCHG and VBAT.

The bit is set regardless of whether VCHG or VBAT is applied first. At power-up after a total power failure, all registers are set to their default states, and the clock does not increment until at least 1 byte is written to the clock register. The first valid write to the RTC section resets the RTCF bit to 0.

9.9.7 Crystal Oscillator

A crystal can be used to generate the 32.768kHz clock and provide the time base for the RTC.

9.9.7.1 Oscillator Frequency Accuracy

The oscillator frequency accuracy primarily depends on the crystal accuracy and the match between the crystal and the load capacitance. If the load capacitance is too small or too large, the oscillator is too fast or too slow, respectively. RAA215300 provides an oscillator frequency adjustment mechanism that includes analog compensation in the RTC ATR register and digital compensation in the RTC DTR register. The combination of analog and digital trimming can give a maximum range of adjustment of -80ppm to +130ppm.

Note: Both of the frequency outputs on INT# and MPIO2 are affected by the setting in the RTC ATR register. The frequency on INT# is affected by the RTC DTR setting at all frequencies except the 32.768kHz setting. The frequency on MPIO2 is not affected by the RTC DTR setting.

9.9.7.2 Crystal Oscillator Frequency Trimming

The RAA215300 provides the option of timing correction of the crystal oscillator. Analog and digital compensation mechanisms are available as follows.



9.9.7.2.1 Analog Trimming with On-Chip Load Capacitance

The analog trimming register bits (ATR[5:0]) are used to trim oscillator frequency by selecting on-chip load capacitance. There are six bits for ATR, and the selectable range is from 4.5pF to 20.25pF. The available trim range of the oscillator frequency accuracy in ppm varies with crystals, operating temperature, and the stray capacitance of the PCB. As an example, the available PPM range for an ECX-.327-CDX-1293 crystal is -20ppm to 70ppm measured on the device evaluation board at 25°C.

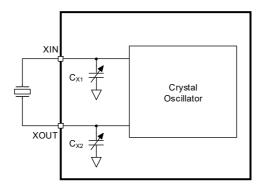


Figure 31. Diagram of On-Chip Load Capacitance

The on-chip load capacitance (C_{LOAD}) is the series combination of C_{X1} and C_{X2} shown in Figure 31. C_{X1} and C_{X2} range from 9pF to 40.5pF. The values of C_{X1} and C_{X2} are given in Equation 3:

(EQ. 3)
$$C_X = (16 \cdot \overline{b5} + 8 \cdot b4 + 4 \cdot b3 + 2 \cdot b2 + 1 \cdot b1 + 0.5 \cdot b0 + 9)pF$$

The series load capacitance (C_{I OAD}) is derived by Equation 4:

(EQ. 4)
$$c_{LOAD} = \frac{1}{\left(\frac{1}{C_{X1}} + \frac{1}{C_{X2}}\right)}$$
$$c_{LOAD} = \left(\frac{16 \cdot \overline{b5} + 8 \cdot b4 + 4 \cdot b3 + 2 \cdot b2 + 1 \cdot b1 + 0.5 \cdot b0 + 9}{2}\right) pF$$

For example, C_{LOAD} = 12.5pF when ATR[5:0] = 00000, C_{LOAD} = 4.5pF when ATR[5:0] = 00000, and C_{LOAD} = 20.25pF when ATR[5:0] = 011111.

9.9.7.2.2 Battery Backup Mode Analog Trimming

The crystal oscillator frequency accuracy can change when the RTC is supplied by different power sources (VCHG or VBAT). The on-chip load capacitance offset between VCHG mode (VRTC supplied by VCHG) and battery backup mode (VRTC supplied by VBAT) is adjustable by BMATR[1:0]. The available range is from -0.5pF to 1pF.

9.9.7.2.3 Digital Trimming

The oscillator frequency is also affected by the digital trimming bits DTR[2:0] in the RTC DTR register. The DTR trim setting modifies the divider stage in the RTC digital block. The available trim range is from -60ppm to +60ppm. It is used for coarse adjustments of frequency drift over temperature or extending the adjustment range provided by the ATR settings.

9.9.7.2.4 Crystal Oscillator Frequency Adjustment

The Initial accuracy of the crystal oscillator can be adjusted by enabling the frequency output on INT# and monitoring it with a calibrated frequency counter. The gating time on the counter should be set long enough to ensure the accuracy of the reading. The ATR[5:0] bits can be set to 000000, to begin with. After the initial measurement is made, the RTC ATR register can be changed to tune the frequency. If the initial measurement



shows the frequency is far off, then the DTR[2:0] can be used to do a coarse adjustment. Most crystal oscillators have tight enough accuracy at room temperature that the RTC ATR register adjustment should be all that is needed.

9.9.7.3 Temperature Compensation

The external crystal temperature drift is progressively worse as the crystal temperature deviates from +25°C. Figure 32 shows an example of temperature drift characteristics. There is a turnover temperature (T0) where the drift is near zero. The shape is parabolic because it varies with the square of the difference between the actual temperature and the turnover temperature.

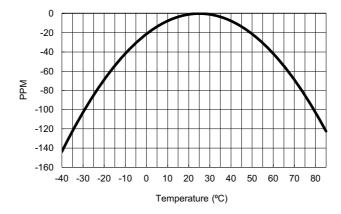


Figure 32. RTC Crystal Temperature Drift Example

A possible system to implement temperature compensation would consist of the RAA215300, a temperature sensor, and a microcontroller. These devices may already be in the system, so the function could just be a matter of implementing software and performing some calculations. Fairly accurate temperature compensation can be implemented just by using the crystal specifications for the turnover temperature T0 and the drift coefficient (β). Equation 5 is used to calculate the oscillator adjustment necessary,

(EQ. 5) Adjustment(ppm) =
$$(T - T_0)^2 * \beta$$

When the temperature curve for a crystal is established, the designer should decide at what discrete temperatures the compensation changes.

A sample curve of the ATR[5:0] setting vs Frequency Adjustment for the RAA215300 and a typical RTC crystal is given in Figure 33. This curve may vary with different crystals and PCBs, so it is good practice to evaluate a given crystal in the RAA215300 circuit before establishing the adjustment values. The curve is then used to determine ATR[5:0] and DTR[2:0] settings. The results could be placed in a lookup table for the micro-controller to access.

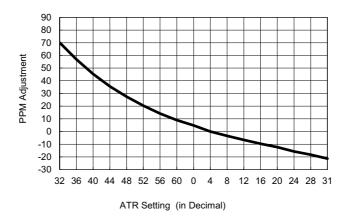


Figure 33. ATR Setting Vs. Crystal Oscillator Frequency Adjustment

9.9.8 Using an External Clock

The RTC can use either a standard 32.768kHz crystal or an external clock. XIN can be programmed for connection to an external clock input using the XTOSCB bit in the RTC SR register. When this bit is set to 1, the oscillator is disabled and XIN is a CMOS-compatible clock input.

The external clock input must be logic level CMOS (0.3 x VBAT LOW, 0.7 x VBAT HIGH), square wave preferred, frequency = 32.768KHz. The clock signal used for the XIN input must come from a source with the same voltage level as the VBAT of the RAA215300 device.

To check if the external clock is working properly, the following methods can be used to check the RTC function:

- Poll the time register to make sure the seconds are advancing at the correct rate.
- Enable the frequency on INT# or MPIO2: Clock and monitor the frequency for the correct value.

9.9.9 Real-Time Clock Registers

9.9.9.1 Clock and Calendar Registers [Address 0x00 to 0x06]

Time is set in BCD format by the following registers:

- RTC SC and RTC MN registers: Sets seconds and minutes that range from 0 to 59.
- RTC HR register: Sets hour that ranges from 0 to 23 or 1 to 12.
- RTC DT register: Sets date that ranges from 1 to 31.
- RTC MO register: Sets month that ranges from 1 to 12.
- RTC YR register: Sets year that ranges from 0 to 99.
- RTC DW register: Sets day of the week that ranges from 0 to 6.

See Register Map Detail for bits decoding.

A 12-hour or 24-hour format can be set by the MIL bit. If it is set to 1, the RTC uses a 24-hour format. If it is set to 0, the RTC uses a 12-hour format. In this case, the HR21 bit functions as an AM/PM indicator with 0 representing AM and 1 representing PM. The clock defaults to a 12-hour format time with HR21 = 0.

February 29 is added for leap years, which are defined as years that are divisible by 4. Years that are divisible by 100 are not considered leap years unless they are also divisible by 400. This means that the year 2000 is considered a leap year by the device, and the year 1900 is not.

9.9.9.2 Control and Status Registers [Address 0x07 to 0x0B]

9.9.9.2.1 RTC Status Register (RTC SR)

This is a volatile register that sets RTC functions and reports status. The following sections detail each bit.



Real-Time Clock Fail Bit (RTCF)

This read-only bit is set to 1 by the device after a power failure where both VCHG and VBAT lose power. After a power failure, all registers are set to their default states when the device powers up again. The host must reactivate the RTC. The first valid write operation to the RTC registers after a power failure resets the RTCF bit to 0.

Battery Bit (BAT)

This bit is set to 1 by the device when the RTC enters battery backup mode. When VCHG is valid again, this bit can be reset either by the host (by writing 0 to it) or automatically reset if ARST = 1.

Alarm Bit (ALM)

This bit is set to 1 if the alarm matches the real-time clock. It can be reset to 0 by the host (by writing 0 to it) or automatically reset if ARST = 1. Writing 1 to this bit is not accepted.

If the ALM bit is set during an RTC SR register reading operation, it remains set after the reading operation is complete.

Write RTC Enable Bit (WRTC)

The WRTC bit enables or disables writing capability into the RTC clock and calendar registers. The factory default setting of this bit is 0. On initialization or power-up, the WRTC bit must be set to 1 to enable the RTC. At the completion of a valid write command (STOP), the RTC starts to count. The RTC internal 1Hz signal is synchronized to the STOP condition during a valid write cycle.

Crystal Oscillator Enable Bit (XTOSCB)

This bit enables/disables the internal crystal oscillator. When XTOSCB is set to 1, the oscillator is disabled, and XIN allows for an external 32.768kHz clock signal to drive the RTC. The XTOSCB bit is set to 0 on power-up.

Auto Reset Enable Bit (ARST)

This bit enables/disables the automatic reset of the BAT and ALM status bits only. When the ARST bit is set to 1, these status bits are automatically reset to 0 after a valid read operation of the respective status register (with a valid STOP condition). When ARST is set to 0, the host must reset the BAT and ALM bits.

9.9.9.2.2 RTC Interrupt Control Register (RTC INT)

This register can be used to control the frequency output and alarm function.

Frequency Out Control Bits (FO[3:0])

These bits enable/disable the Frequency Output function (FOUT) and select the output frequency at INT#. The selectable frequency is listed in Table 5. When the frequency mode is enabled, it overrides the alarm mode at INT#.

Frequency Output and Interrupt Bit (FOBATB)

This bit enables/disables the IRQ/FOUT function during battery backup mode (that is, VBAT power source active). When FOBATB is set to 0, both the Frequency Output and alarm output functions are disabled. When FOBATB is set to 1, the IRQ/FOUT function is enabled during battery backup mode.

Oscillator Bias Current Control Bit (LPMODE)

With LPMODE = 0, the device works with a normal oscillator bias current. With LPMODE = 1, the device works with a reduced oscillator bias current. Renesas does not recommend setting this bit to 1.

Alarm Enable Bit (ALME)

This bit enables/disables the alarm function. When the ALME bit is set to 1, the alarm function is enabled. When ALME is set to 0, the alarm function is disabled. The alarm function can operate in either single-event mode or periodic interrupt mode. See Alarm for more details.



Note: When the frequency output mode is enabled, the alarm function is disabled.

Interrupt/Alarm Mode Bit (IM)

This bit is used to select single-event mode or periodic interrupt mode. See Alarm for more details.

9.9.9.2.3 Trimming Registers RTC ATR and RTC DTR

Analog Trimming (ATR[5:0])

ATR[5:0] bits are used to trim the oscillator frequency by adjusting the on-chip load capacitance value. The on-chip load capacitance value ranges from 4.5pF to 20.25pF in 0.25pF steps. See Analog Trimming with On-Chip Load Capacitance for more details.

Battery Mode ATR Selection (BMATR [1:0])

BMATR[1:0] bits are used to set the on-chip capacitance offset between VCHG mode and battery backup mode. See Battery Backup Mode Analog Trimming for more details.

Digital Trimming (DTR [2:0])

DTR[2:0] bits are used to trim the oscillator frequency by modifying the digital stage in RTC. See Digital Trimming for more details.

9.9.9.3 Alarm Registers Addresses [0x0C to 0x11]

The alarm register bytes are mapped identical to the RTC register bytes, except that the MSB of each byte functions as an enable bit (1 means enabled). These enable bits specify which alarm registers are used to make the comparison. *Note:* There is no alarm byte for year.

The followings are examples of using single-event mode and periodic Interrupt mode.

Example 1 – Alarm set to single-event mode (IM = 0)

A single-event alarm occurs on January 1 at 11:30 am.

Table 7. Register Settings in Example 1

Register Name	Bit 7	Bit 6	Bit 5	Bit 4	Bit 3	Bit 2	Bit 1	Bit 0	Value	Description	
RTC SCA	0	0	0	0	0	0	0	0	0×00	Seconds disabled	
RTC MNA	1	0	1	1	0	0	0	0	0×B0	Minutes set to 30, enabled	
RTC HRA	1	0	0	1	0	0	0	1	0×91	Hours set to 11, enabled	
RTC DTA	1	0	0	0	0	0	0	1	0×81	Date set to 1, enabled	
RTC MOA	1	0	0	0	0	0	0	1	0×81	Month set to 1, enabled	
RTC DWA	0	0	0	0	0	0	0	0	0×00	Day of week disabled	
RTC INT	0	1	X ^[1]	X[1]	0	0	0	0	0×X0	Enable single-event mode	

^{1.} X can be set to either 0 or 1 depending on the application.

After these registers are set, an alarm is generated when the RTC advances to exactly 11:30 am on January 1 (after seconds change from 59 to 00) by setting the ALM bit in the status register to 1 and also pulling the INT# output low.



Example 2 – Alarm set to periodic interrupt mode (IM = 1)

An interrupt occurs every minute when the value of the RTC SC register is at 30 seconds.

Register Name	Bit 7	Bit 6	Bit 5	Bit 4	Bit 3	Bit 2	Bit 1	Bit 0	Value	Description
RTC SCA	1	0	1	1	0	0	0	0	0×B0	Seconds set to 30, enabled
RTC MNA	0	0	0	0	0	0	0	0	0×00	Minutes disabled
RTC HRA	0	0	0	0	0	0	0	0	0×00	Hours disabled
RTC DTA	0	0	0	0	0	0	0	0	0×00	Date disabled
RTC MOA	0	0	0	0	0	0	0	0	0×00	Month disabled
RTC DWA	0	0	0	0	0	0	0	0	0×00	Day of week disabled
RTC INT	1	1	X ^[1]	X ^[1]	0	0	0	0	0×X0	Enable periodic interrupt

Table 8. Register Settings in Example 2

When the registers are set, the following waveform is seen at INT#. The status register ALM bit is set each time the alarm is triggered and is cleared automatically.

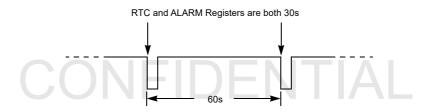


Figure 34. Periodic Interrupt Alarm Signal

9.10 Coin Cell Battery Charger

RAA215300 features a constant current charger to charge an external backup energy storage device to maintain power to the RTC when the VCHG supply falls. A typical energy storage device is a coin cell battery or supercapacitor connected to VBAT. The charger charges the external storage device when VCHG is higher than VBAT.

The charger is always off by default (after power-on or device reset) and must be enabled by I²C.

The charger supports selectable $20\mu\text{A}$ or $60\mu\text{A}$ (typical) charge currents. If the charger is enabled and VCHG is higher than VBAT, the charge current is supplied through VBAT. The charging termination voltage is selectable by $I^2\text{C}$ from $1.8\text{V}\sim3.3\text{V}$ in 100mV steps.

The device does not automatically re-enable the charger when the voltage on the external storage device falls. The host should monitor the PGOODCCBAT fault bits (poll the register using I²C) to decide if and when the charger needs to be re-enabled to charge up the external storage device.

The battery sense comparator is disabled by default, and the PGOODCCBAT live bit stays at 0. The sense comparator is automatically enabled when the charger is enabled. The host can check the battery status by trying to enable the charger (writing 1 to CC Charger EN bit) every certain period of time (depending on the battery backup time), and the following occurs when the device receives the command:

• If VBAT voltage is above or at the target level (charging termination voltage), the charger is not turned on and CC Charger EN bit remains at 0.



^{1.} X can be set to either 0 or 1 depending on the application.

 If VBAT voltage falls below the target level, the comparator and charger are enabled. The PGOODCCBAT live and latched bits are set. INT# is asserted if not masked.

The PGOODCCBAT latched bit can be cleared by writing 1 to it. This bit is edge sensitive. When cleared, it does not set until the next time VBAT falls below the target level. When VBAT reaches the target level, the charger and comparator are automatically disabled, and the PGOODCCBAT live bit is cleared, indicating VBAT PGOOD was attained.

9.10.1 Supercapacitor Backup Time

The supercapacitor backup time is calculated using Equation 6 where C_{BAT} is the capacitance value of the supercapacitor, V_{BAT1} is the battery voltage level when it is fully charged, V_{BAT2} is the voltage level when the battery needs to recharge, and I_{BAT} is the supply current drawn from the supercapacitor.

(EQ. 6)
$$T_{Backup}(seconds) = C_{BAT} \times \frac{V_{BAT1} - V_{BAT2}}{I_{BAT}}$$

For example, if C_{BAT} = 0.1F, V_{BAT1} = 3.3V, V_{BAT2} = 1.8V, and I_{BAT} = 5µA when RTC is clocking, the battery backup time is 30000 seconds which equals 8.33 hours, which means that the host needs to check the battery status every 8 hours.

Charging time is calculated using Equation 7 where I_{Charge} is the charge current set in the register.

(EQ. 7)
$$T_{Charge}(seconds) = C_{BAT} \times \frac{V_{BAT1} - V_{BAT2}}{I_{Charge} - I_{BAT}}$$

In the previous example, if I_{Charge} = 60 μ A, the charge time is 2727 seconds which equals 0.76 hours.

9.11 Buck Regulators

The RAA215300 has six synchronous buck regulators. Internal compensation is employed to simplify application design, reduce PCB space, and reduce the BOM cost. Each buck regulator has its own programmable output range, soft-start, power-up/down timing, switching frequency, and can be individually disabled by the register and EEPROM settings. Some of the buck regulators are optimized to support various DDR memory specifications but can also be used for general purposes. The buck regulators have various output voltage ranges and current ratings, allowing the system to be flexibly designed for improved performance, such as efficiency and voltage ripple. The buck regulators can be automatically reconfigured (by register settings) between {ACTIVE} and {SLEEP} for different applications or different power requirements.

The buck regulators have two operating modes: Auto PFM/PWM and FPWM. Each buck regulator can be set to the ultrasonic mode when operating in PFM (see <u>Ultrasonic Mode</u>) and can use a spread spectrum feature (see <u>Spread Spectrum</u>). A synchronous phase delay feature allows the switching of each buck regulator to be shifted in phase relative to the internal clock, which may improve EMC.

The buck regulators support Dynamic Voltage Scaling (DVS) with programmable ramp-up/down rates (see DVS), and offer various active discharge options (see Output Discharge). Various warnings and faults are monitored and reported (see Device Monitors, Warnings, and Protections).

Note: All buck supplies (BUCKx VINx) = AVDD = VCHG.

9.11.1 Buck1

Buck1 supports the processor or SoC core power. It provides high efficiency, fast load transient response, and low ripple voltage. It can provide up to 5A. The output voltage can be set to 1.03V, and from 0.8V to 1.5Vin 50mV steps. *Note:* The switching frequency should be reduced when using outputs 1.03V and lower.

Buck1 supports high-current warning interrupt if the output current exceeds the programmable Buck1 High Current Threshold. It can be used as an early indicator for system thermal control. It is particularly helpful during the system design phase.



Buck1 configuration details are in registers 0x20 to 0x26.

9.11.2 Buck2

Buck2 supports DDR memory VDDQ rail. It can provide up to 1.5A. The output voltage can be set from 1.1V to 1.85V, in 50mV steps. If Buck2 powers DDR memory and VTT is required, connect VREFIN to the Buck2 output rail externally.

Buck2 configuration details are in registers 0x27 to 0x2D.

9.11.3 Buck3

Buck3 can provide up to 1.5A. The output voltage can be set from 1.8V to 3.3V, in 100mV steps. It can be used to power 1.8V or 3.3V I/O or other loads.

Buck3 configuration details are in registers 0x2E to 0x34.

9.11.4 Buck4

Buck4 can provide up to 3.5A. The output voltage can be set to 0.8V, 0.85V, 0.9V, 0.95V, 1.0V, 1.05V, 1.1V, 1.15V, 1.2V, 1.5V, 1.6V, 1.8V, 1.85V, 2.2V, 2.5V, or 3.3V. It can be used to power 1.8V or 3.3V I/O or other general loads. *Note:* Reduce the switching frequency when using outputs 1.6V and lower.

Buck4 configuration details are in registers 0x35 to 0x3B.

9.11.5 Buck5

Buck5 is a regulator for system peripherals such as WiFi or Ethernet. It can provide up to 0.6A. The output voltage can be set to 1.2V, 1.5V, 1.6V, 1.8V, 1.85V, 2.2V, 2.5V, or 3.3V. It can support up to 0.6A for outputs lower than 2.5V. When the set output voltage is 2.5V or 3.3V, the maximum load current capability derates.

Buck5 configuration details are in registers 0x3C to 0x42.

9.11.6 Buck6

Buck6 supports DDR VTT, which is required to sink (receive) and source (supply) currents up to ±1A. When the VTTREF EN bit = 1, Buck6 is configured for the DDR VTT application (VTT mode). The output voltage tracks the VREFIN input and the output voltage is fixed at VREFIN/2. The power-up/down sequence tracks the VREFIN per DDR memory specification. *Note:* Sink and source currents derate when the output voltage is 0.7V and higher. Also, sink currents and/or maximum input voltage derate when the output voltage is 0.575V or lower.

Buck6 configuration details are in registers 0x43 to 0x49.

9.11.7 Buck Operating Modes

The operating mode (Auto PFM/PWM and FPWM) is set by the Buckx_ACTIVE and Buckx_SLEEP registers.

In Auto PFM/PWM mode, the buck regulator transitions between PFM and PWM modes depending on load current. At light load, it enters PFM to reduce power consumption. As load current increases, the regulator transitions to PWM. PFM mode produces higher output voltage ripple than PWM mode. FPWM produces the lowest output voltage ripple at light load but it increases quiescent current.

FPWM mode makes the regulator operate at a fixed switching frequency, as programmed in EEPROM, irrespective of the load current. At light load, there is a negative inductor current (the current flows from output capacitance, through the inductor and low-side switch).

All bucks soft-start in PFM/PWM mode, irrespective of the mode setting. After soft-start completion, if selected, the device transitions to FPWM 300µs. The regulator is unable to create a negative inductor current until FPWM mode is established.



9.11.8 Ultrasonic Mode

Ultrasonic mode is an optional feature (set in EEPROM) of each buck regulator. Its purpose is to prevent PFM switching frequency from being within the audio frequency band.

9.11.9 Unused Buck

If a buck regulator is not required in a given application, configure that unused buck as follows:

- BUCKx VINx = Always connect to the same supply as AVDD
- BUCKx_LXx = Open
- BUCKx FB = GND
- Disable the BUCKx block in EEPROM by both Buckx EN ACTIVE and Buckx EN SLEEP bits.

A UV fault is triggered at startup if a buck regulator is enabled in the register settings but configured as unused on the board. The fault protection function is configured in the default settings to shut down all the outputs when a UV fault is detected. To avoid shutdown, disable the unused bucks in the EEPROM settings or before asserting PWRON.

When VTTREF_EN = Enabled and the register bit Link_Buck6_to_Buck2 is set to 1, Buck6 and Buck2 start up and shut down simultaneously, and settings of the following register bits are ignored: Buck6_EN_ACTIVE, Buck6_EN_SLEEP, Buck6_Power_On_Delay, and Buck6 Power_Off_Delay. When Link_Buck6_to_Buck2 is set to 0, sequencing of Buck6 and Buck2 is independent.

If VTTREF EN = Enabled and Buck6 is unused, Link Buck6 to Buck2 must be set to 0.

9.11.10 Switching Frequency

The PWM switching frequency (f_{SW}) for each buck is programmable. Changing this setting on the fly using I²C is not recommended. It is preferred to change the frequency only when the output is disabled, or before PWRON assertion. See the Register Map for the available options for each regulator and default selections.

At the load where control changes from PFM to PWM, the switching frequency is not as high as its setting. As load increases, the switching frequency increases. The setting is a maximum.

9.11.11 Spread Spectrum

To improve EMC, spread spectrum operation is optional in each buck regulator. The switching frequency is modulated to reduce peak noise power.

9.11.11.1 PFM mode

The switching frequency depends on load current and peak switch current limit. A 10-bit pseudo-random pattern is applied to the peak switch current limit code to modulate the PFM switching frequency. The PFM spread spectrum modulation rate is adjusted using the 2-bit code Buck#_PFM_AM[1:0].

Each buck regulator has a bit to enable/disable PFM spread spectrum operation.

9.11.11.2 PWM Mode

There are two spread spectrum modulation schemes in PWM mode: pseudo-random and triangular, set by the SS_PWM_Mod bit. The 2-bit code PWM_AM[1:0] sets the amplitude of modulation. The PWM_AM bits can also be set to disable the PWM spread spectrum. The selected modulation scheme and modulation amplitude are applied to all buck regulators.

The pseudo-random scheme is implemented similarly to PFM spread spectrum modulation, but instead of modulating PFM current limit it directly modulates switching frequency. The modulation frequency is set by the 2-bit code Freq_SS[1:0]. The modulation rate is adjusted using the 2-bit code PWM_AM[1:0].



When the triangular modulation profile is selected, the PWM switching frequency is the center frequency (f_{CENTER}). A maximum frequency (f_{MAX}) and minimum frequency (f_{MIN}) are adjusted by the modulation amplitude 2-bit code PWM_AM[1:0]. The modulation frequency (f_{MOD}) is set by the 2-bit code Freq_SS[1:0].

9.11.12 Phase Synchronization

The phase relationships between the starts of switching cycles of different buck regulators can be programmed. The programmed switching frequencies of synchronized buck regulators must be the same, double, or half. When programmed, synchronization occurs when the buck regulators are running at the full switching frequency, which occurs at all loads in FPWM mode and at moderate to high load in Auto PFM/PWM mode. Phase synchronization can be used to improve EMC.

9.12 LDO Regulators

The RAA215300 has three LDO regulators, each with programmable output voltage, soft-start timing, and power on/off delay. Each can be disabled by the register and EEPROM settings. The LDOs support various DDR memory specifications, but can also be used for general purposes. The LDOs can be reconfigured by programmed settings during transitions between {ACTIVE} and {SLEEP}. In {ACTIVE}, hardware inputs (see LDOx Selection Inputs) can change the output voltages of LDO1 and LDO2 at rates determined by DVS settings and limitations caused by current limit, load current, and load capacitance.

DVS settings program a target for the rate of change of output voltage. The maximum rate of increase of output voltage is limited by current limit, load current, and load capacitance.

The maximum rate of decrease of output voltage during DVS is limited by load current and load capacitance.

The maximum rates of increase and decrease in the output voltage can be less than the DVS setting.

The LDO regulators offer various active discharge options (see Output Discharge) at power-off. Various types of LDO regulator faults are monitored and reported, see Device Monitors, Warnings, and Protections.

The maximum rate of decrease of output voltage during a shutdown is limited by load current, load capacitance, and active discharge setting.

9.12.1 LDO1/2

LDO1 and LDO2 use the same design. The output voltages can be set to 0.8V, 0.9V, 1.2V, 1.5V, 1.8V, 2.5V, 3.0V, and 3.3V. The output voltages for {ACTIVE} and {SLEEP} are separately programmable. These LDOs support SD card interface applications.

- LDO1 configuration details are in registers 0x4A to 0x4E.
- LDO2 configuration details are in registers 0x4F to 0x53.

9.12.1.1 LDOx Selection Inputs

The LDO_SELx inputs can be used to change the output voltages while in {ACTIVE}. For example, this can be useful when the LDOs power an SD card interface.

- When LDO_SELx = HIGH, the LDOx_Vo_1_ACTIVE setting is selected.
- When LDO SELx = LOW, the LDOx Vo 0 ACTIVE setting is selected.

LDO_SELx inputs are ignored during {SLEEP}, when powering on, or during transitions from {STANDBY} to {ACTIVE}.

9.12.2 LDO3

LDO3 output voltage can be set to 0.8V, 0.9V, 1.2V, 1.5V, 1.8V, 2.5V, 3.0V, and 3.3V. The output voltages for {ACTIVE} and {SLEEP} are separately programmable. LDO3 can provide power for the DDR memory VPP rail.



9.12.3 LDOx Bypass

Each LDO can be set in bypass mode where the input and output are internally connected through the enhanced pass MOSFET.

The LDO cannot be switched in or out of bypass mode between {ACTIVE} and {SLEEP}.

9.12.4 Unused LDOx

If an LDO regulator is not required in a given application, configure that unused LDO as follows:

- LDOx_VIN = GND
- LDOx OUT = GND
- LDO_SEL1 = GND if LDO1 is not used
- LDO SEL2 = GND if LDO2 is not used
- Disable the LDOx block in EEPROM by both LDOx EN ACTIVE and LDOx EN SLEEP bits.

A UV fault is triggered at startup if an LDO is enabled in the register settings but configured as unused on the board. The fault protection function is configured in the default settings to shut down all the outputs when a UV fault is detected. To avoid shutdown, disable the unused LDOs in the EEPROM settings or before asserting PWRON.

9.13 VTTREF

The VTTREF block provides the VTT reference voltage in DDR applications. VREFOUT = VREFIN/2.

In DDR applications, VREFIN is connected to the VDDQ rail, which is typically generated by Buck2.

When Buck6 is set to VTT mode, Buck6 output provides an active tracking termination voltage (VTT) equal to VREFOUT.

If VTTREF_EN = Enabled, VTTREF is enabled when Buck2 starts up and is disabled when Buck2 shuts down. VREFIN (the input to VTTREF) can be connected to the output of any of the regulators, or to any voltage source. VREFIN UVLO detection is active only after Buck2 completes soft-start and before Buck2 starts power-down.

When VREFIN UVLO is active, UVLO latched fault and live fault bits are set and all outputs shut down if VREFIN is less than its falling UVLO threshold for longer than the VREFIN UVLO Falling Delay period. See VREFIN UVLO.

VTTREF is enabled and disabled simultaneously with Buck2. Therefore, Buck6 must not start up earlier than Buck2 and must not shut down later than Buck2. During startup, VREFIN must be greater than two times the Buck6 output voltage, or Buck6 OV could be triggered. Many things affect the rise times. In FPWM, constraints of minimum on-time and switching frequency can make Buck6 output voltage rise quickly. Therefore, it is necessary to make VREFIN establish quickly or before Buck6. During shutdown, the voltage source connected to VREFIN cannot shut down earlier than Buck6, or Buck6 OV could be triggered.

9.13.1 Unused VTTREF

If VTTREF is not going to be configured for use as a reference for Buck6, configure the schematic and board design as follows:

- VREFIN = GND
- VREFOUT = GND
- Disable the VTTREF block in EEPROM.

9.14 Pre-bias Startup

In some use cases, the output capacitor/load of the regulator may have residual charge and therefore a non-zero output voltage when the device is (re)started (that is, pre-biased). The RAA215300 supports pre-biased start-up.



9.15 Device Monitors, Warnings, and Protections

The RAA215300 has various monitors, warnings, and fault protection features.

If a fault is detected during normal operation, both a latched (sticky) and a live fault status bit are set. INT# is asserted if the fault interrupt is supported and not masked out. Certain fault events can be configured to shut down all rails (enter {FAULT_OUT}), or to keep all rails operating (do not enter {FAULT_OUT}). A latched fault bit remains set until cleared by the host writing a 1 to the latched register bit after the event has subsided. The live status bits show the real-time condition and are used to indicate if the fault has subsided or persists. For more information see Interrupt and Fault and Status Monitoring.

If a fault event shuts down the RAA215300 power rails, all the reset outputs are asserted and the output rails are powered down following the power-off sequence.

9.15.1 Input Voltage Monitor (AVDD Undervoltage Power Down)

To help prevent uncontrolled power-down due to input power loss, an AVDD voltage monitor option is included to provide the host an early warning. It is also called the AVDD Undervoltage Power Down (UVPD) feature, which has a programmable threshold and can be enabled/disabled in the EEPROM. When the programmed threshold is reached, after a delay the AVDD_UVPD_Latched and AVDD_UVPD_Live status bits are set and, if not masked, INT# is asserted. The device powers down according to the power-down sequence and then enters {FAULT_OUT}. At power-on, the device remains in {STANDBY} until AVDD exceeds the UVPD setting if the AVDD UVPD feature is enabled, and stays in this state indefinitely if AVDD remains below its UVPD setting.

The threshold options are:

- 4.25V (for 5V systems)
- 3.0V (for Li-Ion battery systems)
- 2.7V (for 3V systems)

9.15.2 AVDD UVLO

The AVDD input supply has UVLO protection. This checks the power supply is valid for normal operation. See the Electrical Specifications for detailed specifications. When AVDD is below its UVLO falling threshold, the device enters {RESET}. See Operating {States} and Transition Conditions for more details.

9.15.3 VREFIN UVLO

The VREFIN input has UVLO protection. When VREFIN is below its UVLO falling threshold, after a delay the VREFIN_UVLO_Latched and VREFIN_UVLO_Live fault bits are set and, if not masked, INT# is asserted. The device powers down according to the power-down sequence if it is configured to shut down all the rails by the VREFIN_UVLO_Disable bit and then enters {FAULT_OUT}.

Note: The device can be configured to either shut down all the rails or not shut down any rails by register bit VREFIN_UVLO_Disable. If the device is configured to not shut down any rails, the fault cannot be cleared until VREFIN exceeds its UVLO rising threshold. If the device is configured to shut down all the rails, the fault cannot be cleared until the power-off sequence completes.

The VREFIN UVLO Falling Delay timer is enabled after Buck2 finishes soft-start and before Buck2 starts shutdown.



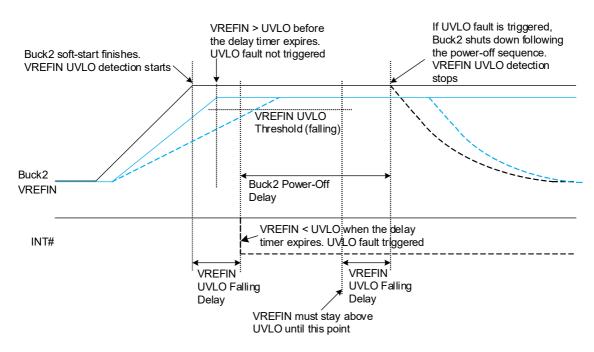


Figure 35. VREFIN UVLO Fault Detection at Power-On

9.15.4 Over-Temperature Warning and Protection

The RAA215300 continuously monitors its die temperature and responds at two thresholds. The lower threshold provides a warning that the temperature is near but less than the higher protection threshold.

The thermal warning threshold is programmable. When the warning threshold is reached, a latched fault flag and live status bit are set and if not masked, it asserts INT#. When the thermal shutdown threshold is reached, a latched fault flag and live status bit are set, INT# is asserted (if not masked), and the device powers down following the power-off sequence and it enters {FAULT_OUT}.

Note: OTP_WARN_Latched fault is edge triggered, that is, when the latched fault is cleared, it is only set again when the live fault goes LOW to HIGH. OTP_Latched fault is level triggered, that is, when the latched fault is cleared, it is set again if the live fault is high.

9.15.5 High Current Warning

Buck1 features a high-current warning with a programmable threshold. This can be used by the system, possibly in conjunction with the over-temperature warning, to moderate processor activity to avoid high-temperature operation. When Buck1 output current is higher than the threshold set in Buck1_High_Current_Threshold register bits, the Buck1_HC_Latched and Buck1_HC_Live bits are set, and INT# is asserted (if not masked). The device remains operating in this condition.

9.15.6 Overvoltage and Undervoltage Protection

All buck regulators have undervoltage (UV) and overvoltage (OV) fault protection. The LDOs have UV protection. PMIC response to a fault is configurable and can include assertion of INT#. When UV or OV protection threshold is reached, a latched fault flag and live status bit are set, and INT# is asserted (if not masked). If the UV_Disable or OV_Disable bit of the regulator is configured to shut down all the rails, the device powers down following the power-off sequence and enters {FAULT_OUT}. If it is configured to not shut down any rails, the device remains operating.

Note: The LDOx live status bits are PGOOD live status, and they are monitored when the related LDO is enabled and disabled. The LDOx latched status bits are UV latched status and are only monitored when the related LDO is enabled. Similarly, the BUCKx UV and OV status are only monitored when the related buck regulator is enabled. The INT# status depends on the latched fault status.



9.15.7 Interrupt

The RAA215300 has an interrupt (INT#) pin, which is an open-drain, active low output that can notify the system/host of a PMIC fault or alarm condition. Each latched fault can be configured to be unmasked or masked with respect to INT#. Unmasked faults assert INT#; masked faults do not. *Note:* The host can read latched and live faults from the status registers.

It is the responsibility of the host to de-assert/release INT# by clearing the latched fault bit(s). If INT# is not de-asserted, it is unable to notify the host of further qualifying events.

9.15.8 Fault and Status Monitoring

The RAA215300 supports numerous interrupt qualifying events and numerous status flags. Different fault events may have associated latched flags, live flags, and the ability to assert the INT# and power down all outputs (enter {FAULT_OUT}).

Note: Latched and live fault bits can be polled by the host at any time to check status. A latched fault sets the related flag to 1, and this remains until cleared by the host. The fault is re-triggered if the fault condition persists.

See Table 9 for a summary of all fault and status flags, see the Register Map for all details of the bits summarized.

Table 9. Fault and Status Flags: Behavior and Partitioning

Fault Register Partitioning	Fault/Status Name	Live Bit Status	Latched Bit Status	INT# Mask Option	Fault Response Option	Deglitch Time (ms)	Notes
	Buck6 UV	Yes	Yes	Yes	Yes	1	
	Buck5 UV	Yes	Yes	Yes	Yes	1	
Fault 1	Buck4 UV	Yes	Yes	Yes	Yes	1	
rault i	Buck3 UV	Yes	Yes	Yes	Yes	1	
	Buck2 UV	Yes	Yes	Yes	Yes	1	_
	Buck1 UV	Yes	Yes	Yes	Yes	1	
	VIO_PGOOD	Yes	Yes	Yes	No	1	
Fault 2	LDO3 UV	Yes	Yes	Yes	Yes	1	
rauil 2	LDO2 UV	Yes	Yes	Yes	Yes	1	
	LDO1 UV	Yes	Yes	Yes	Yes	1	
	Buck6 OV	Yes	Yes	Yes	Yes	1	
	Buck5 OV	Yes	Yes	Yes	Yes	1	
F# 0	Buck4 OV	Yes	Yes	Yes	Yes	1	
Fault 3	Buck3 OV	Yes	Yes	Yes	Yes	1	
	Buck2 OV	Yes	Yes	Yes	Yes	1	
	Buck1 OV	Yes	Yes	Yes	Yes	1	
Fault 4	Buck1_HC	Yes	Yes	Yes	No	0.1	
Fault 5	NVM Read	No	Yes	No	No	-	Ok/good when bit = 1

Table 9. Fault and Status Flags: Behavior and Partitioning (Cont.)

Fault Register Partitioning	Fault/Status Name	Live Bit Status	Latched Bit Status	INT# Mask Option	Fault Response Option	Deglitch Time (ms)	Notes
	PGOODCCBAT	Yes	Yes	Yes	No	0.1	
	VREFIN UVLO	Yes	Yes	Yes	Yes	1	Only monitored after Buck2 (VDDQ) rail soft-start is completed.
	AVDD UVPD	Yes	Yes	Yes	No	0.1	
Fault 6	NVM_Error	No	Yes	Yes	No	-	
	CRST Triggered	Yes	Yes	Yes	No	-	
	WDT Error	Yes	Yes	Yes	No	-	
	ОТР	Yes	Yes	Yes	No	-	
	OTP Warn	Yes	Yes	Yes	No	-	
	EE Bank 7 ECC Corrected	No	Yes	No	No	-	Clear latched flag by writing 1 to the bit location
ECC Detail 1	EE Bank 6 ECC Corrected	No	Yes	No	No	-	Clear latched flag by writing 1 to the bit location
	EE Bank 5 ECC Corrected	No	Yes	No	No	-	Clear latched flag by writing 1 to the bit location
	EE Bank 4 ECC Corrected	No	Yes	No	No	-	Clear latched flag by writing 1 to the bit location
ECC Detail 1	EE Bank 3 ECC Corrected	No	Yes	No	No	TAL	Clear latched flag by writing 1 to the bit location
	EE Bank 2 ECC Corrected	No	Yes	No	No	-	Clear latched flag by writing 1 to the bit location
	EE Bank 1 ECC Corrected	No	Yes	No	No	-	Clear latched flag by writing 1 to the bit location
	EE Bank 0 ECC Corrected	No	Yes	No	No	-	Clear latched flag by writing 1 to the bit location
	EE Bank 7 ECC Error	No	Yes	No	No	-	Clear latched flag by writing 1 to the bit location
	EE Bank 6 ECC Error	No	Yes	No	No	-	Clear latched flag by writing 1 to the bit location
	EE Bank 5 ECC Error	No	Yes	No	No	-	Clear latched flag by writing 1 to the bit location
ECC Detail 2	EE Bank 4 ECC Error	No	Yes	No	No	-	Clear latched flag by writing 1 to the bit location
LOO Detail 2	EE Bank 3ECC Error	No	Yes	No	No	-	Clear latched flag by writing 1 to the bit location
	EE Bank 2 ECC Error	No	Yes	No	No	-	Clear latched flag by writing 1 to the bit location
	EE Bank 1 ECC Error	No	Yes	No	No	-	Clear latched flag by writing 1 to the bit location
	EE Bank 0 ECC Error	No	Yes	No	No	-	Clear latched flag by writing 1 to the bit location

Latched

Fault Register Partitioning	Fault/Status Name	Live Bit Status	Latched Bit Status	INT# Mask Option	Fault Response Option	Deglitch Time (ms)	Notes
EE Detail	Valid EE Data	No	Yes	No	No	-	Clear latched flag by writing 1 to the bit location
EE Detail	EE Error	NI-	V	NI-	NI-		Clear latched flag by

Table 9. Fault and Status Flags: Behavior and Partitioning (Cont.)

9.16 Maximum Recommended Power Dissipation

The maximum power dissipation recommended in a package is calculated using Equation 8 where T_{JMAX} = Maximum junction temperature, T_{AMAX} = Maximum ambient temperature, θ_{JA} = Thermal resistance of the package, and P_{DMAX} = Maximum power dissipation recommended.

(EQ. 8)
$$P_{DMAX} = \frac{T_{JMAX} - T_{AMAX}}{\theta_{JA}}$$

An example of the maximum recommended power dissipation versus ambient temperature curve is shown in Figure 36. In this example, the maximum power dissipation across the temperature range is specified at 25°C and the maximum junction temperature is set to 125°C, which is the maximum recommended operating junction temperature.

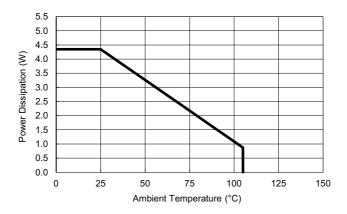


Figure 36. Power Dissipation vs Ambient Temperature

10. External Component Selection

The RAA215300 includes six synchronous buck regulators, three LDOs, and various features. It works with physically small components to reduce PCB assembly area and height. Switching MOSFETs are fully integrated and no external MOSFETs or diodes are needed.

10.1 Output Filters

The inductor and output capacitors are low-pass filters for the voltage at the buck switching node. Their characteristics influence the transfer function of the regulator and the control loop. It the transient load changes, the capacitors maintain output voltage with greater effective bandwidth than that achievable by the control loop



writing 1 to the bit location

alone. The permissible values of inductance and capacitance are dictated by PMIC design and settings. The values in Table 10 are consistent with stable operation and performance in accordance with Electrical Specifications.

10.1.1 Inductor Selection

At full load of the application, which is not necessarily the PMIC maximum rated load, inductors must have at least 90% of their low-current inductance. At 150% of PMIC maximum rated load, inductors must have at least 50% of their low-current inductance. For high efficiency, the inductors should have low resistance and low core loss. Choose molded or screened types for the best EMC.

Other similarly specified components may also be acceptable in the application, see Recommended External Components.

10.1.2 Output Capacitor Selection

Capacitors must be ceramic. When selecting for capacitance value, account for the effects of operating voltage and temperature.

Ceramic capacitors have temperature and voltage (bias) coefficients, which can significantly derate their effective capacitance value. When choosing capacitors, the effective capacitance rating for a given package size, voltage rating, and applied temperature and DC bias must be considered to ensure enough capacitance is used in the design. X5R and X7R types are recommended, depending on operating temperature. Other similarly specified components may also be acceptable in the application, see Recommended External Components.

10.2 Input Capacitor Selection

Ceramic input capacitors provide the high-frequency components of current flowing into the high-side MOSFETs. Place the capacitors close to the PMIC. If the power source is connected to the PMIC by long wires or traces, it may be necessary to add bulk capacitors near (not as close as the ceramic input capacitors) the PMIC to damp oscillation.

Other similarly specified components may also be acceptable in the application, see Recommended External Components.

10.3 Recommended External Components

Table 10. Recommended External Components

Name	Description	Description Qty Part Number		Key Electrical Specifications	Imperial (Metric) Size	Manufacturer				
All capacito	All capacitors: ^[1]									
Supplies										
C _{AVDD}	AVDD Input capacitance, MLCC	1	GRM188R61A106MAAL	10μF±20%, 10V, X5R	0603 (1608)	Murata				
C _{VIO}	Output capacitance, MLCC	1	GRM155R61A225KE01D	2.2µF±10%, 10V, X5R	0402 (1005)	Murata				
C _{VCHG}	Input capacitance, MLCC	1	GRM155R61A225KE01D	2.2µF±10%, 10V, X5R	0402 (1005)	Murata				
C _{VRTC}	Input capacitance, MLCC	DNP	GRM155R61A225KE01D	2.2µF±10%, 10V, X5R	0402 (1005)	Murata				
C _{VPROG}	Optional: Input capacitance for EEPROM Programming, MLCC	1	GRM155R6YA225KE11	2.2µF±20%, 35V, X5R	0402 (1005)	Murata				

Table 10. Recommended External Components (Cont.)

Name	Description	Qty	Part Number	Key Electrical Specifications	Imperial (Metric) Size	Manufacturer
C _{VBAT}	Output capacitance, supercapacitor	1	FMR0H104ZF	0.1F, 5.5V	-	Kemet
Buck1						
	Inductor	1	HBED042T-1R0MS-99	1.0μH±20%, 8.2A I _{SAT} , 9mΩ DCR	(4.1x4.1 x2.0mm)	Cyntec
	Option A	1	FDSD0420-H-1R0M=P3	1.0μH±20%, 6.8A I _{SAT} , 29mΩ DCR	(4.0x4.0 x2.0mm)	Murata
L _{BK1}	Option B	1	XGL4030-102ME	1.0μH±20%, 10.3A I _{SAT} , 7.2mΩ DCR	(4.0x4.0 x3.1mm)	Coilcraft
	Option C	1	SPM4020T-1R0M-LR	1.0μH±20%, 9A I _{SAT} , 28.1mΩ DCR	(4.4x4.1 x2.0mm)	TDK
C _{BK1_VIN}	Input capacitance, MLCC	2	GRM188R61A106MAAL	10µF±20%, 10V, X5R	0603 (1608)	Murata
C _{BK1_OUT}	Output capacitance, MLCC	5	GRM188R60J476ME15	47µF±20%, 6.3V, X5R	0603 (1608)	Murata
Buck2	-			1		!
L _{BK2}	Inductor	1	DFE322512F-1R5M	1.5μH±20%, 3.9A I _{SAT} , 48mΩ DCR	(3.2x2.5 x1.2mm)	Murata
C _{BK2_VIN}	Input capacitance, MLCC	1	GRM188R61A106MAAL	10µF±20%, 10V, X5R	0603 (1608)	Murata
C _{BK2_OUT}	Output capacitance, MLCC	3	GRM188R60J476ME15	47μF±20%, 6.3V, X5R	0603 (1608)	Murata
Buck3			1	1		
L _{BK3}	Inductor	1	DFE322512F-1R5M	1.5μH±20%, 3.9A I _{SAT} , 48mΩ DCR	(3.2x2.5 x1.2mm)	Murata
C _{BK3_VIN}	Input capacitance, MLCC	1	GRM188R61A106MAAL	10µF±20%, 10V, X5R	0603 (1608)	Murata
C _{BK3_OUT}	Output capacitance, MLCC	2	LMK107BBJ226MA-T	22µF±20%, 10V, X5R	0603 (1608)	Taiyo Yuden
Buck4						
	Inductor	1	HBED042T-1R5MS-99	1.5μH±20%, 6.8A I _{SAT} , 14mΩ DCR	(4.1x4.1 x2.0mm)	Cyntec
	Option A	1	FDSD0420-H-1R5M=P3	1.5μH±20%, 5.7A I _{SAT} , 36mΩ DCR	(4.0x4.0 x2.0mm)	Murata
L _{BK4}	Option B	1	XGL4030-152ME	1.5μH±20%, 8.8A I _{SAT} , 10.5mΩ DCR	(4.0x4.0 x3.1mm)	Coilcraft
	Option C	1	SPM4020T-1R5M-LR	1.5μH±20%, 6.3A I _{SAT} , 40mΩ DCR	(4.4x4.1 x2.0mm)	TDK
C _{BK4_VIN}	Input capacitance, MLCC	2	GRM188R61A106MAAL	10µF±20%, 10V, X5R	0603 (1608)	Murata

Table 10. Recommended External Components (Cont.)

Name	Description	Qty	Part Number	Key Electrical Specifications	Imperial (Metric) Size	Manufacturer
C _{BK4_OUT}	Output capacitance, MLCC	4	GRM21BR61A226ME44	22μF±20%, 10V, X5R	0805 (2012)	Murata
Buck5						
L _{BK5}	Inductor	1	DFE252012F-1R5M	1.5μH±20%, 3.8A I _{SAT} , 58mΩ DCR	(2.5x2.0x1. 2mm)	Murata
C _{BK5_VIN}	Input capacitance, MLCC	1	GRM188R61A106MAAL	10μF±20%, 10V, X5R	0603 (1608)	Murata
C _{BK5_OUT}	Output capacitance, MLCC	2	LMK107BBJ226MA-T	22μF±20%, 10V, X5R	0603 (1608)	Taiyo Yuden
Buck6 (supp	oorting VTT Mode)					
L _{BK6}	Inductor	1	DFE252012F-R47M	0.47μH±20%, 6.7A I _{SAT} , 23mΩ DCR	(2.5x2.0 x1.2mm)	Murata
C _{BK6_VIN}	Input capacitance, MLCC	1	GRM188R61A106MAAL	10μF±20%, 10V, X5R	0603 (1608)	Murata
C _{BK6_OUT}	Output capacitance, MLCC	5	GRM188R60J476ME15	47μF±20%, 6.3V, X5R	0603 (1608)	Murata
LDO 1						
C _{LDO1_VIN}	Input capacitance, MLCC	11	GRM188R61A475KAAJ	4.7µF±10%, 10V, X5R	0603 (1608)	Murata
C _{LDO1_OUT}	Output capacitance, MLCC	2	LMK107BBJ226MA-T	22μF±20%, 10V, X5R	0603 (1608)	Taiyo Yuden
LDO 2						
C _{LDO2_VIN}	Input capacitance, MLCC	1	GRM188R61A475KAAJ	4.7µF±10%, 10V, X5R	0603 (1608)	Murata
C _{LDO2_OUT}	Output capacitance, MLCC	2	LMK107BBJ226MA-T	22μF±20%, 10V, X5R	0603 (1608)	Taiyo Yuden
LDO 3						
C _{LDO3_VIN}	Input capacitance, MLCC	1	GRM155R61A225KE01D	2.2µF±10%, 10V, X5R	0402 (1005)	Murata
C _{LDO3_OUT}	Output capacitance, MLCC	1	GRM155R61A475MEAA	4.7µF±20%, 10V, X5R	0402 (1005)	Murata
VTTREF						•
C _{VREFIN}	Input capacitance, MLCC	1	GRM155R61A225KE01D	2.2µF±10%, 10V, X5R	0402 (1005)	Murata
C _{VREFOUT}	Output capacitance, MLCC	1	GRM155R61A475MEAA	4.7μF±20%, 10V, X5R	0402 (1005)	Murata

Table 10. Recommended External Components (Cont.)

Name	Description	Qty	Part Number	Key Electrical Specifications	Imperial (Metric) Size	Manufacturer	
Crystal Oscillator							
XTAL	Crystal	1	ECX327-CDX-1293	32.768kHz, ±5ppm, 70kΩ max ESR, 12.5pF load capacitance	(3.2x1.5x 0.9mm)	ECS	
	Option A	1	ECX327-CDX-2096	32.768kHz, ±5ppm, 50kΩ max ESR, 12.5pF load capacitance	(3.2x1.5x 0.9mm)	ECS	
C _{XIN} ^[2]	Input capacitance	DNP		Up to 10pF, COG	0402 (1005)		
C _{XOUT} ^[2]	Output capacitance	DNP		Up to 10pF, COG	0402 (1005)		
Resistance							
R _{SDA} , R _{SCL}	I ² C Pull-up resistance	1	RC0402JR-0710KL	10kΩ±5%	0402 (1005)	Yageo	
R _{INT}	INT# Pull-up resistance	1	RC0402FR-07100KL	100kΩ±5%	0402 (1005)	Yageo	
R _{MPIO}	Optional: MPIOx Pull-up or Pull-down resistance	1	RC0402FR-074K75L	4.75kΩ±5%	0402 (1005)	Yageo	

^{1.} The capacitance listed in the above table is not derated. Refer to the capacitors datasheets for effective capacitance.

10.4 Recommended Effective Capacitance

The effective capacitance of the ceramic capacitors changes with the DC bias voltage. When choosing the input capacitors or output capacitors for each regulator, the total capacitance needs to be equivalent to the recommended value as shown in Table 11.

Table 11. Recommended Effective Capacitance^[1]

Regulator	Total Output Effective Capacitance (μF)	Total Input Effective Capacitance (µF)
Buck1	190	7.2
Buck2	110	3.6
Buck3	34	3.6
Buck4	59	7.2
Buck5	40	3.6
Buck6 (VTT mode)	222	3.6
LDO1	22	3.2
LDO2	22	3.2
LDO3	3	0.6
VIO	1.5	N/A

^{2.} Do Not Populate capacitors by default. They are only needed for oscillator tuning. Renesas recommends placing footprints for these components in the system design in case they are needed.

Table 11. Recommended Effective Capacitance^[1]

Regulator	Total Output Effective Capacitance (μF)	Total Input Effective Capacitance (μF)
VREFIN	1.8	N/A
VREFOUT	4.6	N/A

The recommended effective capacitance is determined based on the RTKA215300DE0000BU BOM and the DC characteristics curves
that are available on the capacitor vendor website. The DC bias voltages are the typical input and output voltages of each regulator as
stated in Electrical Specifications.

11. Layout Guidelines

PCB design is crucial to proper performance of the PMIC and system. The following are recommendations to achieve proper device performance.

11.1 Power Ground (PGND)

PGND is the reference for all voltages of the power system. Many components must have low-impedance connections to PGND (most importantly the input and output capacitors). Create a PGND plane on at least one PCB layer and extend it to at least the connection points of all relevant components. The PGND plane is an important heatsink and it may also provide electrostatic screening. Aim to avoid interrupting the plane with non-PGND vias, especially if they are in a row and form a slit. The PGND plane is not perfect because it has impedance and there are unwanted voltages developed across it.

11.2 Analog Ground (AGND)

AGND is an electrically quiet reference for signals that could be corrupted if they were connected to PGND. These signals are the PMIC internal power supply and those associated with the RTC and its power supply. Create a small plane that connects these signals to Pin 26 and Pin 42. Connect this plane directly to PGND at the EPAD.

11.3 Digital Ground

Connect the grounds of digital signals to PGND.

11.4 Exposed Pad (EPAD)

Internal to the PMIC, all regulator power grounds are bonded to the EPAD. The EPAD is in close thermal contact with the PMIC die. Therefore, the connection between EPAD and PCB is important to both the grounding scheme and thermal management. Connect the EPAD to the PGND plane.

Place thermal vias, in a 1 to 1.2mm pitch grid formation, under the PMIC at least in the area of the EPAD, and connect them to the PGND plane. The vias must not wick solder from the EPAD joint.

11.5 Buck Regulators

The current through the MOSFETs is periodically and rapidly switched. The current generates a magnetic field that inductively couples current into nearby conductors. At some distance (dependent on frequency) from the source, the magnetic field becomes electromagnetic radiation (noise). Voltage (noise) develops across impedance in the current paths.

To mitigate the effects of switched current, make paths short and low impedance, make loop areas small and avoid sharing ground connections with sensitive circuits.

The MOSFETs are internal to the PMIC, so their current paths are predetermined. The main external high-frequency current path is through input capacitors. Place input capacitors close to their respective buck regulator input terminals, which usually means placing them on the same side as the PMIC. Connect the positive side with short wide copper. If the negative side needs to connect to an inner-layer PGND plane, do so with



multiple vias. In some applications, it might be helpful to place a physically small capacitor with a lower high-frequency impedance closest to the PMIC. Current in the inductor has smaller high-frequency content than the MOSFETs; however, it is still necessary to connect the inductor to the switch node PMIC terminals with low-impedance copper and to make low-impedance connections to the output capacitors. The output capacitors must be intimately connected to the PGND plane so use multiple vias if the PGND plane is on an inner layer.

The voltage at the switch node is periodically and rapidly switched. The voltage generates an electric field that capacitively couples voltage into nearby conductors. At some distance (dependent on frequency) from the source, the electric field becomes electromagnetic radiation (noise).

To mitigate the effects of switched voltage, make the copper area of the switched node small. This partially contradicts the requirement to make a low-impedance connection between the switch node and inductor, but this is a compromise that must happen. Make the path short but only wide enough to carry the current. Do not add copper that does not have a high current density. Most of the generated electric field is perpendicular to the copper surface. The PGND plane is an effective shield. The inductor terminal also generates an electric field, in directions perpendicular to its surfaces.

11.6 Linear Regulators (LDOs)

The LDOs require good high-frequency decoupling of their inputs and outputs. Connections to input and output capacitors must be low impedance at high frequency. Place capacitors close to PMIC pins and connect with short wide copper. Connect capacitors to the PGND plane with multiple vias.

11.7 Crystal Oscillator

Place the crystal close to the PMIC. Pin 28, XIN, has very high impedance, and oscillator circuits operating at low frequencies are susceptible to noise if good layout practice is not followed. Erratic clocking and accuracy errors can be caused by adjacent noisy signals. Do not route noisy traces near the crystal. Add a guard ring around the crystal and connect one end to AGND. To avoid affecting load capacitance, keep all layers clear of copper in the area of the crystal and its connecting traces.

11.8 Device Specific Layout Guidelines

The following table provides layout guidelines (such as trace routing and size, and component placements) for the various pins of RAA215300. *Note:* All buck supplies (BUCKx VINx) = AVDD = VCHG.

Pin Number	Pin Name	Layout Guideline
1, 2	MPIO4, MPIO3	Digital input/output pin. Route trace away from any buck switch node. Consider placing the trace such that the PGND plane is between the trace and any buck switch node.
3, 4, 5	BUCK1_LX3, BUCK1_LX2, BUCK1_LX1	Place the inductor close to the pins. Connect the pins together and to the inductor with short, wide copper, but keep the area small. Do not place sensitive signal traces (for example, feedback) near this copper on the same layer, or in the same area on inner layers unless shielded by the PGND plane.
6, 7, 8	BUCK1_VIN3, BUCK1_VIN2, BUCK1_VIN1	Place input capacitors close to the pins and connect with short, wide copper.
9	PGND	Connect the PGND pin directly to the top layer of copper under the exposed pad (EPAD). The PGND pin may also be connected to top layer copper - for example to nearby input capacitors for BUCK1
10	BUCK1_FB	Run a dedicated trace to BUCK1 output capacitors. Connect directly to a capacitor but away from the main path of output current. Route the trace away from any noisy signals, switch nodes, or output inductors. Consider placing the trace such that the PGND plane is between the trace and any buck switch node.
11	VPROG	Connect to PGND (if programming EEPROM is not required).



Pin Number	Pin Name	Layout Guideline
12	BUCK3_FB	Run a dedicated trace to BUCK3 output capacitors. Connect directly to a capacitor but away from the main path of output current. Route the trace away from any noisy signals, switch nodes, or output inductors. Consider placing the trace such that the PGND plane is between the trace and any buck switch node.
13	LDO_SEL2	Digital input pin. Should be isolated from the high di/dt and dv/dt signals to minimize any coupling. This signal should be placed on a quiet layer.
14	BUCK3_VIN	Place input capacitors close to the pin and connect with short, wide copper.
15	BUCK3_LX	Place the inductor close to the pin. Connect the pin to the inductor with short, wide copper, but keep the area small. Do not place sensitive signal traces (for example, feedback) near this copper on the same layer, or in the same area on inner layers unless shielded by the PGND plane.
16	INT#	Digital output pin. Should be isolated from the high di/dt and dv/dt signals to minimize any coupling. This signal should be placed on a quiet layer.
17	SCL	Digital input pins. Should be isolated from the high di/dt and dv/dt signals to minimize any coupling.
18	SDA	These signals should be placed on a quiet layer. If not used, connect to VIO.
19	LDO_SEL1	Digital input pin. Should be isolated from the high di/dt and dv/dt signals to minimize any coupling. This signal should be placed on a quiet layer.
20, 21	BUCK4_LX2, BUCK4_LX1	Place the inductor close to the pins. Connect the pins to the inductor with short, wide copper, but keep the area small. Do not place sensitive signal traces (for example, feedback) near this copper on the same layer, or in the same area on inner layers unless shielded by the PGND plane.
22, 23	BUCK4_VIN2, BUCK4_VIN1	Place input capacitors close to the pins and connect with short, wide copper.
24	VIO	Place the decoupling capacitor close to the pin and connect with short, wide copper. Connect the other side of the capacitor to pin 26 (AGND) with short, wide copper.
25	BUCK4_FB	Run a dedicated trace to BUCK4 output capacitors. Connect directly to a capacitor but away from the main path of output current. Route the trace away from any noisy signals, switch nodes, or output inductors. Consider placing the trace such that the PGND plane is between the trace and any buck switch node.
26, 42	AGND	Analog ground (AGND) and power ground (PGND) of the IC should be separated on the board, but connected directly to EPAD. To avoid unwanted noise coupling into the AGND plane, keep the plane localized to the area where AGND is required.
27	XOUT	Avoid routing serial bus lines, any high-speed logic lines, high dv/dt, or di/dt signals in the vicinity of
28	XIN	crystal pins. These can induce noise in the oscillator circuit causing misclocking. Add a ground trace around the crystal with one end terminated at the chip analog ground, providing termination for emitted noise in the vicinity of the RTC device. Avoid ground plane in the layer(s) under these pins, traces, and external crystal, as this affects the load capacitance on the pins and therefore, the oscillator accuracy of the circuit. Connect to ground if not used.
29	VRTC	When RTC is used, place a decoupling capacitor footprint close to the pin and connect with short, wide copper. Connect the other side of the capacitor footprint to AGND. This capacitor should be Do Not Populated by default.
30	VBAT	Connect to battery or supercapacitor with short trace. Connect to PGND if not used.
31	VCHG	AVDD, VCHG, and BUCKx_VINx must be the same voltage. Place the decoupling capacitor close to the pin and connect with short, wide copper. Connect the other side of the capacitor to PGND.
32, 35, 36	LDO1_OUT, LDO2_OUT, LDO3_OUT	Place decoupling capacitors close to their respective outputs and connect with wide traces.

Pin Number	Pin Name	Layout Guideline
33, 34, 37	LDO1_VIN, LDO2_VIN, LDO3_VIN	Place decoupling capacitors close to their respective inputs and connect with wide traces.
38	BUCK5_LX	Place the inductor close to the pin. Connect the pin to the inductor with short, wide copper, but keep the area small. Do not place sensitive signal traces (for example, feedback) near this copper on the same layer, or in the same area on inner layers unless shielded by the PGND plane.
39	BUCK5_VIN	Place input capacitors close to the pin and connect with short, wide copper.
40	AVDD	AVDD, VCHG, and BUCKx_VINx must be the same voltage. Place the decoupling capacitor close to the pin and connect with short, wide copper. Connect the other side of the capacitor to PGND.
41	BUCK5_FB	Run a dedicated trace to BUCK5 output capacitors. Connect directly to a capacitor but away from the main path of output current. Route the trace away from any noisy signals, switch nodes, or output inductors. Consider placing the trace such that the PGND plane is between the trace and any buck switch node.
43	VREFIN	Place the decoupling capacitor close to the pin and connect with short, wide copper. Connect the other side of the capacitor to PGND. Note: Pin has a $1M\Omega$ (typical) internal resistor to GND.
44	VREFOUT	Place the decoupling capacitor close to the pin and connect with short, wide copper. Connect the other side of the capacitor to PGND.
45	MPIO5	Digital input/output pin. Route trace away from any buck switch node. Consider placing the trace such that the PGND plane is between the trace and any buck switch node.
46	BUCK6_FB	Run a dedicated trace to BUCK3 output capacitors. Connect directly to a capacitor but away from the main path of output current. Route the trace away from any noisy signals, switch nodes, or output inductors. Consider placing the trace such that the PGND plane is between the trace and any buck switch node.
47	CEN	Digital input pin. Route trace away from any buck switch node. Consider placing the trace such that the PGND plane is between the trace and any buck switch node.
48	BUCK6_VIN	Place input capacitors close to the pin and connect with short, wide copper.
49	BUCK6_LX	Place the inductor close to the pin. Connect the pin to the inductor with short, wide copper, but keep the area small. Do not place sensitive signal traces (for example, feedback) near this copper on the same layer, or in the same area on inner layers unless shielded by the PGND plane.
50	BUCK2_LX	Place the inductor close to the pin. Connect the pin to the inductor with short, wide copper, but keep the area small. Do not place sensitive signal traces (for example, feedback) near this copper on the same layer, or in the same area on inner layers unless shielded by the PGND plane.
51	BUCK2_VIN	Place input capacitors close to the pin and connect with short, wide copper.
52	PWRON	Digital input pin. Should be isolated from the high di/dt and dv/dt signals to minimize any coupling. This signal should be placed on a quiet layer.
53	BUCK2_FB	Run a dedicated trace to BUCK2 output capacitors. Connect directly to a capacitor but away from the main path of output current. Route the trace away from any noisy signals, switch nodes, or output inductors. Consider placing the trace such that the PGND plane is between the trace and any buck switch node.
54	MPIO0	Digital input/output pin. Route the trace away from any buck switch node. Consider placing the trace such that the PGND plane is between the trace and any buck switch node.
55	MPIO1	Digital input/output pin. Route the trace away from any buck switch node. Consider placing the trace such that the PGND plane is between the trace and any buck switch node.

Pin Number	Pin Name	Layout Guideline
56	MPIO2	Digital input/output pin. Route trace away from any buck switch node. Consider placing the trace such that the PGND plane is between the trace and any buck switch node.
-	EPAD	Connect to PGND with matching shape. Connect to the GND layer using an array of equidistant vias to achieve better thermal performance.

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12. Register Map

Any register addresses (pointers) not indicated in the following section, Register Map Detail, are reserved and should not be used.

Register addresses 0x00~13 are read and write accessed using only the RTC Slave Address (set in register 0x1F).

All other register addresses are read and write accessed using the Main Slave Address (set in register 0x1E). See 7-bit Device Addresses.

12.1 Register Map Detail

The default values in the following table are for RAA215300A2GNP#HA0. Any differences with other part numbers are outlined in Part Number Differences.

Register Pointer	Register Bit(s)	Bit(s)/Function Name	Description	Setting/Range	Default	
0x00	Register Name - RTC SC Type - (RW, Non EEPROM)					
	[7]	not used			<0>	
	[6]	SC22	Set seconds (0-59) in BCD format	RTC SC[6:0] BCD decode:	<0>	
	[5]	SC21	1	0000000: 0sec	<0>	
	[4]	SC20	†	0000001: 1sec 0000010: 2sec	<0>	
	[3]	SC13		0000010. 2sec	<0>	
	[2]	SC12	-)NHI)H	0001001: 9sec	<0>	
	[1]	SC11		0010000: 10sec	<0>	
	[0]	SC10	┥	0010001: 11sec	<0>	
				1010111: 57sec 1011000: 58sec 1011001: 59sec		
0x01	Type - (R\	lame - RTC MN V, Non EEPROM)			0x00 / 0	
	[7]	not used			<0>	
	[6]	MN22	Set minutes (0-59) in BCD format	RTC MN[6:0] BCD decode: 0000000: 0min	<0>	
	[5]	MN21		0000000: 0min 0000001: 1min	<0>	
	[4]	MN20		0000010: 2min	<0>	
	[3]	MN13		ļ	<0>	
	[2]	MN12	1	0001001: 9min	<0>	
	[1]	MN11	7	0010000: 10min 0010001: 11min	<0>	
	[0]	MN10	7		<0>	
				1010111: 57min 1011000: 58min 1011001: 59min		

Type -	er Name - RTC HF (RW, Non EEPRC			0)
'''	, , ==	,		
[7]	MIL	12-hour or 24-hour format selection bit	0: 12-hour format 1: 24-hour format	
[6]	not used			1
[5]	HR21	Set hours in BCD format. If the MIL bit is	If MIL = 1	1
[4]	HR20	"0", the RTC uses a 12-hour format and	RTC HR[5:0] decodes for 24-hour	
[3]	HR13	HR21 bit functions as an AM/PM indicate with a "1" representing PM.	or f ormat: 000000: 0hr	
[2]	HR12	with a 1 representing Pivi.	000001: 1hr	
[1]	HR11			
[0]	HR10		001001: 9hr 010000: 10hr	
			 011001: 19hr 100000: 20hr	
			 100011: 23hr If MIL = 0 RTC HR[4:0] decodes for 12-hour format with RTC HR [5] indicating	
			AM/PM: 00000: INVALID 00001: 1 AM/PM 00010: 2 AM/PM	
			 01001: 9 AM/PM 10000: 10 AM/PM	
			10001: 11 AM/PM	
	er Name - RTC DT (RW. Non EEPRO		10001: 11 AM/PM 10010: 12 AM/PM	0:
Type -	(RW, Non EEPRC			0:
Type - [7:6]	not used	MONFIDE	10010: 12 AM/PM	
Type - [7:6] [5]	not used DT21			
Type - [7:6] [5] [4]	not used DT21 DT20	MONFIDE	RTC DT[5:0] BCD decode: 000000: INVALID 000001: date 1	
Type - [7:6] [5] [4]	not used DT21 DT20 DT13	MONFIDE	RTC DT[5:0] BCD decode: 000000: INVALID	
Type - [7:6] [5] [4] [3]	not used DT21 DT20 DT13 DT12	MONFIDE	RTC DT[5:0] BCD decode: 000000: INVALID 000001: date 1	
Type - [7:6] [5] [4] [3] [2]	not used DT21 DT20 DT13 DT12 DT11	MONFIDE	RTC DT[5:0] BCD decode: 000000: INVALID 000001: date 1 000010: date 2	
Type - [7:6] [5] [4] [3]	not used DT21 DT20 DT13 DT12	MONFIDE	RTC DT[5:0] BCD decode: 000000: INVALID 000001: date 1 000010: date 2 001001: date 9	
Type - [7:6] [5] [4] [3] [2]	not used DT21 DT20 DT13 DT12 DT11	MONFIDE	RTC DT[5:0] BCD decode: 000000: INVALID 000001: date 1 000010: date 2 001001: date 9 010000: date 10 011001: date 19 100000: date 20 101001: date 29 110000: date 30	
Type - [7:6] [5] [4] [3] [2] [1] [0]	hot used DT21 DT20 DT13 DT12 DT11 DT10	Set date (1-31) in BCD format	RTC DT[5:0] BCD decode: 000000: INVALID 000001: date 1 000010: date 2 001001: date 9 010000: date 10 011001: date 19 100000: date 20 101001: date 29	
Type - [7:6] [5] [4] [3] [2] [1] [0]	not used DT21 DT20 DT13 DT12 DT11	Set date (1-31) in BCD format	RTC DT[5:0] BCD decode: 000000: INVALID 000001: date 1 000010: date 2 001001: date 9 010000: date 10 011001: date 19 100000: date 20 101001: date 29 110000: date 30	
Type - [7:6] [5] [4] [3] [2] [1] [0] Registe Type -	hot used DT21 DT20 DT13 DT12 DT11 DT10 er Name - RTC MC (RW, Non EEPRO	Set date (1-31) in BCD format	RTC DT[5:0] BCD decode: 000000: INVALID 000001: date 1 000010: date 2 001001: date 9 010000: date 10 011001: date 19 100000: date 20 101001: date 29 110000: date 30	
Type - [7:6] [5] [4] [3] [2] [1] [0] Registe Type -	not used DT21 DT20 DT13 DT12 DT11 DT10 er Name - RTC MC (RW, Non EEPRC	Set date (1-31) in BCD format	RTC DT[5:0] BCD decode: 000000: INVALID 000001: date 1 000010: date 2 001001: date 9 010000: date 10 011001: date 19 100000: date 20 101001: date 29 110000: date 30 110001: date 31	0
Type - [7:6] [5] [4] [3] [2] [1] [0] Registe Type - [7:5] [4]	hot used DT21 DT20 DT13 DT12 DT11 DT10 er Name - RTC MC (RW, Non EEPRC) hot used MO20	Set date (1-31) in BCD format	RTC DT[5:0] BCD decode: 000000: INVALID 000001: date 1 000010: date 2 001001: date 9 010000: date 10 011001: date 19 100000: date 20 101001: date 29 110000: date 30	0
(7:6) [7:6] [4] [3] [2] [1] [0] Registe Type - [7:5] [4] [3]	not used DT21 DT20 DT13 DT12 DT11 DT10 PT Name - RTC MC (RW, Non EEPRC) not used MO20 MO13	Set date (1-31) in BCD format	RTC DT[5:0] BCD decode: 000000: INVALID 000001: date 1 000010: date 2 001001: date 9 010000: date 10 011001: date 19 100000: date 20 101001: date 29 110000: date 30 110001: date 31	0
(7:6) [5] [4] [3] [2] [1] [0] Registe Type - [7:5] [4] [3] [2]	not used DT21 DT20 DT13 DT12 DT11 DT10 Pr Name - RTC MC (RW, Non EEPRC) hot used MO20 MO13 MO12	Set date (1-31) in BCD format	RTC DT[5:0] BCD decode: 000000: INVALID 000001: date 1 000010: date 2 001001: date 9 010000: date 10 011001: date 19 100000: date 20 101001: date 29 110000: date 30 110001: date 31	0
Type - [7:6] [5] [4] [3] [2] [1] [0] Registe Type - [7:5] [4] [3] [2] [1]	not used DT21 DT20 DT13 DT12 DT11 DT10 Pr Name - RTC MC (RW, Non EEPRC) not used MO20 MO13 MO12 MO11	Set date (1-31) in BCD format	RTC DT[5:0] BCD decode: 000000: INVALID 000001: date 1 000010: date 2 001001: date 9 010000: date 10 011001: date 19 100000: date 20 101001: date 29 110000: date 30 110001: date 31	0
(7:6) [5] [4] [3] [2] [1] [0] Registe Type - [7:5] [4] [3] [2]	not used DT21 DT20 DT13 DT12 DT11 DT10 Pr Name - RTC MC (RW, Non EEPRC) hot used MO20 MO13 MO12	Set date (1-31) in BCD format	RTC DT[5:0] BCD decode: 000000: INVALID 000001: date 1 000010: date 2 001001: date 9 010000: date 10 011001: date 19 100000: date 20 101001: date 29 110000: date 30 110001: date 31	

x05		er Name - RTC YR (RW, Non EEPROM))		0x00 /
		,	,		
	[7]	YR23	Set year (0-99) in BCD format	RTC YR[7:0] decodes:	<0>
	[6]	YR22		0000 0000: 0th year	<0>
	[5]	YR21		0000 0001: 1st year	<0>
	[4]	YR20		 0001 0000: 10th year	<0>
	[3]	YR13		0001 0000. 10th year	<0>
	[2]	YR12			<0>
				1000 0000: 80th year	
	[1]	YR11		1000 0001: 81st year	<0>
	[0]	YR10		 1001 1000: 98th year 1001 1001: 99th year	<0>
x06	Registe	er Name - RTC DW		1001 1001. 33til year	0x00 /
	Type - ((RW, Non EEPROM))		
	[7:3]	not used			<00000
	[2]	DW2	Set day of the week (1-7)	RTC DW[2:0] decodes:	<0>
	[1]	DW1		000: 1st day of the week	<0>
	[0]	DW0		001: 2nd day of the week 010: 3rd day of the week	<0>
x07		r Name - RTC SR (RW, Non EEPROM))	110: 7th day of the week	0x01 /
x07	Type - ((RW, Non EEPROM)			
x07			Auto reset enable bit	0:Disable the automatic reset of the BAT and ALM status bits only 1: Enable the automatic reset of the	0x01/
x07	Type - ((RW, Non EEPROM)		0:Disable the automatic reset of the BAT and ALM status bits only	
x07	Type - ((RW, Non EEPROM)		0:Disable the automatic reset of the BAT and ALM status bits only 1: Enable the automatic reset of the	
×07	Type - (RW, Non EEPROM	Auto reset enable bit Internal crystal oscillator enable bit. XTOSCB needs to be set to '0' when external crystal is used. XTOSCB needs to be set to 1' when external 32kHz clock	O:Disable the automatic reset of the BAT and ALM status bits only 1: Enable the automatic reset of the BAT and ALM status bits only O: Enable internal crystal oscillator	<0>
x07	Type - (ARST XTOSCB	Auto reset enable bit Internal crystal oscillator enable bit. XTOSCB needs to be set to '0' when external crystal is used. XTOSCB needs to be set to 1' when external 32kHz clock	O:Disable the automatic reset of the BAT and ALM status bits only 1: Enable the automatic reset of the BAT and ALM status bits only O: Enable internal crystal oscillator	<0>
×07	Type - ([7] [6] [5] [4]	ARST XTOSCB not used WRTC	Auto reset enable bit Internal crystal oscillator enable bit. XTOSCB needs to be set to '0' when external crystal is used. XTOSCB needs to be set to 1' when external 32kHz clock signal is applied at XIN pin.	O:Disable the automatic reset of the BAT and ALM status bits only 1: Enable the automatic reset of the BAT and ALM status bits only O: Enable internal crystal oscillator 1: Disable internal crystal oscillator O: Disable write capability into the RTC timing registers 1: Enable write capability into the	<0>
×07	Type - ([7] [6] [5] [4]	ARST XTOSCB not used wrtc	Internal crystal oscillator enable bit. XTOSCB needs to be set to '0' when external crystal is used. XTOSCB needs to be set to 1' when external 32kHz clock signal is applied at XIN pin. Write RTC enable bit	D:Disable the automatic reset of the BAT and ALM status bits only 1: Enable the automatic reset of the BAT and ALM status bits only D: Enable internal crystal oscillator 1: Disable internal crystal oscillator D: Disable write capability into the RTC timing registers 1: Enable write capability into the RTC timing registers	<0> <0> <0>
×07	Type - ([7] [6] [5] [4]	ARST XTOSCB not used WRTC	Auto reset enable bit Internal crystal oscillator enable bit. XTOSCB needs to be set to '0' when external crystal is used. XTOSCB needs to be set to 1' when external 32kHz clock signal is applied at XIN pin.	O:Disable the automatic reset of the BAT and ALM status bits only 1: Enable the automatic reset of the BAT and ALM status bits only O: Enable internal crystal oscillator 1: Disable internal crystal oscillator O: Disable write capability into the RTC timing registers 1: Enable write capability into the	<0> <0> <0>
×07	Type - ([7] [6] [5] [4]	ARST XTOSCB not used wrtc	Internal crystal oscillator enable bit. XTOSCB needs to be set to '0' when external crystal is used. XTOSCB needs to be set to 1' when external 32kHz clock signal is applied at XIN pin. Write RTC enable bit	D:Disable the automatic reset of the BAT and ALM status bits only 1: Enable the automatic reset of the BAT and ALM status bits only D: Enable internal crystal oscillator 1: Disable internal crystal oscillator 1: Disable internal crystal oscillator 1: Disable write capability into the RTC timing registers 1: Enable write capability into the RTC timing registers D: Alarm doesn't match the real time clock	<0> <0> <0>

	RW, Non EEPRO	- M)		0x10
[7]	IM	Interrupt/alarm mode bit	0: Enable single event alarm mode 1: Enable periodic interrupt alarm mode	<0:
[6]	ALME	Alarm enable bit	0: Disable the alarm function 1: Enable the alarm function	<0:
[5]	LPMODE	Oscillator bias current control bit	0: Normal oscillator bias current 1: Reduced oscillator bias current	<0:
[4]	FOBATB	Enable/disable the FOUT/IRQ function in battery backup mode	Disable the FOUT/IRQ function in battery backup mode Enable the FOUT/IRQ function in battery backup mode	<1
[3:0]	FO	Enable/disable the frequency output function and select the output frequency at the INT# pin		<000
			1110: 1/16Hz 1111: 1/32Hz	
	ed for Renesas Int			0x00
Registe	ed for Renesas Int r Name - RTC AT RW, Non EEPRO	R		0x00
Registe	r Name - RTC AT	R	1111: 1/32Hz	0x000 <000

_	er Name - RTC DT (RW, Non EEPRO			0x0(
[7:3]	not used			<000
[2:0]	DTR	Adjust the average number of counts per second and average the ppm error to achieve better accuracy	000: 0ppm 001: +20ppm 010: +40ppm 011: +60ppm 100: 0ppm 101: -20ppm 110: -40ppm 111: -60ppm	<00
	I er Name - RTC SC (RW, Non EEPRC			0x00
[7]	ESCA	Enable or disable alarm register bytes for seconds	Disable the alarm register bytes for seconds Enable the alarm register bytes for seconds	<0
[6]	ASC22	Set alarm seconds (0-59) in BCD format.	RTC ASC[6:0] BCD decode:	<(
[5]	ASC21		0000000: 0sec	<(
[4]	ASC20	occurs between the alarm registers and the RTC registers for seconds	0000001: 1sec 0000010: 2sec	<(
[3]	ASC13	irie ivio registers for seconds		<(
[2]	ASC12		0001001: 9sec	<(
[1]	ASC11		0010000: 10sec	<(
[0]	ASC10	 	0010001: 11sec	<(
		ALLIDEN	 1010111: 57sec 1011000: 58sec 1011001: 59sec	
	er Name - RTC MI (RW, Non EEPRO		1011001. 39360	0x0
[7]	EMNA	Enable or disable alarm register bytes for minutes	Disable the alarm register bytes for minutes Enable the alarm register bytes for minutes	<(
[6]	AMN22	Set alarm minutes (0-59) in BCD format.		<(
[5]	AMN21		0000000: 0min	<(
[4]	AMN20	——occurs between the alarm registers and the RTC registers for minutes	0000001: 1min 0000010: 2min	<(
[3]	AMN13			<(
[2]	AMN12		0001001: 9min	<(
[1]	AMN11		0010000: 10min 0010001: 11min	<(
[0]	AMN10		DO 1000 1. 1 1111111 L	<(
			 1010111: 57min	

	`			0:
[7]	EHRA	Enable or disable alarm register bytes for hours	D: Disable the alarm register bytes for hours Enable the alarm register bytes for hours D: Enable the alarm register bytes for hours	
[6]	not used	•		
[5]	AHR21	Set hours in BCD format. If the MIL bit is	f MIL = 1	
[4]	AHR20	"0", the RTC uses a 12-hour format and	RTC AHR[5:0] decodes for 24-hour	
[3]	AHR13	——AHR21 bit functions as an AM/PM indica- tor with a "1" representing PM. The alarm	format: 000000: 0hr	
[2]	AHR12	will be triggered once a match occurs	000001: 1hr	
[1]	AHR11	between the alarm registers and the RTC	ļ <u>†</u>	
[0]	AHR10	registers for hours	001001: 9hr 010000: 10hr	
			 011001: 19hr 100000: 20hr	
			 100011: 23hr	
			If MIL = 0 RTC AHR[4:0] decodes for 12-hour format with RTC AHR[5] indicating AM/PM: 00000: INVALID 00001: 1 AM/PM 00010: 2 AM/PM	
Registe	or Name - RTC DTA	ONFIDEN	 01001: 9 AM/PM 10000: 10 AM/PM 10001: 11 AM/PM 10010: 12 AM/PM	(
	(RW, Non EEPROM))		
Туре - (
Type - (EDTA	Enable or disable alarm register bytes for date	D: Disable the alarm register bytes for date 1: Enable the alarm register bytes for date	
	EDTA not used	•	for date 1: Enable the alarm register bytes for	
[7]		date Set alarm date (1-31) in BCD format. The	for date 1: Enable the alarm register bytes for date RTC ADT[5:0] BCD decode:	
[7] [6]	not used	Set alarm date (1-31) in BCD format. The alarm will be triggered once a match	for date 1: Enable the alarm register bytes for date RTC ADT[5:0] BCD decode: 000000: INVALID	
[7] [6] [5]	not used ADT21	Set alarm date (1-31) in BCD format. The alarm will be triggered once a match occurs between the alarm registers and	for date 1: Enable the alarm register bytes for date RTC ADT[5:0] BCD decode: 000000: INVALID 000001: date 1	
[7] [6] [5] [4]	not used ADT21 ADT20	Set alarm date (1-31) in BCD format. The alarm will be triggered once a match	for date 1: Enable the alarm register bytes for date RTC ADT[5:0] BCD decode: 000000: INVALID 000001: date 1 000010: date 2	
[7] [6] [5] [4]	not used ADT21 ADT20 ADT13	Set alarm date (1-31) in BCD format. The alarm will be triggered once a match occurs between the alarm registers and	for date 1: Enable the alarm register bytes for date RTC ADT[5:0] BCD decode: 000000: INVALID 000001: date 1 000010: date 2 001001: date 9	
[6] [5] [4] [3]	not used ADT21 ADT20 ADT13 ADT12	Set alarm date (1-31) in BCD format. The alarm will be triggered once a match occurs between the alarm registers and	for date 1: Enable the alarm register bytes for date RTC ADT[5:0] BCD decode: 000000: INVALID 000001: date 1 000010: date 2	
[6] [5] [4] [3] [2] [1]	not used ADT21 ADT20 ADT13 ADT12 ADT11	Set alarm date (1-31) in BCD format. The alarm will be triggered once a match occurs between the alarm registers and	for date 1: Enable the alarm register bytes for date RTC ADT[5:0] BCD decode: 000000: INVALID 000001: date 1 000010: date 2 001001: date 9	

(10	Register Name - RTC MOA Type - (RW, Non EEPROM)				0x00 /
	[7]	EMOA	Enable or disable alarm register bytes for month	Disable the alarm register bytes for month Enable the alarm register bytes for month	<0>
	[6:5]	not used			<00>
	[4]	AMO20	Set alarm month (1-12) in BCD format.	RTC AMO[4:0] BCD decode:	<0>
	[3]	AMO13	The alarm will be triggered once a match	00000: INVALID	<0>
	[2]	AMO12	bccurs between the alarm registers and the RTC registers for month	00001: 1st month (Jan) 00010: 2nd month (Feb)	<0>
	[1]	AMO11		00011: 3rd month (Mar)	<0>
	[0]	AMO10		 01001: 9th month (Sep) 10000: 10th month (Oct) 10001: 11th month (Nov) 10010: 12th month(Dec)	<0>
x11	Register	Name - RTC DW	4	10010. 12tif month(Dec)	0x00 /
		RW, Non EEPRON			
	[7]	EDWA	Enable or disable alarm register bytes for day of the week	Disable the alarm register bytes for day of the week Enable the alarm register bytes for day of the week	<0>
	[6:3]	not used	-		<0000
	[2]	ADW12	Set alarm day of the week (1-7). The	RTC ADW[2:0] decodes:	<0>
	[1]	ADW11	alarm will be triggered once a match	000: 1st day of the week 001: 2nd day of the week	<0>
	[0]	ADW10	occurs between the alarm registers and the RTC registers for day of the week	010: 2nd day of the week 010: 3rd day of the week	<0>
				110: 7th day of the week	
k12		· Name - RTC USF RW, Non EEPRON		1 1 / \L	0x00 /
	[7]	USR17	Battery-backed user memory storage		<0>
	[6]	USR16			<0>
	[5]	USR15			<0>
	[4]	USR14			
	[+]	USK 14			<0>
	[3]	USR13			
					<0>
	[3]	USR13			<0>
	[3] [2]	USR13 USR12			<0> <0>
x13	[3] [2] [1] [0] Register	USR13 USR12 USR11			<0> <0> <0> <0>
x13	[3] [2] [1] [0] Register Type - (F	USR13 USR12 USR11 USR10 TName - RTC USF			<0> <0> <0> <0> 0x00 /
x13	[3] [2] [1] [0] Register Type - (f	USR13 USR12 USR11 USR10 'Name - RTC USFRW, Non EEPRON	Л)		<0> <0> <0> <0> <0> <0> <0> <0> <0> <0>
k13	[3] [2] [1] [0] Register Type - (F	USR13 USR12 USR11 USR10 Name - RTC USFRW, Non EEPRON USR27 USR26	Л)		<0><0><0><0><0><0><0><0><0><0><0><0><0><
x13	[3] [2] [1] [0] Register Type - (F	USR13 USR12 USR11 USR10 Name - RTC USF RW, Non EEPRON USR27 USR26 USR25	Л)		<0><0><0><0><0><0><0><0><0><0><0><0><0><
x13	[3] [2] [1] [0] Register Type - (f [7] [6] [5]	USR13 USR12 USR11 USR10 Name - RTC USF RW, Non EEPRON USR27 USR26 USR25 USR24	Л)		<0><0><0><0><0><0><0><0><0><0><0><0><0><
x13	[3] [2] [1] [0] Register Type - (F [7] [6] [5] [4]	USR13 USR12 USR11 USR10 Name - RTC USF RW, Non EEPRON USR27 USR26 USR25 USR24 USR23	Л)		<0> <0> <0> <0> <0> <0> <0> <0> <0> <0>
x13	[3] [2] [1] [0] Register Type - (f [7] [6] [5]	USR13 USR12 USR11 USR10 Name - RTC USF RW, Non EEPRON USR27 USR26 USR25 USR24	M)		<0><0><0><0><0><0><0><0><0><0><0><0><0><

0x1E	_	r Name - Main Slave Ad RW, EEPROM)	ddress		0x00 /	
	[7]	not used			<0>	
	[6:0]	Main Slave Addr	Set the 7-bit main I2C slave address	0000000: slave address 0x12 0000001: slave address 0x01 0000010: slave address 0x02	<000000	
				1111111: slave address 0x7F		
0x1F	Register Name - RTC Slave Address Type - (RW, EEPROM)					
	[7]	not used			<0>	
	[6:0]	RTC Slave Addr	Set the 7-bit RTC I2C slave address	0000000: slave address 0x6F 0000001: slave address 0x01 0000010: slave address 0x02 1111111: slave address 0x7F	<000000	
0x20	_			<u> </u>	0x07 /	
	[7:5]	not used			<000>	
	[4]	Buck1 Phase Sync EN	Enable Buck1 Phase Synchronization function	0: Disabled 1: Enabled	<0>	
	[3]	Buck1 SS EN	Enable Buck1 PFM Spread Spectrum function in PFM mode	0: Disabled 1: Enabled	<0>	
	[2]	Buck1 ABS EN	Enable Buck1 ABS (Ultrasonic) mode	0: Disabled 1: Enabled	<1>	
	[1]	Buck1 EN SLEEP	Enable Buck1 in SLEEP state	0: Disabled 1: Enabled	<1>	
	[0]	Buck1 EN ACTIVE	Enable Buck1 in ACTIVE state	0: Disabled 1: Enabled	<1>	
)x21		r Name - Buck1 ACTIV RW, EEPROM)	Ė		0x06 /	
	[7:6]	not used			<00>	
	[5:4]	Buck1 Mode ACTIVE	Set Buck1 operation mode in ACTIVE state	00: Auto PFM/PWM mode 01: Forced PWM mode 1x: Reserved	<00>	
	[3:0]	Buck1 Vo ACTIVE	Set Buck1 output voltage in ACTIVE state	4'b0000 - 4'b1110: Buck1 = 0.8V + 0.05V x Buck1_Vo_ACTIVE[3:0] 4'b1111: 1.03V	<0110	
0x22		r Name - Buck1 SLEEF RW, EEPROM)			0x06 /	
	[7:6]	not used			<00>	
	[5:4]	Buck1 Mode SLEEP	Set Buck1 operation mode in SLEEP state	00: Auto PFM/PWM mode 01: Forced PWM mode 1x: Reserved	<00>	
	[3:0]	Buck1 Vo SLEEP	Set Buck1 output voltage in SLEEP state	4'b0000 - 4'b1110: Buck1 = 0.8V + 0.05V x Buck1_Vo_SLEEP[3:0]	<0110	

0x23		r Name - Buck1 Power RW, EEPROM)	On		0x02 / 2	
	[7]	not used			<0>	
	[6:0]	Buck1 Power On Delay	Delay timed from the beginning of power- on sequence	0: 0ms 1: 1ms 127: 127ms	<0000010>	
0x24	Register Name - Buck1 Power Off Type - (RW, EEPROM)					
	[7]	not used			<0>	
	[6:0]	Buck1 Power Off Delay	Delay timed from the beginning of power- off sequence	0: 0ms 1: 1ms 127: 127ms	<0111100>	
0x25	Register Name - Buck1 SR Type - (RW, EEPROM)					
	[7:6]	Buck1 TSoftStart	Set Buck1 soft-start time	00: 4ms 01: 2ms 10: 1ms 11: 0.5ms	<01>	
	[5:4]	Buck1 TShutDown	when Shutdown Option Buck is set to	00: 4ms 01: 2ms 10: 1ms 11: 0.5ms	<01>	
	[3:2]	Buck1 DVS SRup	Set Buck1 output ramp-up slew rate	00: 2mV/μs 01: 4mV/μs 10: 8mV/μs 11: 16mV/μs	<10>	
	[1:0]	Buck1 DVS SRdn	Set Buck1 output ramp-down slew rate	00: 2mV/μs 01: 4mV/μs 10: 8mV/μs 11: 16mV/μs	<10>	

	er Name - Buck1 Config (RW, EEPROM)			0x1:
[7]	not used			<
		b . b	In a	
[6:5]	Buck1 Phase Sync Delay	Set Buck1 phase shift relative to the inter- nal clock when Buck1 Phase Sync EN is enabled	00: 0deg 01: 90deg 10: 180deg 11: 270deg	<(
[4:2]	Buck1 SW Freq	Set Buck1 switching frequency when in PWM operation	000: 0.667MHz 001: 0.769MHz 010: 0.833MHz 011: 1MHz 100: 1.11MHz 101: 1.33MHz 110: 1.54MHz 111: 1.67MHz	<1
[1:0]	Buck1 Discharge	Set Buck1 output discharge resistance	00: Disabled 01: Slow 10: Medium 11: Fast	<
_	er Name - Buck2 Enable (RW, EEPROM)			0x0
[7:5]	not used			<(
[4]	Buck2 Phase Sync EN	Enable Buck2 Phase Synchronization function	0: Disabled 1: Enabled	1
[3]	Buck2 SS EN	Enable Buck2 PFM Spread Spectrum function in PFM mode	0: Disabled 1: Enabled	•
[2]	Buck2 ABS EN	Enable Buck2 ABS (Ultrasonic) mode	0: Disabled 1: Enabled	<
[1]	Buck2 EN SLEEP	Enable Buck2 in SLEEP state	0: Disabled 1: Enabled	•
[0]	Buck2 EN ACTIVE	Enable Buck2 in ACTIVE state	0: Disabled 1: Enabled	
	er Name - Buck2 ACTIV (RW, EEPROM)	E		0xi
[7:6]	not used			<
[5:4]	Buck2 Mode ACTIVE	Set Buck2 operation mode in ACTIVE state	00: Auto PFM/PWM mode 01: Forced PWM mode 1x: Reserved	<
[3:0]	Buck2 Vo ACTIVE	Set Buck2 output voltage in ACTIVE state	Buck2 = 1.1V + 0.05V x Buck2_Vo_ACTIVE[3:0]	<0
	er Name - Buck2 SLEEF (RW, EEPROM)			0x
[7:6]	not used			<
[5:4]		Set Buck2 operation mode in SLEEP state	e00: Auto PFM/PWM mode 01: Forced PWM mode 1x: Reserved	<
[3:0]	Buck2 Vo SLEEP	Set Buck2 output voltage in SLEEP state	Buck2 = 1.1V + 0.05V x Buck2_Vo_SLEEP[3:0]	<0

0x2A		Name - Buck2 Power RW, EEPROM)	On		0x03 / 3
	[7]	not used			<0>
	[6:0]	Buck2 Power On Delay	Delay timed from the beginning of power- on sequence	0: 0ms 1: 1ms	<0000011>
				127: 127ms	
)x2B	Register Name - Buck2 Power Off Type - (RW, EEPROM)				
	[7]	not used			<0>
	[6:0]	Buck2 Power Off Delay	Delay timed from the beginning of power- off sequence	0: 0ms 1: 1ms	<0111011>
				 127: 127ms	
:2C	Register Name - Buck2 SR Type - (RW, EEPROM)				
	[7:6]	Buck2 TSoftStart	Set Buck2 soft-start time	00: 4ms 01: 2ms 10: 1ms 11: 0.5ms	<01>
	[5:4]	Buck2 TShutDown	Set Buck2 shutdown period. Note: this setting sets the Shut Down SR when Shutdown Option Buck is set to 2b'00, 2b'01 or 2b'10. In addition, when CEN goes from high to low, the shutdown period starts to count from the time when the last rail is turned off. At the end of the shutdown period the FSM transitions to (STANDBY) then onward to {RESET}.	00: 4ms 01: 2ms 10: 1ms 11: 0.5ms	<01>
	[3:2]	Buck2 DVS SRup	Set Buck2 output ramp-up slew rate	00: 2mV/μs 01: 4mV/μs 10: 8mV/μs 11: 16mV/μs	<10>
	[1:0]	Buck2 DVS SRdn	Set Buck2 output ramp-down slew rate	00: 2mV/μs 01: 4mV/μs 10: 8mV/μs 11: 16mV/μs	<10>

-	ter Name - Buck2 Config · (RW, EEPROM)			0x06 / 6
[7]	not used			<0>
[6:5]	Buck2 Phase Sync Delay	Set Buck2 phase shift relative to the inter- nal clock when Buck1 Phase Sync EN is enabled	-00: 0deg 01: 90deg 10: 180deg 11: 270deg	<00>
[4:2]	Buck2 SW Freq	Set Buck2 switching frequency when in PWM operation	000: 0.667MHz 001: 0.769MHz 010: 0.833MHz 011: 1MHz 100: 1.11MHz 101: 1.33MHz 110: 1.54MHz 111: 1.67MHz	<001>
[1:0]	Buck2 Discharge	Set Buck2 output discharge resistance	00: Disabled 01: Slow 10: Medium 11: Fast	<10>
	ter Name - Buck3 Enable · (RW, EEPROM)	3		0x07 / 7
[7:5]	not used			<000>
[4]	Buck3 Phase Sync EN	Enable Buck3 Phase Synchronization function	0: Disabled 1: Enabled	<0>
[3]	Buck3 SS EN	Enable Buck3 PFM Spread Spectrum function in PFM mode	0: Disabled 1: Enabled	<0>
[2]	Buck3 ABS EN	Enable Buck3 ABS (Ultrasonic) mode	0: Disabled 1: Enabled	<1>
[1]	Buck3 EN SLEEP	Enable Buck3 in SLEEP state	0: Disabled 1: Enabled	<1>
[0]	Buck3 EN ACTIVE	Enable Buck3 in ACTIVE state	0: Disabled 1: Enabled	<1>
	er Name - Buck3 ACTIV · (RW, EEPROM)	Ė		0x00 / (
[7:6]	not used			<00>
[5:4]	Buck3 Mode ACTIVE	Set Buck3 operation mode in ACTIVE state	00: Auto PFM/PWM mode 01: Forced PWM mode 1x: Reserved	<00>
[3:0]	Buck3 Vo ACTIVE	Set Buck3 output voltage in ACTIVE state	Buck3 = 1.8V + 0.1V x Buck3_Vo_ACTIVE[3:0]	<0000>
	er Name - Buck3 SLEEF · (RW, EEPROM)	<u>,</u>	•	0x00 / 0
	not used			<00>
[7:6]		Set Buck3 operation mode in SLEEP state		<00>
[7:6] [5:4]	Buck3 Mode SLEEF		01: Forced PWM mode 1x: Reserved	

0x31		r Name - Buck3 Power RW, EEPROM)	On		0x02 / 2	
	[7]	not used			<0>	
	[6:0]	Buck3 Power On Delay	Delay timed from the beginning of power- on sequence	0: 0ms 1: 1ms 127: 127ms	<0000010>	
0x32	Register Name - Buck3 Power Off Type - (RW, EEPROM)					
	[7] not used				<0>	
	[6:0]	Buck3 Power Off Delay	Delay timed from the beginning of power- off sequence	0: 0ms 1: 1ms 127: 127ms	<0111100>	
0x33	Register Name - Buck3 SR Type - (RW, EEPROM)					
	[7:6]	Buck3 TSoftStart	Set Buck3 soft-start time	00: 4ms 01: 2ms 10: 1ms 11: 0.5ms	<01>	
	[5:4]	Buck3 TShutDown	when Shutdown Option Buck is set to	00: 4ms 01: 2ms 10: 1ms 11: 0.5ms	<01>	
	[3:2]	Buck3 DVS SRup	Set Buck3 output ramp-up slew rate	00: 2mV/μs 01: 4mV/μs 10: 8mV/μs 11: 16mV/μs	<10>	
	[1:0]	Buck3 DVS SRdn	Set Buck3 output ramp-down slew rate	00: 2mV/μs 01: 4mV/μs 10: 8mV/μs 11: 16mV/μs	<10>	

	er Name - Buck3 Config (RW, EEPROM)			0x1A
[7]	not used			<(
[6:5]	Buck3 Phase Sync Delay	Set Buck3 phase shift relative to the inter- nal clock when Buck1 Phase Sync EN is enabled	00: 0deg 01: 90deg 10: 180deg 11: 270deg	<0
[4:2]	Buck3 SW Freq	Set Buck3 switching frequency when in PWM operation	000: 0.667MHz 001: 0.769MHz 010: 0.833MHz 011: 1MHz 100: 1.11MHz 101: 1.33MHz 110: 1.54MHz 111: 1.67MHz	<11
[1:0]	Buck3 Discharge	Set Buck3 output discharge resistance	00: Disabled 01: Slow 10: Medium 11: Fast	<1
	er Name - Buck4 Enable (RW, EEPROM)	3	•	0x0
[7:5]	not used			<00
[4]	Buck4 Phase Sync EN	Enable Buck4 Phase Synchronization function	0: Disabled 1: Enabled	<(
[3]	Buck4 SS EN	Enable Buck4 PFM Spread Spectrum function in PFM mode	0: Disabled 1: Enabled	<(
[2]	Buck4 ABS EN	Enable Buck4 ABS (Ultrasonic) mode	0: Disabled 1: Enabled	<
[1]	Buck4 EN SLEEP	Enable Buck4 in SLEEP state	0: Disabled 1: Enabled	<
[0]	Buck4 EN ACTIVE	Enable Buck4 in ACTIVE state	0: Disabled 1: Enabled	<
	er Name - Buck4 ACTIV (RW, EEPROM)	Ë		0x0F
[7:6]	not used			<0
[5:4]	Buck4 Mode ACTIVE	Set Buck4 operation mode in ACTIVE state	00: Auto PFM/PWM mode 01: Forced PWM mode 1x: Reserved	<0
[3:0]	Buck4 Vo ACTIVE	Set Buck4 output voltage in ACTIVE state	A0: Vo=1.8V + 0.1V x Buck4_Vo_ACTIVE[3:0] A1: Codes 0-8 *decimal Vo= 0.8V + 0.05V x Buck4_Vo_AC- TIVE[3:0] A1: Codes 9-15 decimal Vo= 1.5, 1.6, 1.8, 1.85, 2.2, 2.5, 3.3	<11

Туре - (r Name - Buck4 SLEEF (RW, EEPROM)			0x0F / 15
[7:6]	not used			<00>
[5:4]	Buck4 Mode SLEEF	Set Buck4 operation mode in SLEEP state	00: Auto PFM/PWM mode 01: Forced PWM mode 1x: Reserved	<00>
[3:0]	Buck4 Vo SLEEP	Set Buck4 output voltage in SLEEP state	A0: Vo=1.8V + 0.1V x Buck4_Vo_SLEEP[3:0] A1: Codes 0-8 *decimal Vo= 0.8V + 0.05V x Buck4_Vo_SLEEP[3:0] A1: Codes 9-15 decimal Vo= 1.5, 1.6, 1.8, 1.85, 2.2, 2.5, 3.3	<1111>
	r Name - Buck4 Power RW, EEPROM)	On		0x0A / 1
[7]	not used			<0>
[7] [6:0]	Buck4 Power On	Delay timed from the beginning of power-	D: 0ms	<0001010
[0.0]	Delay	on sequence	1: 1ms 127: 127ms	-0001010
	Register Name - Buck4 Power Off Type - (RW, EEPROM)			0x00 / 0
	,			
[7]	hot used	NIEIDEN	ITIAI	<0>
[7] [6:0]		Delay timed from the beginning of power- off sequence	0: 0ms 1: 1ms	
	not used Buck4 Power Off			
[6:0]	not used Buck4 Power Off		1: 1ms 	<0000000
[6:0]	not used Buck4 Power Off Delay r Name - Buck4 SR		1: 1ms 	<0> <0000000 0x5A / 90 <01>
[6:0] Registe Type - (not used Buck4 Power Off Delay r Name - Buck4 SR (RW, EEPROM)	off sequence	1: 1ms 127: 127ms 00: 4ms 01: 2ms 10: 1ms 11: 0.5ms 00: 4ms 01: 2ms 10: 1ms 11: 0.5ms	<0000000 0x5A / 9
[6:0] Registe Type - ([7:6]	not used Buck4 Power Off Delay r Name - Buck4 SR RW, EEPROM) Buck4 TSoftStart	Set Buck4 soft-start time Set Buck4 shutdown period. Note: this setting sets the Shut Down SR when Shutdown Option Buck is set to 2b'00, 2b'01 or 2b'10. In addition, when CEN goes from high to low, the shutdown period starts to count from the time when the last rail is turned off. At the end of the shutdown period the FSM transitions to	1: 1ms 127: 127ms 00: 4ms 01: 2ms 10: 1ms 11: 0.5ms 00: 4ms 01: 2ms 10: 1ms 11: 0.5ms	<0000000 0x5A / 9 <01>

x3B		r Name - Buck4 Config RW, EEPROM)			0x1A / 2
	[7]	not used			<0>
	[6:5]	Buck4 Phase Sync Delay	Set Buck4 phase shift relative to the inter- nal clock when Buck1 Phase Sync EN is enabled	00: 0deg 01: 90deg 10: 180deg 11: 270deg	<00>
	[4:2]	Buck4 SW Freq	Set Buck4 switching frequency when in PWM operation	000: 0.667MHz 001: 0.769MHz 010: 0.833MHz 011: 1MHz 100: 1.11MHz 101: 1.33MHz 110: 1.54MHz 111: 1.67MHz	<110>
	[1:0]	Buck4 Discharge	Set Buck4 output discharge resistance	00: Disabled 01: Slow 10: Medium 11: Fast	<10>
хЗС	_	r Name - Buck5 Enable RW, EEPROM)	3		0x07 /
	[7:5]	not used			<000>
	[4]	Buck5 Phase Sync EN	Enable Buck5 Phase Synchronization function	0: Disabled 1: Enabled	<0>
	[3]	Buck5 SS EN	Enable Buck5 PFM Spread Spectrum function in PFM mode	0: Disabled 1: Enabled	<0>
	[2]	Buck5 ABS EN	Enable Buck5 ABS (Ultrasonic) mode	0: Disabled 1: Enabled	<1>
	[1]	Buck5 EN SLEEP	Enable Buck5 in SLEEP state	0: Disabled 1: Enabled	<1>
	[0]	Buck5 EN ACTIVE	Enable Buck5 in ACTIVE state	0: Disabled 1: Enabled	<1>
x3D		r Name - Buck5 ACTIV RW, EEPROM)	É		0x00 /
	[7:5]	not used			<000>
	[4:3]	Buck5 Mode ACTIVE	Set Buck5 operation mode in ACTIVE state	00: Auto PFM/PWM mode 01: Forced PWM mode 1x: Reserved	<00>
	[2:0]	Buck5 Vo ACTIVE	Set Buck5 output voltage in ACTIVE state	000: 1.2V 001: 1.5V 010: 1.6V 011: 1.8V 100: 1.85V 101: 2.2V 110: 2.5V 111: 3.3V	<000>

Type - (r Name - Buck5 SLEEF RW, EEPROM)	5		0x00
[7:5]	not used			<000
[4:3]	Buck5 Mode SLEEF	Set Buck5 operation mode in SLEEP state	00: Auto PFM/PWM mode 01: Forced PWM mode 1x: Reserved	<00
[2:0]	Buck5 Vo SLEEP	Set Buck5 output voltage in SLEEP state	000: 1.2V 001: 1.5V 010: 1.6V 011: 1.8V 100: 1.85V 101: 2.2V 110: 2.5V 111: 3.3V	<000
_	r Name - Buck5 Power RW, EEPROM)	On		0x0F /
[7]	not used			<0>
[6:0]	Buck5 Power On	Delay timed from the beginning of power-	0: 0ms	<00011
[0.0]	Delay	on sequence	1: 1ms 	
			127: 127ms	
Register Name - Buck5 Power Off Type - (RW, EEPROM)				
	not used			<0>
[7]	not used	Delay timed from the beginning of newer	h: 0ma	<0>
[6:0]	not used Buck5 Power Off Delay	Delay timed from the beginning of power- off sequence	0: 0ms 1: 1ms 127: 127ms	
[6:0] Registe	Buck5 Power Off		1: 1ms	<00000
[6:0] Registe	Buck5 Power Off Delay r Name - Buck5 SR		1: 1ms	0x5A /
[6:0] Registe Type - (Buck5 Power Off Delay r Name - Buck5 SR RW, EEPROM)	Set Buck5 soft-start time Set Buck5 shutdown period. Note: this setting sets the Shut Down SR when Shutdown Option Buck is set to	1: 1ms 127: 127ms 00: 4ms 01: 2ms 10: 1ms	<00000 0x5A /
[6:0] Registe Type - ([7:6]	Buck5 Power Off Delay r Name - Buck5 SR RW, EEPROM) Buck5 TSoftStart	Set Buck5 soft-start time Set Buck5 shutdown period. Note: this setting sets the Shut Down SR when Shutdown Option Buck is set to 2b'00, 2b'01 or 2b'10. In addition, when CEN goes from high to low, the shutdown period starts to count from the time when the last rail is turned off. At the end of the shutdown period the FSM transitions to	1: 1ms 127: 127ms 00: 4ms 01: 2ms 10: 1ms 11: 0.5ms 00: 4ms 01: 2ms 10: 1ms	<00000 0x5A /

1,750 (r Name - Buck5 Config RW, EEPROM)			0x1A / 2	
[7]	not used			<0>	
[6:5]	Buck5 Phase Sync Delay	Set Buck5 phase shift relative to the inter- nal clock when Buck1 Phase Sync EN is enabled	00: 0deg 01: 90deg 10: 180deg 11: 270deg	<00>	
[4:2]	Buck5 SW Freq	Set Buck5 switching frequency when in PWM operation	000: 0.667MHz 001: 0.769MHz 010: 0.833MHz 011: 1MHz 100: 1.11MHz 101: 1.33MHz 110: 1.54MHz 111: 1.67MHz	<110>	
[1:0]	Buck5 Discharge	Set Buck5 output discharge resistance	00: Disabled 01: Slow 10: Medium 11: Fast	<10>	
	Register Name - Buck6 Enable Type - (RW, EEPROM)				
[7:5]	not used			<000>	
[4]	Buck6 Phase Sync EN	Enable Buck6 Phase Synchronization function	0: Disabled 1: Enabled	<0>	
[3]	Buck6 SS EN	Enable Buck6 PFM Spread Spectrum function in PFM mode	0: Disabled 1: Enabled	<0>	
[2]	Buck6 ABS EN	Enable Buck6 ABS (Ultrasonic) mode	0: Disabled 1: Enabled	<1>	
[1]	Buck6 EN SLEEP	Enable Buck6 in SLEEP state	0: Disabled 1: Enabled	<1>	
[0]	Buck6 EN ACTIVE	Enable Buck6 in ACTIVE state	0: Disabled 1: Enabled	<1>	
_	r Name - Buck6 ACTIV RW, EEPROM)	Ē		0xD0 / 2	
[7]	Link Buck6 to Buck2	Link the sequencing of Buck 6 to Buck 2	0: Buck 6 and Buck 2 soft-start inde- pendently 1: Buck 6 and Buck 2 soft-start together	<1>	
[6]	VTTREF EN	When VTTREF EN is set to '1', buck6 (VTT) = VREFOUT	0: Disabled 1: Enabled	<1>	
	1				
[5:4]	Buck6 Mode ACTIVE	Set Buck6 operation mode in ACTIVE state	00: Auto PFM/PWM mode 01: Forced PWM mode 1x: Reserved	<01>	
[5:4] [3:0]		•	01: Forced PWM mode		
[3:0] x45 Registe	ACTIVE	state	01: Forced PWM mode	<0000	
[3:0] x45 Registe	ACTIVE reserved r Name - Buck6 SLEEF	state	01: Forced PWM mode	<0000 0xC0 / 1	
[3:0] (45 Register Type - (ACTIVE reserved r Name - Buck6 SLEEF RW, EEPROM) EnPD VTTRef	state	01: Forced PWM mode 1x: Reserved 00: Disabled 01: Slow 10: Medium 11: Fast	<01> <0000: 0xC0 / 1 <11>	

0x46		r Name - Buck6 Power RW, EEPROM)	On		0x0A / 10	
	[7]	not used			<0>	
	[6:0]	Buck6 Power On Delay	Delay timed from the beginning of power- on sequence	0: 0ms 1: 1ms 127: 127ms	<0001010>	
0x47	Register Name - Buck6 Power Off Type - (RW, EEPROM)					
	[7]	not used			<0>	
	[6:0]	Buck6 Power Off Delay	Delay timed from the beginning of power- off sequence	0: 0ms 1: 1ms 127: 127ms	<0000000>	
0x48	Register Name - Buck6 SR Type - (RW, EEPROM)					
	[7:6]	Buck6 TSoftStart	Set Buck6 soft-start time	00: 4ms 01: 2ms 10: 1ms 11: 0.5ms	<01>	
	[5:4]	Buck6 TShutDown	when Shutdown Option Buck is set to	00: 4ms 01: 2ms 10: 1ms 11: 0.5ms	<01>	
	[3:2]	Buck6 DVS SRup	Set Buck6 output ramp-up slew rate	00: 2mV/μs 01: 4mV/μs 10: 8mV/μs 11: 16mV/μs	<10>	
	[1:0]	Buck6 DVS SRdn	Set Buck6 output ramp-down slew rate	00: 2mV/μs 01: 4mV/μs 10: 8mV/μs 11: 16mV/μs	<10>	

	r Name - Buck6 Config RW, EEPROM)			0x0
[7]	Last ward			<
[7]	not used			
[6:5]	Buck6 Phase Sync Delay	Set Buck6 phase shift relative to the inter- nal clock when Buck1 Phase Sync EN is enabled	00: 0deg 01: 90deg 10: 180deg 11: 270deg	<(
[4:2]	Buck6 SW Freq	Set Buck6 switching frequency when in PWM operation	000: 0.667MHz 001: 0.769MHz 010: 0.833MHz 011: 1MHz 100: 1.11MHz 101: 1.33MHz 110: 1.54MHz 111: 1.67MHz	<0
[1:0]	Buck6 Discharge	Set Buck6 output discharge resistance when it is configured as an individual regu- lator	00: Disabled 01: Slow 10: Medium 11: Fast	<
Registe	r Name - LDO1 ACTIVI		•	0x70
Type - (RW, EEPROM)			
[7]	LDO1 Bypass	Set LDO1 to bypass mode	0: Normal LDO mode 1: Bypass mode	<
[6]	LDO1 EN ACTIVE	Enable LDO1 in ACTIVE state	0: Disabled 1: Enabled	<
[5:3]	LDO1 Vo 1 ACTIVE	Set LDO1 output voltage in ACTIVE state		<1
	CC	DNFIDEN	010: 1.2V 011: 1.5V 100: 1.8V 101: 2.5V 110: 3V 111: 3.3V	
[2:0]	LDO1 Vo 0 ACTIVE	Set LDO1 output voltage in ACTIVE state when LDO_SEL1 = LOW	000: 0.8V 001: 0.9V 010: 1.2V 011: 1.5V 100: 1.8V 101: 2.5V 110: 3V 111: 3.3V	<1
	r Name - LDO1 SLEEP RW, EEPROM)			0x0
	not used			<00
[7:4]	LDO4 ENICLEED	Enable LDO1 in SLEEP state	0: Disabled	<
[7:4] [3] [2:0]	LDO1 EN SLEEP	Set LDO1 output voltage in SLEEP state	1: Enabled 000: 0.8V	<1

0x4C		Name - LDO1 Power RW, EEPROM)	On		0x0A / 10
	[7]	not used			<0>
	[6:0]	LDO1 Power On Delay	Delay timed from the beginning of power- on sequence	0: 0ms 1: 1ms	<0001010>
				127: 127ms	
0x4D		Name - LDO1 Power RW, EEPROM)	Öff	,	0x00 / 0
	[7]	not used			<0>
	[6:0]	LDO1 Power Off Delay	Delay timed from the beginning of power- off sequence	0: 0ms 1: 1ms	<0000000>
				 127: 127ms	
)x4E		Name - LDO1 SR RW, EEPROM)		•	0x5A / 90
	[7:6]	LDO1 TSoftStart	Set LDO1 soft-start time	00: 4ms 01: 2ms 10: 1ms 11: 0.5ms	<01>
	[5:4]	LDO1 TShutDown	Set LDO1 shutdown period. Note: this setting sets the Shut Down SR when Shutdown Option Buck is set to 2b'00, 2b'01 or 2b'10. In addition, when CEN goes from high to low, the shutdown period starts to count from the time when the last rail is turned off. At the end of the shutdown period the FSM transitions to (STANDBY) then onward to {RESET}.	00: 4ms 01: 2ms 10: 1ms 11: 0.5ms	<01>
	[3:2]	LDO1 DVS SRup	Set LDO1 output ramp-up slew rate	00: 2mV/μs 01: 4mV/μs 10: 8mV/μs 11: 16mV/μs	<10>
	[1:0]	LDO1 DVS SRdn	Set LDO1 output ramp-down slew rate	00: 2mV/μs 01: 4mV/μs 10: 8mV/μs 11: 16mV/μs	<10>

0x4F		r Name - LDO2 ACTIVI (RW, EEPROM)			0x7C / 12	
	171	DOO Dumana	Catt DOO to humana mada	h. Named I DO made	<0>	
	[7]	LDO2 Bypass	Set LDO2 to bypass mode	0: Normal LDO mode 1: Bypass mode	<0>	
	[6]	LDO2 EN ACTIVE	Enable LDO2 in ACTIVE state	0: Disabled 1: Enabled	<1>	
	[5:3]	LDO2 Vo 1 ACTIVE	Set LDO2 output voltage in ACTIVE state when LDO_SEL2 = HIGH	000: 0.8V 001: 0.9V	<111>	
			WHICH EDO_OLLZ = THOTT	010: 1.2V 011: 1.5V		
				100: 1.8V 101: 2.5V 110: 3V		
				111: 3.3V		
	[2:0]	LDO2 Vo 0 ACTIVE	Set LDO2 output voltage in ACTIVE state when LDO_SEL2 = LOW	000: 0.8V 001: 0.9V 010: 1.2V	<100>	
				011: 1.5V 100: 1.8V		
				101: 2.5V 110: 3V 111: 3.3V		
0x50	111: 3.3V					
	[7:4]	not used			<0000>	
	[3]	LDO2 EN SLEEP	Enable LDO2 in SLEEP state	0: Disabled 1: Enabled	<1>	
	[2:0]	LDO2 Vo SLEEP		000: 0.8V 001: 0.9V 010: 1.2V	<100>	
				010. 1.2V 011: 1.5V 100: 1.8V		
				101: 2.5V 110: 3V 111: 3.3V		
0x51	Registe	r Name - LDO2 Power	On	111. 3.3V	0x0A / 10	
	Type - ((RW, EEPROM)				
	[7]	not used			<0>	
	[6:0]	LDO2 Power On Delay	Delay timed from the beginning of power- on sequence	0: 0ms 1: 1ms	<0001010	
				127: 127ms		
0x52		r Name - LDO2 Power (RW, EEPROM)	Off		0x00 / 0	
	[7]	not used			<0>	
	[6:0]	LDO2 Power Off Delay	Delay timed from the beginning of power- off sequence	0: 0ms 1: 1ms	<0000000	
				 127: 127ms		

_	er Name - LDO2 SR (RW, EEPROM)			0x5A
[7:6]	LDO2 TSoftStart	Set LDO2 soft-start time	00: 4ms 01: 2ms 10: 1ms 11: 0.5ms	<01
[5:4]	LDO2 TShutDown	when Shutdown Option Buck is set to	00: 4ms 01: 2ms 10: 1ms 11: 0.5ms	<01
[3:2]	LDO2 DVS SRup	Set LDO2 output ramp-up slew rate	00: 2mV/μs 01: 4mV/μs 10: 8mV/μs 11: 16mV/μs	<10
[1:0]	LDO2 DVS SRdn	Set LDO2 output ramp-down slew rate	00: 2mV/μs 01: 4mV/μs 10: 8mV/μs 11: 16mV/μs	<10
Dowint-	Ar Nome I DOS ACTIVA			
Type -	er Name - LDO3 ACTIV (RW, EEPROM)		N. Disabled	
Type - [7]	(RW, EEPROM) LDO3 EN SLEEP	Enable LDO3 in SLEEP state	0: Disabled 1: Enabled	<1
Type -	(RW, EEPROM)	Enable LDO3 in SLEEP state Enable LDO3 in ACTIVE state		<1
Type - [7]	(RW, EEPROM) LDO3 EN SLEEP	Enable LDO3 in SLEEP state Enable LDO3 in ACTIVE state Set LDO3 output voltage in SLEEP state	1: Enabled 0: Disabled	<1
Type - [7]	(RW, EEPROM) LDO3 EN SLEEP LDO3 EN ACTIVE	Enable LDO3 in SLEEP state Enable LDO3 in ACTIVE state Set LDO3 output voltage in SLEEP state Set LDO3 output voltage in ACTIVE state	1: Enabled 0: Disabled 1: Enabled 000: 0.8V 001: 0.9V 010: 1.2V 011: 1.5V 100: 1.8V 101: 2.5V 110: 3V 111: 3.3V	<1 <1 <10
[7] [6] [5:3]	(RW, EEPROM) LDO3 EN SLEEP LDO3 EN ACTIVE LDO3 Vo SLEEP	Enable LDO3 in SLEEP state Enable LDO3 in ACTIVE state Set LDO3 output voltage in SLEEP state Set LDO3 output voltage in ACTIVE state	1: Enabled 0: Disabled 1: Enabled 000: 0.8V 001: 0.9V 010: 1.2V 011: 1.5V 100: 1.8V 101: 2.5V 110: 3.V 111: 3.3V 000: 0.8V 001: 0.9V 010: 1.2V 011: 1.5V 100: 1.8V 101: 2.5V 110: 3.V	<10
[7] [6] [5:3]	LDO3 EN SLEEP LDO3 EN ACTIVE LDO3 Vo SLEEP LDO3 Vo ACTIVE	Enable LDO3 in SLEEP state Enable LDO3 in ACTIVE state Set LDO3 output voltage in SLEEP state Set LDO3 output voltage in ACTIVE state	1: Enabled 0: Disabled 1: Enabled 000: 0.8V 001: 0.9V 010: 1.2V 011: 1.5V 100: 1.8V 101: 2.5V 110: 3.V 111: 3.3V 000: 0.8V 001: 0.9V 010: 1.2V 011: 1.5V 100: 1.8V 101: 2.5V 110: 3.V	<10 <10 0x02
[7] [6] [5:3] [2:0] Register Type -	LDO3 EN SLEEP LDO3 EN ACTIVE LDO3 Vo SLEEP LDO3 Vo ACTIVE	Enable LDO3 in SLEEP state Enable LDO3 in ACTIVE state Set LDO3 output voltage in SLEEP state Set LDO3 output voltage in ACTIVE state	1: Enabled 0: Disabled 1: Enabled 000: 0.8V 001: 0.9V 010: 1.2V 011: 1.5V 100: 1.8V 101: 2.5V 110: 3.V 111: 3.3V 000: 0.8V 001: 0.9V 010: 1.2V 011: 1.5V 100: 1.8V 101: 2.5V 110: 3.V 111: 3.3V	0xED

	ter Name - LDO3 Power · (RW, EEPROM)	Off		0x46 /
	T			
[7]	not used			<0:
[6:0]	LDO3 Power Off Delay	Delay timed from the beginning of power- off sequence	0: 0ms 1: 1ms	<10001
			127: 127ms	
	er Name - LDO3 SR · (RW, EEPROM)	•		0x5A
[7·6]	LDO3 TSoftStart	Set LDO3 soft-start time	00: 4ms	<01
[7:6]	LDOS TSURSIARI	Set EDOS Suit-Start time	01: 2ms 10: 1ms 11: 0.5ms	V 01
[5:4]	LDO3 TShutDown	Set LDO3 shutdown period. Note: this setting sets the Shut Down SR when Shutdown Option Buck is set to 2b'00, 2b'01 or 2b'10. In addition, when CEN goes from high to low, the shutdown period starts to count from the time when the last rail is turned off. At the end of the shutdown period the FSM transitions to (STANDBY) then onward to {RESET}.	00: 4ms 01: 2ms 10: 1ms 11: 0.5ms	<01
[3:2]	LDO3 DVS SRup	LDO3 DVS SRup Set LDO3 output ramp-up slew rate	00: 2mV/μs 01: 4mV/μs 10: 8mV/μs 11: 16mV/μs	<10
[1:0]	LDO3 DVS SRdn		00: 2mV/μs 01: 4mV/μs 10: 8mV/μs 11: 16mV/μs	<10
	er Name - LDOs Config · (RW, EEPROM)	1		0x2A
[7]	not used			<0:
[6]	LDO3 Bypass	Set LDO3 to bypass mode	0: Normal LDO mode 1: Bypass mode	<0:
[5:4]	5:4] LDO3 Discharge		00: Disabled 01: Slow 10: Medium 11: Fast	<10:
[3:2]	LDO2 Discharge	Set LDO2 output discharge resistance	00: Disabled 01: Slow 10: Medium 11: Fast	<10
[1:0]	LDO1 Discharge	Set LDO1 output discharge resistance	00: Disabled 01: Slow 10: Medium 11: Fast	<10

''	(RW, Non EEPROM)	Status 1		0x0
[7:6]	not used			<0
[5]	Buck6 UV Latched	Buck6 undervoltage fault latched bit. Write		<(
[4]	Buck5 UV Latched	1' to clear the fault Buck5 undervoltage fault latched bit. Write		<(
[3]	Buck4 UV Latched	1' to clear the fault Buck4 undervoltage fault latched bit. Write	, ,	<(
[2]	Buck3 UV Latched	1' to clear the fault Buck3 undervoltage fault latched bit. Write		<(
[1]	Buck2 UV Latched	1' to clear the fault Buck2 undervoltage fault latched bit. Write		<(
[0]	Buck1 UV Latched	1' to clear the fault Buck1 undervoltage fault latched bit. Write		<(
	er Name - Fault Latched (RW, Non EEPROM)	1' to clear the fault Status 2	1: Undervoltage fault occurs	0x0
	(,			
[7:4]	not used			<00
[3]	VIO Pgood Latched	VIO Pgood latched bit. Write '1' to clear the fault	0: OK (normal) 1: VIO level below its power-good threshold	\
[2]	LDO3 UV Latched	LDO3 undervoltage fault latched bit. Write 1' to clear the fault	Undervoltage fault occurs	<
[1]	LDO2 UV Latched	LDO2 undervoltage fault latched bit. Write 1' to clear the fault	0: OK (normal) 1: Undervoltage fault occurs	<
[0]	LDO1 UV Latched	LDO1 undervoltage fault latched bit. Write 1' to clear the fault Status 3	0: OK (normal) 1: undervoltage fault occurs	
Regist	LDO1 UV Latched er Name - Fault Latched (RW, Non EEPROM)	1' to clear the fault	0: OK (normal) 1: undervoltage fault occurs	
Regist	er Name - Fault Latched	1' to clear the fault Status 3	1: undervoltage fault occurs	0x0
Regist Type -	er Name - Fault Latched (RW, Non EEPROM)	1' to clear the fault Status 3	D: OK (normal) 1: undervoltage fault occurs D: OK (normal) 1: Overvoltage fault occurs	0x0
Regist Type -	er Name - Fault Latched (RW, Non EEPROM) not used	1' to clear the fault Status 3 Buck6 overvoltage fault latched bit. Write	1: undervoltage fault occurs 0: OK (normal)	0x0 <0
Regist Type - [7:6]	rer Name - Fault Latched (RW, Non EEPROM) not used Buck6 OV Latched	Status 3 Buck6 overvoltage fault latched bit. Write 1' to clear the fault Buck5 overvoltage fault latched bit. Write	1: undervoltage fault occurs 0: OK (normal) 1: Overvoltage fault occurs 0: OK (normal) 1: Overvoltage fault occurs	0x0 <0 <1
Regist Type - [7:6] [5]	hot used Buck6 OV Latched	Buck6 overvoltage fault latched bit. Write 1' to clear the fault Buck5 overvoltage fault latched bit. Write 1' to clear the fault Buck4 overvoltage fault latched bit. Write	1: undervoltage fault occurs 0: OK (normal) 1: Overvoltage fault occurs 0: OK (normal) 1: Overvoltage fault occurs 0: OK (normal)	0x0 <0 <1
Regist Type - [7:6] [5] [4]	hot used Buck6 OV Latched Buck4 OV Latched	Buck6 overvoltage fault latched bit. Write 1' to clear the fault Buck5 overvoltage fault latched bit. Write 1' to clear the fault Buck4 overvoltage fault latched bit. Write 1' to clear the fault Buck3 overvoltage fault latched bit. Write 1' to clear the fault	1: undervoltage fault occurs 0: OK (normal) 1: Overvoltage fault occurs 0: OK (normal) 1: Overvoltage fault occurs 0: OK (normal) 1: Overvoltage fault occurs 0: OK (normal)	0x0 <0 <1
Regist Type - [7:6] [5] [4] [3]	hot used Buck6 OV Latched Buck4 OV Latched Buck3 OV Latched	Buck6 overvoltage fault latched bit. Write 1' to clear the fault Buck5 overvoltage fault latched bit. Write 1' to clear the fault Buck4 overvoltage fault latched bit. Write 1' to clear the fault Buck3 overvoltage fault latched bit. Write 1' to clear the fault Buck3 overvoltage fault latched bit. Write 1' to clear the fault Buck2 overvoltage fault latched bit. Write	1: undervoltage fault occurs 0: OK (normal) 1: Overvoltage fault occurs 0: OK (normal) 1: Overvoltage fault occurs 0: OK (normal) 1: Overvoltage fault occurs 0: OK (normal) 1: Overvoltage fault occurs 0: OK (normal) 0: OK (normal)	0x0 <(C) <() <() <()
Regist Type - [7:6] [5] [4] [2] [1] [0] Regist	not used Buck6 OV Latched Buck4 OV Latched Buck3 OV Latched Buck2 OV Latched	Buck6 overvoltage fault latched bit. Write 1' to clear the fault Buck5 overvoltage fault latched bit. Write 1' to clear the fault Buck4 overvoltage fault latched bit. Write 1' to clear the fault Buck3 overvoltage fault latched bit. Write 1' to clear the fault Buck3 overvoltage fault latched bit. Write 1' to clear the fault Buck2 overvoltage fault latched bit. Write 1' to clear the fault Buck1 overvoltage fault latched bit. Write 1' to clear the fault	1: undervoltage fault occurs 0: OK (normal) 1: Overvoltage fault occurs 0: OK (normal) 1: Overvoltage fault occurs 0: OK (normal) 1: Overvoltage fault occurs 0: OK (normal) 1: Overvoltage fault occurs 0: OK (normal) 1: Overvoltage fault occurs 0: OK (normal) 1: Overvoltage fault occurs 0: OK (normal)	0x0
Regist Type - [7:6] [5] [4] [2] [1] [0] Regist	hot used Buck6 OV Latched Buck5 OV Latched Buck4 OV Latched Buck3 OV Latched Buck2 OV Latched Buck1 OV Latched	Buck6 overvoltage fault latched bit. Write 1' to clear the fault Buck5 overvoltage fault latched bit. Write 1' to clear the fault Buck4 overvoltage fault latched bit. Write 1' to clear the fault Buck3 overvoltage fault latched bit. Write 1' to clear the fault Buck3 overvoltage fault latched bit. Write 1' to clear the fault Buck2 overvoltage fault latched bit. Write 1' to clear the fault Buck1 overvoltage fault latched bit. Write 1' to clear the fault	1: undervoltage fault occurs 0: OK (normal) 1: Overvoltage fault occurs 0: OK (normal) 1: Overvoltage fault occurs 0: OK (normal) 1: Overvoltage fault occurs 0: OK (normal) 1: Overvoltage fault occurs 0: OK (normal) 1: Overvoltage fault occurs 0: OK (normal) 1: Overvoltage fault occurs 0: OK (normal)	0x0 <0 <0 <0 <0 <0 <0 <0 <0 <0 <0 <0 <0 <
Regist Type - [7:6] [5] [4] [2] [1] [0] Regist Type -	hot used Buck6 OV Latched Buck5 OV Latched Buck4 OV Latched Buck3 OV Latched Buck1 OV Latched Buck1 OV Latched Buck1 OV Latched Buck1 OV Latched	Buck6 overvoltage fault latched bit. Write 1' to clear the fault Buck5 overvoltage fault latched bit. Write 1' to clear the fault Buck4 overvoltage fault latched bit. Write 1' to clear the fault Buck3 overvoltage fault latched bit. Write 1' to clear the fault Buck3 overvoltage fault latched bit. Write 1' to clear the fault Buck2 overvoltage fault latched bit. Write 1' to clear the fault Buck1 overvoltage fault latched bit. Write 1' to clear the fault	1: undervoltage fault occurs 0: OK (normal) 1: Overvoltage fault occurs 0: OK (normal) 1: Overvoltage fault occurs 0: OK (normal) 1: Overvoltage fault occurs 0: OK (normal) 1: Overvoltage fault occurs 0: OK (normal) 1: Overvoltage fault occurs 0: OK (normal) 1: Overvoltage fault occurs 0: OK (normal)	0x0 <0x0 <1 <1 <1 <1 <1 <1 <1 <1 <1 <
Regist Type - [7:6] [5] [4] [3] [1] [0] Regist Type - [7:1] [0]	hot used Buck6 OV Latched Buck4 OV Latched Buck3 OV Latched Buck2 OV Latched Buck1 OV Latched	Buck6 overvoltage fault latched bit. Write 1' to clear the fault Buck5 overvoltage fault latched bit. Write 1' to clear the fault Buck4 overvoltage fault latched bit. Write 1' to clear the fault Buck3 overvoltage fault latched bit. Write 1' to clear the fault Buck3 overvoltage fault latched bit. Write 1' to clear the fault Buck2 overvoltage fault latched bit. Write 1' to clear the fault Buck1 overvoltage fault latched bit. Write 1' to clear the fault Status 4 Buck1 high current warning latched bit. Write '1' to clear the fault	1: undervoltage fault occurs 0: OK (normal) 1: Overvoltage fault occurs 0: OK (normal) 1: Overvoltage fault occurs 0: OK (normal) 1: Overvoltage fault occurs 0: OK (normal) 1: Overvoltage fault occurs 0: OK (normal) 1: Overvoltage fault occurs 0: OK (normal) 1: Overvoltage fault occurs 0: OK (normal) 1: Overvoltage fault occurs	0x0 <0x0 <1 <1 <1 <1 <1 <1 <1 <1 <1 <
Regist Type - [7:6] [5] [4] [3] [1] [0] Regist Type - [7:1] [0]	hot used Buck6 OV Latched Buck5 OV Latched Buck4 OV Latched Buck3 OV Latched Buck2 OV Latched Buck1 OV Latched	Buck6 overvoltage fault latched bit. Write 1' to clear the fault Buck5 overvoltage fault latched bit. Write 1' to clear the fault Buck4 overvoltage fault latched bit. Write 1' to clear the fault Buck3 overvoltage fault latched bit. Write 1' to clear the fault Buck3 overvoltage fault latched bit. Write 1' to clear the fault Buck2 overvoltage fault latched bit. Write 1' to clear the fault Buck1 overvoltage fault latched bit. Write 1' to clear the fault Status 4 Buck1 high current warning latched bit. Write '1' to clear the fault	1: undervoltage fault occurs 0: OK (normal) 1: Overvoltage fault occurs 0: OK (normal) 1: Overvoltage fault occurs 0: OK (normal) 1: Overvoltage fault occurs 0: OK (normal) 1: Overvoltage fault occurs 0: OK (normal) 1: Overvoltage fault occurs 0: OK (normal) 1: Overvoltage fault occurs 0: OK (normal) 1: Overvoltage fault occurs	

'	er Name - Fault Latched (RW, Non EEPROM)	Status 6		0x00
[7]	PgoodCCBAT Latched	VBAT Pgood latched bit. Write '1' to clear the fault. This bit is edge sensitive.	0: OK (normal) 1: Battery voltage is below its power- good threshold	<0
[6]	VREFIN UVLO Latched	VREFIN UVLO fault latched bit. Write '1' to clear the fault.	0: OK (normal) 1: VREFIN UVLO occurs	<0
[5]	AVDD UVPD Latched	AVDD undervoltage power down fault atched bit. Write '1' to clear the fault.	0: OK (normal) 1: AVDD UVPD occurs	<0
[4]	NVM Error Latched	This bit gets set when any of the following conditions occurs: 1) There are ECC errors (both corrected and uncorrected). 2) The EEPROM voltage is not sufficient. 3) The EEPROM data is not valid. Write '1' to clear this bit which clears the detail bit(s) in 0x83/4/5.	0: OK (normal) 1: ECC error detected, insufficient EEPROM voltage or invalid EEPROM data	<0
[3]	CRST Triggered Latched	CRST Triggered latched bit. Write '1' to clear the fault	0: OK (normal) 1: CRST_IN# is asserted	<()
[2]	WDT Error Latched	WDT Error latched bit. Write '1' to clear the fault	0: OK (normal) 1: WDT Error occurs	<0
[1]	OTP Latched	Over temperature fault latched bit. Write 1' to clear the fault	0: OK (normal) 1: Over temperature fault occurs	<0
[0]	OTP WARN Latched	Over temperature warning latched bit. Write '1' to clear the fault	0: OK (normal) 1: Over temperature warning occurs	<()
	er Name - Fault Live Sta (Read-Only)	tus 1	ITIAL	0x00
[7:6]	not used			
	not useu			<0
[5]	Buck6 UV Live	Buck6 undervoltage fault live bit. This bit is automatically cleared when the fault condition subsides.		
[5] [4]		automatically cleared when the fault con-	Undervoltage fault occurs OK (normal)	<0 <0 <0
	Buck6 UV Live	automatically cleared when the fault condition subsides. Buck5 undervoltage fault live bit. This bit is automatically cleared when the fault con-	1: Undervoltage fault occurs 0: OK (normal) 1: Undervoltage fault occurs 0: OK (normal)	<(
[4]	Buck6 UV Live Buck5 UV Live	automatically cleared when the fault condition subsides. Buck5 undervoltage fault live bit. This bit is automatically cleared when the fault condition subsides. Buck4 undervoltage fault live bit. This bit is automatically cleared when the fault conditions.	1: Undervoltage fault occurs 0: OK (normal) 1: Undervoltage fault occurs 0: OK (normal) 1: Undervoltage fault occurs 0: OK (normal)	<(
[4]	Buck6 UV Live Buck5 UV Live Buck4 UV Live	automatically cleared when the fault condition subsides. Buck5 undervoltage fault live bit. This bit is automatically cleared when the fault condition subsides. Buck4 undervoltage fault live bit. This bit is automatically cleared when the fault condition subsides. Buck3 undervoltage fault live bit. This bit is automatically cleared when the fault conditions undervoltage fault live bit. This bit is automatically cleared when the fault conditions undervoltage fault live bit.	1: Undervoltage fault occurs 0: OK (normal) 1: Undervoltage fault occurs 0: OK (normal) 1: Undervoltage fault occurs 0: OK (normal) 1: Undervoltage fault occurs	<()

_	er Name - Fault Live Sta (Read-Only)	atus 2	0x00
[7:3]	not used		<0000
[2]	LDO3 PGood Live	LDO3 Pgood live bit. This bit is monitored 0: PGood HIGH when the LDO is enabled and disabled.	<0>
[1]	LDO2 PGood Live	LDO2 Pgood live bit. This bit is monitored 0: PGood HIGH when the LDO is enabled and disabled. 1: PGood LOW	<0>
[0]	LDO1 PGood Live	LDO1 Pgood live bit. This bit is monitored 0: PGood HIGH when the LDO is enabled and disabled. 1: PGood LOW	<0>
_	er Name - Fault Live Sta (Read-Only)	atus 3	0x00
[7:6]	not used		<00:
[5]	Buck6 OV Live	Buck6 overvoltage fault live bit. This bit is automatically cleared when the fault condition subsides.	<0>
[4]	Buck5 OV Live	Buck5 overvoltage fault live bit. This bit is automatically cleared when the fault condition subsides. 0: OK (normal) 1: Overvoltage fault occurs	<0>
[3]	Buck4 OV Live	Buck4 overvoltage fault live bit. This bit is automatically cleared when the fault condition subsides. 0: OK (normal) 1: Overvoltage fault occurs	<0>
[2]	Buck3 OV Live	Buck3 overvoltage fault live bit. This bit is automatically cleared when the fault condition subsides. 0: OK (normal) 1: Overvoltage fault occurs	<0>
[1]	Buck2 OV Live	Buck2 overvoltage fault live bit. This bit is automatically cleared when the fault condition subsides. 0: OK (normal) 1: Overvoltage fault occurs	<0>
[0]	Buck1 OV Live	Buck1 overvoltage fault live bit. This bit is automatically cleared when the fault condition subsides. 0: OK (normal) 1: Overvoltage fault occurs	<0>
	er Name - Fault Live Sta (Read-Only)	atus 4	0x00 /
[7:1]	not used		<00000
[0]	Buck1 HC Live	Buck1 high current warning live bit. This bit is automatically cleared when the fault condition subsides.	<0>

i ype -	er Name - Fault Live Sta (Read-Only)			0x0
[7]	PgoodCCBAT Live	VBAT Pgood live bit. This bit is automatically cleared when the fault condition subsides.		<
[6]	VREFIN UVLO Live	VREFIN UVLO fault live bit. This bit is automatically cleared when the fault con- dition subsides.	0: OK (normal) 1: VREFIN UVLO occurs	<
[5]	AVDD UVPD Live	AVDD undervoltage power down live bit. This bit is automatically cleared when the fault condition subsides.	0: OK (normal) 1: AVDD UVPD occurs	<
[4]	not used			<
[3]	CRST Triggered Live	CRST Triggered live bit. This bit is automatically cleared when the fault condition subsides.	0: OK (normal) 1: The FSM is currently transitioning to either IORESET or FAULT_OUT	<
[2]	WDT Error Live	WDT Error live bit. This bit is automatically cleared when the fault condition subsides.		<
[1]	OTP Live		0: OK (normal) 1: Over temperature fault occurs	<
		0	0: OK (normal)	<
[0]	OTP WARN Live	Over temperature warning live bit. This bit is automatically cleared when the fault condition subsides.	Over temperature warning occurs	
Registe	OTP WARN Live er Name - nINT Mask 1 (RW, EEPROM)	is automatically cleared when the fault		
Registe	er Name - nINT Mask 1	is automatically cleared when the fault		0x(
Registe Type -	er Name - nINT Mask 1 (RW, EEPROM)	is automatically cleared when the fault	1: Over temperature warning occurs	0x0
Registo Type -	er Name - nINT Mask 1 (RW, EEPROM) not used Buck6 UV nINT	is automatically cleared when the fault condition subsides. Configure INT# pin response to Buck6 UV	D: Unmask undervoltage fault from INT# pin Mask undervoltage fault from INT# pin	0x0
Registe Type - [7:6]	er Name - nINT Mask 1 (RW, EEPROM) not used Buck6 UV nINT Mask Buck5 UV nINT	condition subsides. Configure INT# pin response to Buck6 UV fault Configure INT# pin response to Buck5 UV	1: Over temperature warning occurs O: Unmask undervoltage fault from INT# pin 1: Mask undervoltage fault from INT# pin O: Unmask undervoltage fault from INT# pin 1: Mask undervoltage fault from INT# pin 1: Mask undervoltage fault from INT# pin	0x(
Registe Type - [7:6] [5]	er Name - nINT Mask 1 (RW, EEPROM) not used Buck6 UV nINT Mask Buck5 UV nINT Mask	Configure INT# pin response to Buck6 UV fault Configure INT# pin response to Buck5 UV fault Configure INT# pin response to Buck5 UV fault	D: Unmask undervoltage fault from INT# pin D: Mask undervoltage fault from INT# pin	0x0
Registo Type - [7:6] [5]	er Name - nINT Mask 1 (RW, EEPROM) not used Buck6 UV nINT Mask Buck5 UV nINT Mask Buck4 UV nINT Mask	Configure INT# pin response to Buck6 UV fault Configure INT# pin response to Buck5 UV fault Configure INT# pin response to Buck4 UV fault Configure INT# pin response to Buck4 UV fault Configure INT# pin response to Buck4 UV fault	1: Over temperature warning occurs O: Unmask undervoltage fault from INT# pin 1: Mask undervoltage fault from INT# pin 0: Unmask undervoltage fault from INT# pin 1: Mask undervoltage fault from INT# pin 0: Unmask undervoltage fault from INT# pin 1: Mask undervoltage fault from INT# pin 0: Unmask undervoltage fault from INT# pin 1: Mask undervoltage fault from INT# pin 1: Mask undervoltage fault from INT# pin 1: Mask undervoltage fault from INT# pin	0xt

	er Name - nINT Mask 2 (RW, EEPROM)			0x00
[7:4]	not used			<000
		Configuration and the last of	for the manufacture of the state of the stat	
[3]	VIO Pgood nINT mask	Configure INT# pin response to the loss of VIO Pgood	D: Onmask VIO Pgood fault from INT# pin 1: Mask VIO Pgood fault from INT# pin	<0
[2]	LDO3 UV nINT Ma	skConfigure INT# pin response to LDO3 UV fault	0: Unmask undervoltage fault from INT# pin 1: Mask undervoltage fault from INT# pin	<0
[1]	LDO2 UV nINT Ma	skConfigure INT# pin response to LDO2 UV fault	0: Unmask undervoltage fault from INT# pin 1: Mask undervoltage fault from INT# pin	<0
[0]	LDO1 UV nINT Ma	skConfigure INT# pin response to LDO1 UV fault	Unmask undervoltage fault from INT# pin Mask undervoltage fault from INT# pin	<0
66 Registe	er Name - nINT Mask 3		1	0x00
	(RW, EEPROM)			
[7:6]	not used			<00
[5]	Buck6 OV nINT Mask	Configure INT# pin response to Buck6 OV fault	0: Unmask over-voltage fault from INT# pin 1: Mask over-voltage fault from INT# pin	<0
[4]	Buck5 OV nINT Mask	Configure INT# pin response to Buck5 OV fault	0: Unmask over-voltage fault from INT# pin 1: Mask over-voltage fault from INT# pin	<0
			ſ	
[3]	Buck4 OV nINT Mask	Configure INT# pin response to Buck4 OV fault	0: Unmask over-voltage fault from INT# pin 1: Mask over-voltage fault from INT# pin	<0
[2]			INT# pin 1: Mask over-voltage fault from INT# pin	-
	Mask Buck3 OV nINT	fault Configure INT# pin response to Buck3 OV	INT# pin 1: Mask over-voltage fault from INT# pin 0: Unmask over-voltage fault from INT# pin 1: Mask over-voltage fault from INT# pin	<0
[2]	Mask Buck3 OV nINT Mask Buck2 OV nINT	Configure INT# pin response to Buck3 OV fault Configure INT# pin response to Buck2 OV	INT# pin 1: Mask over-voltage fault from INT# pin 0: Unmask over-voltage fault from INT# pin 1: Mask over-voltage fault from INT# pin 0: Unmask over-voltage fault from INT# pin INT# pin 1: Mask over-voltage fault from INT# pin	<0
[2] [1] [0]	Buck3 OV nINT Mask Buck2 OV nINT Mask Buck1 OV nINT	Configure INT# pin response to Buck3 OV fault Configure INT# pin response to Buck2 OV fault Configure INT# pin response to Buck1 OV fault	INT# pin 1: Mask over-voltage fault from INT# pin O: Unmask over-voltage fault from INT# pin 1: Mask over-voltage fault from INT# pin O: Unmask over-voltage fault from INT# pin 1: Mask over-voltage fault from INT# pin 1: Mask over-voltage fault from INT# pin O: Unmask over-voltage fault from INT# pin INT# pin INT# pin I: Mask over-voltage fault from INT# pin	<0
[2] [1] [0]	Mask Buck3 OV nINT Mask Buck2 OV nINT Mask Buck1 OV nINT Mask	Configure INT# pin response to Buck3 OV fault Configure INT# pin response to Buck2 OV fault Configure INT# pin response to Buck1 OV fault	INT# pin 1: Mask over-voltage fault from INT# pin O: Unmask over-voltage fault from INT# pin 1: Mask over-voltage fault from INT# pin O: Unmask over-voltage fault from INT# pin 1: Mask over-voltage fault from INT# pin 1: Mask over-voltage fault from INT# pin O: Unmask over-voltage fault from INT# pin INT# pin INT# pin I: Mask over-voltage fault from INT# pin	<0

	er Name - nINT Mask 6 (RW, EEPROM)			0x0
[7]	PgoodCCBAT nINT Mask	Configure INT# response to the loss of VBAT Pgood	0: Unmask PgoodCCBAT fault from NT# pin 1: Mask PgoodCCBAT fault from NT# pin	<
[6]	VREFIN UVLO nINT Mask	Configure INT# response to VREFIN UVLO fault	0: Unmask VREFIN UVLO fault from INT# pin 1: Mask VREFIN UVLO fault from INT# pin	<
[5]	AVDD UVPD nINT Mask	Configure INT# response to AVDD UVPD fault	0: Unmask AVDD UVPD fault from INT# pin 1: Mask AVDD UVPD fault from INT# pin	<
[4]	NVM Error nINT Mask	Configure INT# response to NVM Error	0: Unmask NVM Error from INT# pin 1: Mask NVM Error from INT# pin	<
[3]	CRST Triggered nINT Mask	Configure INT# response to CRST Trig- gered event	0: Unmask CRST Triggered fault from INT# pin 1: Mask CRST Triggered fault from INT# pin	<
[2]	WDT Error nINT Mask	Configure INT# response to WDT Error event	0: Unmask WDT Error from INT# pin 1: Mask WDT Error from INT# pin	<
[1]	OTP nINT Mask	Configure INT# response to OTP fault	0: Unmask Over Temp fault from INT# pin 1: Mask Over Temp fault from INT# pin	<
[0]	OTP WARN nINT Mask	Configure INT# response to OTP warning event	0: Unmask Over Temp Warning from NT# pin 1: Mask Over Temp Warning from NT# pin	<
_	er Name - Fault Config 1 (RW, EEPROM)			0x3
[7:6]	not used			<
[7:6] [5]	not used Buck6 UV Disable	UV fault	0: UV fault does not shut down any rail 1: UV fault shuts down all the rails	<
		UV fault	rail	
[5]	Buck6 UV Disable	UV fault Configure the device response to Buck5 UV fault	rail 1: UV fault shuts down all the rails 0: UV fault does not shut down any rail	•
[5]	Buck6 UV Disable Buck5 UV Disable	UV fault Configure the device response to Buck5 UV fault Configure the device response to Buck4 UV fault	rail 1: UV fault shuts down all the rails 0: UV fault does not shut down any rail 1: UV fault shuts down all the rails 0: UV fault does not shut down any rail	<
[5] [4] [3]	Buck6 UV Disable Buck5 UV Disable Buck4 UV Disable	UV fault Configure the device response to Buck5 UV fault Configure the device response to Buck4 UV fault Configure the device response to Buck3 UV fault	rail 1: UV fault shuts down all the rails 0: UV fault does not shut down any rail 1: UV fault shuts down all the rails 0: UV fault does not shut down any rail 1: UV fault shuts down all the rails 0: UV fault shuts down all the rails 0: UV fault does not shut down any rail	<

	er Name - Fault Config 2 (RW, EEPROM)	2		0x07 /
[7:3]	not used			<00000
[2]	LDO3 UV Disable	Configure the device response to LDO3 UV fault	UV fault does not shut down any rail UV fault shuts down all the rails	<1>
[1]	LDO2 UV Disable	Configure the device response to LDO2 UV fault	UV fault does not shut down any rail UV fault shuts down all the rails	<1>
[0]	LDO1 UV Disable	Configure the device response to LDO1 UV fault	0: UV fault does not shut down any rail 1: UV fault shuts down all the rails	<1>
	er Name - Fault Config 3 (RW, EEPROM)	3	•	0x7F / 1
[7]	not used			<0>
[6]	VREFIN UVLO Dis- able	Configure the device response to VREFINUVLO fault	NO: VREFIN UVLO fault does not shut down any rail 1: VREFIN UVLO fault shuts down all the rails	<1>
[5]	Buck6 OV Disable	Configure the device response to Buck6 OV fault	0: OV fault does not shut down any rail 1: OV fault shuts down all the rails	<1>
[4]	Buck5 OV Disable	Configure the device response to Buck5 OV fault	O: OV fault does not shut down any rail T: OV fault shuts down all the rails	<1>
[3]	Buck4 OV Disable	Configure the device response to Buck4 OV fault	O: OV fault does not shut down any rail COV fault shuts down all the rails O: OV fault shuts down all the rails	<1>
[2]	Buck3 OV Disable	Configure the device response to Buck3 OV fault	O: OV fault does not shut down any rail OV fault shuts down all the rails	<1>
[1]	Buck2 OV Disable	Configure the device response to Buck2 OV fault	O: OV fault does not shut down any rail OV fault shuts down all the rails	<1>
[0]	Buck1 OV Disable	Configure the device response to Buck1 OV fault	O: OV fault does not shut down any rail OV fault shuts down all the rails	<1>

_	eter Name - Block EN - (RW, EEPROM)			0x00 /
[7]	SLEEP State EN	Configure the device to enter {SLEEP}. This bit is not EEPROM backed	0: Exit SLEEP state 1: Enter SLEEP state	<0>
[6]	RTC EN	Enable the RTC. This bit is battery backed	0: Disabled 1: Enabled	<0>
[5]	CC Charger EN	Enable the coin cell battery charger. This bit is not EEPROM backed	0: Disabled 1: Enabled	<0>
[4]	CCBAT COMP EN	Enable the VBAT comparator	0: Disabled 1: Enabled	<0>
[3]	WD EN	Enable the watchdog timer	0: Disabled 1: Enabled	<0>
[2]	WD PD EN	Enable the power-down feature when the watchdog timer expires	0: Disabled 1: Enabled	<0>
[1]	WD RST EN		0: Disabled 1: Enabled	<0>
[0]	CRST Fault EN	Enable the power-down feature when the CRST_IN# is asserted		<0>
_	ter Name - Software Rese - (RW, Non EEPROM)	<u> </u>	1	0x00 /
[7:2]	not used			<00000
[1]	Warm Reset	Configure the device to do a warm reset	0: Normal 1: Warm reset	<0>
[0]	Cold Reset	Configure the device to do a cold reset	0: Normal 1: Cold reset	<0>
x6E Regis	Cold Reset ster Name - I2C Trigger Po - (RW, Non EEPROM)		0: Normal	<0>
x6E Regis	ster Name - I2C Trigger Po		0: Normal	0xA8 / ²
x6E Regis Type [7:0]	ster Name - I2C Trigger Po - (RW, Non EEPROM) I2C Trigger Power	Read-only. But when a data is written to this register, it will not ignore it. When the write data matches the read value, power off	0: Normal	0xA8 / ′
x6E Regis Type [7:0]	ster Name - I2C Trigger Po - (RW, Non EEPROM) I2C Trigger Power Off key	Read-only. But when a data is written to this register, it will not ignore it. When the write data matches the read value, power off sequence starts. Set the charge current level of the coin cell	0: Normal 1: Cold reset	0xA8 / ′
x6E Regis Type [7:0]	ster Name - I2C Trigger Po - (RW, Non EEPROM) I2C Trigger Power Off key ster Name - Config 1 - (RW, EEPROM)	Read-only. But when a data is written to this register, it will not ignore it. When the write data matches the read value, power off sequence starts. Set the charge current level of the coin cell battery charger when it is enabled	0: Normal 1: Cold reset	0xA8 / 2 <101010 0xFB / 2
x6E Regis Type [7:0]	ster Name - I2C Trigger Po - (RW, Non EEPROM) I2C Trigger Power Off key ster Name - Config 1 - (RW, EEPROM) Charge Current Level Thermal Warning Threshold	Read-only. But when a data is written to this register, it will not ignore it. When the write data matches the read value, power off sequence starts. Set the charge current level of the coin cell battery charger when it is enabled Set the thermal warning temperature ris-	0: Normal 1: Cold reset 0: 20μΑ 1: 60μΑ 00: 105C 01: 110C 10: 115C 11: 120C	0xA8 / 1
x6E Regis Type [7:0] x6F Regis Type [7]	ster Name - I2C Trigger Por - (RW, Non EEPROM) I2C Trigger Power Off key Ster Name - Config 1 - (RW, EEPROM) Charge Current Level Thermal Warning Threshold Buck1 High Current Threshold	Read-only. But when a data is written to this register, it will not ignore it. When the write data matches the read value, power off sequence starts. Set the charge current level of the coin cell battery charger when it is enabled Set the thermal warning temperature rising threshold Set the buck1 high current warning thresh-	0: 20μA 1: Cold reset 0: 20μA 1: 60μA 00: 105C 01: 110C 10: 115C 11: 120C 00: 4A 01: 5A 10: 5.5A 11: 6A	0xA8 / 2 <101010

	Name - Config 2 RW, EEPROM)			0xF8 /
[7:4]	VCCBAT	Set the coin cell battery termination voltage	4'b0000 - 4'b1111: 1.8V + 0.1V*VCCBAT[3:0]	<111
[3:2]	reserved			<10
[1:0]	PWRON Hold Perio	odSet the period in which the PWRON needs to stay high/low when it is configured as long push button	00: 1s 01: 1.5s 10: 2s 11: 3s	<00
	Name - Config 3 RW, EEPROM)	•		0x17
[7:5]	not used			<000
[4:3]	VIO Timeout	Set the timeout period in which VIO_P-good is monitored. If VIO_Pgood is asserted before the timer expires, then the FSM transitions to {STANDBY} before the end of the timeout period. If VIO_Pgood is not asserted when the timer expires, then the FSM transitions to {FAULT_OUT}.	11: 2ms	<10
	Cold Reset Delay Name - MPIO0 Power	power-off sequence to the start of power-on	0: No delay 1: 15ms 2: 31ms 3: 63ms 4: 95ms 5: 127ms 6: 191ms 7: 255ms	<11 0x46
[7]	hot used			<0:
[6:0]	MPIO0 Power On Delay	Delay timed from the beginning of power- on sequence. The alternative function of bits[3:0] is to select which regulator is used for the PGood when MPIO0 is con- figured as PGood output. Refer to the set- tings for details	0: 0ms 1: 1ms 	<1000
	Name - MPIO0 Powe RW, EEPROM)	er Off		0x00
				<0:
[7] [6:0]	not used MPIO0 Power Off	Delay timed from the beginning of power-	In	<0000

	(RW, EEPROM)		
[7]	lant was al		_
[7] [6:0]	not used MPIO1 Power On	Delay timed from the beginning of power- Bits[6:0] decodes:	<
	Delay	on sequence. The alternative function of bits[3:0] is to select which regulator is used for the PGood when MPIO1 is configured as PGood output. Refer to the settings for details Alternative decodes of bits[3:0]: 0000: Buck1 0001: Buck2 0010: Buck3 0011: Buck4 0100: Buck5 0101: Buck6 0110: LDO1 0111: LDO2 1000: LDO3 1001: VTTREF 1010: AND of all regulators PGood	
•	r Name - MPIO1 Powe RW, EEPROM) not used MPIO1 Power Off	Delay timed from the beginning of power- off sequence 0: 0ms	<1
	Delay		
	r Name - MPIO2 Powe (RW, EEPROM)	127: 127ms er On	

	er Name - MPIO2 Powe (RW, EEPROM)	r Off		0x00 / 0
[7]	not used			<0>
[6:0 <u>]</u>	MPIO2 Power Off Delay	Delay timed from the beginning of power- off sequence. The alternative function of bits[2:0] is to set the frequency when MPIO2 is configured as 32K_CLK. Refer to the settings for details	Bits[6:0] decodes: 0: 0ms 1: 1ms 127: 127ms Alternative decodes of bits[2:0]: 000: 32.768kHz 001: 16.384kHz 010: 8.192kHz 011: 4.096kHz 100: 2.048kHz 101: 1.024kHz 110: 512Hz 111: 256Hz	<000000
_	I er Name - MPIO3 Powe (RW, EEPROM)	er On	l	0x00 / (
[7]	not used			<0>
[6:0]	MPIO3 Power On Delay	bits[3:0] is to select which regulator is used for the PGood when MPIO3 is configured as PGood output. Refer to the settings for details	0: 0ms 1: 1ms 	<000000
	er Name - MPIO3 Powe (RW, EEPROM)	or Off		
			0: 0ms	0x00 / 0 <0>

i ype -	er Name - MPIO4 Powe (RW, EEPROM)	er Un	0x0
[7]	not used		<
[6:0]	MPIO4 Power On Delay	Delay timed from the beginning of power- on sequence. The alternative function of bits[3:0] is to select which regulator is used for the PGood when MPIO4 is con- figured as PGood output. Refer to the set- tings for details 1: 1ms 127: 127ms Alternative decodes of bits[3:0]: 0000: Buck1 0001: Buck2 0010: Buck3 0011: Buck4 0100: Buck5 0101: Buck6 0110: LDO1 0111: LDO2 1000: LDO3 1001: VTTREF 1010: AND of all regulators PGood	<000
	Pr Name - MPIO4 Powe (RW, EEPROM)	er Off	0x
[7]	not used		
[6:0]	MPIO4 Power Off Delay	Delay timed from the beginning of power- off sequence. The alternative function of bits[3:0] is used to set the timeout period when MPIO4 is configured as Watchdog	<000

	er Name - MPIO5 Powe (RW, EEPROM)	er On		0x00
[7]	not used			<0>
[6:0]	MPIO5 Power On Delay	Delay timed from the beginning of powe on sequence. The alternative function of bits[3:0] is used to select which regulato is used for the PGood when MPIO5 is configured as PGood output. Refer to the settings for details	: 0: 0ms r 1: 1ms n	<00000
Type -	Pr Name - MPIO5 Powe (RW, EEPROM)	er Off		
Type - ((RW, EEPROM)			<0
Type -	(RW, EEPROM)	Delay timed from the beginning of powe off sequence	1: 1ms 	<0:
Type - (7) [6:0]	(RW, EEPROM) not used MPIO5 Power Off	Delay timed from the beginning of powe off sequence		<00000
Type - (7) [6:0]	hot used MPIO5 Power Off Delay Pr Name - MPIO Input S	Delay timed from the beginning of powe off sequence	1: 1ms 	<00000 <00000
Type - (7) [6:0] Registe Type - (hot used MPIO5 Power Off Delay er Name - MPIO Input S (Read-Only)	Delay timed from the beginning of powe off sequence	1: 1ms 	<000000 <000000 0x000
7ype - (7) [6:0] Register Type - (7:6)	hot used MPIO5 Power Off Delay Pr Name - MPIO Input S (Read-Only)	Delay timed from the beginning of powe off sequence	1: 1ms 127: 127ms D: Low	0x000 <000000 0x000 <000 <000
7ype - (7) [6:0] Register Type - (7:6) [5]	not used MPIO5 Power Off Delay Pr Name - MPIO Input S (Read-Only) not used MPIO5 Status	Delay timed from the beginning of powe off sequence Status Read back the live status of MPIO5	1: 1ms 127: 127ms 0: Low 1: High 0: Low	<000000 <000000 <000 <000
[7] [6:0] Registe Type - [7:6] [5]	not used MPIO5 Power Off Delay Per Name - MPIO Input S (Read-Only) not used MPIO5 Status MPIO4 Status	Delay timed from the beginning of powe off sequence Status Read back the live status of MPIO5 Read back the live status of MPIO4	1: 1ms 127: 127ms 0: Low 1: High 0: Low 1: High 0: Low	<000000 <000000 <000 <000 <000 <000
[7] [6:0] Registe Type - [7:6] [5] [4]	not used MPIO5 Power Off Delay Per Name - MPIO Input S (Read-Only) not used MPIO5 Status MPIO4 Status MPIO3 Status	Delay timed from the beginning of powe off sequence Status Read back the live status of MPIO5 Read back the live status of MPIO4 Read back the live status of MPIO3	1: 1ms 127: 127ms 0: Low 1: High 0: Low 1: High 0: Low 1: High 0: Low 1: High	<000000 <000000 <000 <000

[7:6]	not used			<00>
[5]	MPIO5 I2C Output	Set the status of MPIO5 when its function		<0>
		is set to "Output from I2C output"	1: Set high	
[4]	MPIO4 I2C Output	Set the status of MPIO4 when its function	0: Set low	<0>
		is set to "Output from I2C output"	1: Set high	
[3]	MPIO3 I2C Output	Set the status of MPIO3 when its function	0: Set low	<0>
		is set to "Output from I2C output"	1: Set high	
[2]	MPIO2 I2C Output	Set the status of MPIO2 when its function	0: Set low	<0>
		is set to "Output from I2C output"	1: Set high	
[1]	MPIO1 I2C Output	Set the status of MPIO1 when its function	0: Set low	<0>
		is set to "Output from I2C output"	1: Set high	
[0]	MPIO0 I2C Output	Set the status of MPIO0 when its function	0: Set low	<0>
	·	is set to "Output from I2C output"	1: Set high	

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	r Name - MPIO Assertic RW, EEPROM)	ווע		0x3
[7:6]	not used			•
[5]	MPIO5 Assertion	Configure the MPIO5 operation during transition between {ACTIVE} and {SLEEP} when it is set to reset output or Enternal VR EN output	0: A reset output will NOT be asserted (or an external VR enable will NOT be de-asserted) in SLEEP state 1: A reset output will be asserted (or an external VR enable be de- asserted) in SLEEP state	
[4]	MPIO4 Assertion	Configure the MPIO4 operation during transition between {ACTIVE} and {SLEEP} when it is set to reset output or Enternal VR EN output	0: A reset output will NOT be asserted (or an external VR enable will NOT be de-asserted) in SLEEP state 1: A reset output will be asserted (or an external VR enable be de- asserted) in SLEEP state	
[3]	MPIO3 Assertion	Configure the MPIO3 operation during transition between {ACTIVE} and {SLEEP} when it is set to reset output or Enternal VR EN output	0: A reset output will NOT be asserted (or an external VR enable will NOT be de-asserted) in SLEEP state 1: A reset output will be asserted (or an external VR enable be de- asserted) in SLEEP state	
[2]	MPIO2 Assertion	Configure the MPIO2 operation during transition between {ACTIVE} and {SLEEP} when it is set to reset output or Enternal VR EN output	0: A reset output will NOT be asserted (or an external VR enable will NOT be de-asserted) in SLEEP state 1: A reset output will be asserted (or an external VR enable be de- asserted) in SLEEP state	
[1]	MPIO1 Assertion	Configure the MPIO1 operation during transition between {ACTIVE} and {SLEEP} when it is set to reset output or Enternal VR EN output	0: A reset output will NOT be asserted (or an external VR enable will NOT be de-asserted) in SLEEP state 1: A reset output will be asserted (or an external VR enable be de- asserted) in SLEEP state	
[0]	MPIO0 Assertion	Configure the MPIO0 operation during transition between {ACTIVE} and {SLEEP} when it is set to reset output or Enternal VR EN output	0: A reset output will NOT be asserted (or an external VR enable will NOT be de-asserted) in SLEEP state 1: A reset output will be asserted (or an external VR enable be deasserted) in SLEEP state	
	r Name - Input Pin Stat Read-Only)	us		0×
[7:5]	not used			<
[4]	VPROG Status	Read back the live status of VPROG	0: Low 1: High	
[3]	LDO2VSEL Status	Read back the live status of LDO2VSEL	0: Low 1: High	
[2]	LDO1VSEL Status	Read back the live status of LDO1VSEL	0: Low 1: High	
[1]	PWRON Status	Read back the live status of PWRON	0: Low 1: High	
[0]	CEN Status	Read back the live status of CEN	0: Low	

_	ter Name - Report Buck N - (Read-Only)	Лоde		0x00 / 0
[7:6]	not used			<00>
[5]	Buck6 Mode	Read back the operation status of buck6	0: PFM 1: PWM	<0>
[4]	Buck5 Mode	Read back the operation status of buck5	0: PFM 1: PWM	<0>
[3]	Buck4 Mode	Read back the operation status of buck4	0: PFM 1: PWM	<0>
[2]	Buck3 Mode	Read back the operation status of buck3	0: PFM 1: PWM	<0>
[1]	Buck2 Mode	Read back the operation status of buck2	0: PFM 1: PWM	<0>
[0]	Buck1 Mode	Read back the operation status of buck1	0: PFM 1: PWM	<0>
_	L ter Name - ECC Detail 1 · (RW, Non EEPROM)			0x00 / 0
_	- (RW, Non EEPROM)	Cleared by writing '1' to 0x5E[4] NVM Error bit	0: Bank7 ECC OK (normal) 1: Bank7 ECC corrected flag	0x00 / 0 <0>
Type -	EE Bank7 ECC Corrected		` ,	
Type -	EE Bank7 ECC Corrected EE Bank6 ECC Corrected	Error bit Cleared by writing '1' to 0x5E[4] NVM	1: Bank7 ECC corrected flag 0: Bank6 ECC OK (normal)	<0>
Type - [7]	EE Bank7 ECC Corrected EE Bank6 ECC Corrected EE Bank5 ECC Corrected	Error bit Cleared by writing '1' to 0x5E[4] NVM Error bit Cleared by writing '1' to 0x5E[4] NVM	1: Bank7 ECC corrected flag 0: Bank6 ECC OK (normal) 1: Bank6 ECC corrected flag 0: Bank5 ECC OK (normal)	<0>
Type - [7] [6]	EE Bank7 ECC Corrected EE Bank6 ECC Corrected EE Bank5 ECC Corrected EE Bank4 ECC Corrected	Error bit Cleared by writing '1' to 0x5E[4] NVM Error bit Cleared by writing '1' to 0x5E[4] NVM Error bit Cleared by writing '1' to 0x5E[4] NVM	1: Bank7 ECC corrected flag 0: Bank6 ECC OK (normal) 1: Bank6 ECC corrected flag 0: Bank5 ECC OK (normal) 1: Bank5 ECC corrected flag 0: Bank4 ECC OK (normal)	<0> <0>
[7] [6] [5]	EE Bank7 ECC Corrected EE Bank6 ECC Corrected EE Bank5 ECC Corrected EE Bank4 ECC Corrected EE Bank4 ECC Corrected EE Bank3 ECC Corrected	Error bit Cleared by writing '1' to 0x5E[4] NVM Error bit Cleared by writing '1' to 0x5E[4] NVM Error bit Cleared by writing '1' to 0x5E[4] NVM Error bit Cleared by writing '1' to 0x5E[4] NVM Cleared by writing '1' to 0x5E[4] NVM	1: Bank7 ECC corrected flag 0: Bank6 ECC OK (normal) 1: Bank6 ECC corrected flag 0: Bank5 ECC OK (normal) 1: Bank5 ECC corrected flag 0: Bank4 ECC OK (normal) 1: Bank4 ECC Corrected flag 0: Bank3 ECC OK (normal)	<0> <0> <0>
[7] [6] [5] [4]	EE Bank7 ECC Corrected EE Bank6 ECC Corrected EE Bank5 ECC Corrected EE Bank4 ECC Corrected EE Bank4 ECC Corrected EE Bank3 ECC Corrected EE Bank2 ECC Corrected	Error bit Cleared by writing '1' to 0x5E[4] NVM Error bit Cleared by writing '1' to 0x5E[4] NVM Error bit Cleared by writing '1' to 0x5E[4] NVM Error bit Cleared by writing '1' to 0x5E[4] NVM Error bit Cleared by writing '1' to 0x5E[4] NVM Cleared by writing '1' to 0x5E[4] NVM	1: Bank7 ECC corrected flag 0: Bank6 ECC OK (normal) 1: Bank6 ECC OK (normal) 1: Bank5 ECC OK (normal) 1: Bank5 ECC corrected flag 0: Bank4 ECC OK (normal) 1: Bank4 ECC corrected flag 0: Bank3 ECC OK (normal) 1: Bank3 ECC OK (normal) 0: Bank2 ECC OK (normal)	<0> <0> <0> <0> <0> <0> <0>

	r Name - ECC Detail 2 (RW, Non EEPROM)			0x00 / (
[7]	EE Bank7 ECC Erro	Cleared by writing '1' to 0x5E[4] NVM Error bit	0: Bank7 ECC OK (normal) 1: Bank7 ECC uncorrectable error flag	<0>
[6]	EE Bank6 ECC Erro	Cleared by writing '1' to 0x5E[4] NVM Error bit	0: Bank6 ECC OK (normal) 1: Bank6 ECC uncorrectable error flag	<0>
[5]	EE Bank5 ECC Erro	Cleared by writing '1' to 0x5E[4] NVM Error bit	0: Bank5 ECC OK (normal) 1: Bank5 ECC uncorrectable error flag	<0>
[4]	EE Bank4 ECC Erro	Cleared by writing '1' to 0x5E[4] NVM Error bit	0: Bank4 ECC OK (normal) 1: Bank4 ECC uncorrectable error flag	<0>
[3]	EE Bank3 ECC Erro	Cleared by writing '1' to 0x5E[4] NVM Error bit	0: Bank3 ECC OK (normal) 1: Bank3 ECC uncorrectable error flag	<0>
[2]	EE Bank2 ECC Erro	Cleared by writing '1' to 0x5E[4] NVM Error bit	0: Bank2 ECC OK (normal) 1: Bank2 ECC uncorrectable error flag	<0>
[1]	EE Bank1 ECC Erro	Cleared by writing '1' to 0x5E[4] NVM Error bit	0: Bank1 ECC OK (normal) 1: Bank1 ECC uncorrectable error flag	<0>
[0]	EE Bank0 ECC Erro	Cleared by writing '1' to 0x5E[4] NVM Error bit	0: Bank0 ECC OK (normal) 1: Bank0 ECC uncorrectable error flag	<0>
	r Name - EE Detail (RW, Non EEPROM)	MEIDE	NITIAI	0x00 / (
[7:2]	not used		NHAL	<000000
[1]	Valid EE Data	Customer data is considered as valid if either of the EEPROM ID 1/2 registers a non-zero. Cleared by writing '1' to 0x5E NVM Error bit		<0>
[0]	EE Error Latched	Cleared by writing '1' to 0x5E[4] NVM Error bit	0: OK (normal) 1: Insufficient EEPROM voltage	<0>

_	er Name - Spread Spe (RW, EEPROM)	ctrum 1		0x00 / 0
[7:6]	Freq SS	Spread spectrum modulation frequency	00: 17.5kHz 01: 20kHz 10: 22.5kHz 11: 25kHz	<00>
[5:4]	PWM AM	Spread spectrum modulation amplitude in PWM mode. Setting these two bits to 2b'00 disables the spread spectrum function in PWM mode for all buck regulators	00: 0, 0, 0, 0, 0, 0, 0	<00>
[3:2]	Buck6 PFM AM	Buck6 spread spectrum modulation amplitude in PFM mode	-00: -1, -1, 0, 0, 0, 0, +1, +1 01: -2, -1, -1, 0, 0, +1, +1, +2 10: -3, -2, -1, 0, 0, +1, +2, +3 11: -4, -3, -1, 0, 0, +1, +3, +4	<00>
[1:0]	Buck5 PFM AM	Buck5 spread spectrum modulation ampli- tude in PFM mode	-00: -1, -1, 0, 0, 0, 0, +1, +1 01: -2, -1, -1, 0, 0, +1, +1, +2 10: -3, -2, -1, 0, 0, +1, +2, +3 11: -4, -3, -1, 0, 0, +1, +3, +4	<00>
_	I er Name - Spread Spe (RW, EEPROM)	ctrum 2		0x00 / 0
_		Buck4 spread spectrum modulation ampli- tude in PFM mode	-00: -1, -1, 0, 0, 0, 0, +1, +1 01: -2, -1, -1, 0, 0, +1, +1, +2 10: -3, -2, -1, 0, 0, +1, +2, +3 11: -4, -3, -1, 0, 0, +1, +3, +4	0x00 / 0
Type -	(RW, EEPROM)	Buck4 spread spectrum modulation ampli	01: -2, -1, -1, 0, 0, +1, +1, +2 10: -3, -2, -1, 0, 0, +1, +2, +3 11: -4, -3, -1, 0, 0, +1, +3, +4	0x00 / 0 <00>
Type -	(RW, EEPROM) Buck4 PFM AM	Buck4 spread spectrum modulation ampli- tude in PFM mode Buck3 spread spectrum modulation ampli-	01: -2, -1, -1, 0, 0, +1, +1, +2 10: -3, -2, -1, 0, 0, +1, +2, +3 11: -4, -3, -1, 0, 0, +1, +3, +4 -00: -1, -1, 0, 0, 0, 0, +1, +1 01: -2, -1, -1, 0, 0, +1, +1, +2 10: -3, -2, -1, 0, 0, +1, +2, +3 11: -4, -3, -1, 0, 0, +1, +3, +4	<00>
Type - [7:6]	Buck4 PFM AM Buck3 PFM AM	Buck4 spread spectrum modulation ampli- tude in PFM mode Buck3 spread spectrum modulation ampli- tude in PFM mode Buck2 spread spectrum modulation ampli-	01: -2, -1, -1, 0, 0, +1, +1, +2 10: -3, -2, -1, 0, 0, +1, +2, +3 11: -4, -3, -1, 0, 0, +1, +3, +4 -00: -1, -1, 0, 0, 0, 0, +1, +1 01: -2, -1, -1, 0, 0, +1, +1, +2 10: -3, -2, -1, 0, 0, +1, +2, +3 11: -4, -3, -1, 0, 0, +1, +3, +4 -00: -1, -1, 0, 0, 0, 0, +1, +1 01: -2, -1, -1, 0, 0, +1, +1, +2 10: -3, -2, -1, 0, 0, +1, +2, +3 11: -4, -3, -1, 0, 0, +1, +3, +4	<00>
Type - [7:6] [5:4] [1:0]	(RW, EEPROM) Buck4 PFM AM Buck3 PFM AM Buck2 PFM AM	Buck4 spread spectrum modulation amplitude in PFM mode Buck3 spread spectrum modulation amplitude in PFM mode Buck2 spread spectrum modulation amplitude in PFM mode Buck1 spread spectrum modulation amplitude in PFM mode	01: -2, -1, -1, 0, 0, +1, +1, +2 10: -3, -2, -1, 0, 0, +1, +2, +3 11: -4, -3, -1, 0, 0, +1, +3, +4 -00: -1, -1, 0, 0, 0, 0, +1, +1 01: -2, -1, -1, 0, 0, +1, +1, +2 10: -3, -2, -1, 0, 0, +1, +2, +3 11: -4, -3, -1, 0, 0, +1, +3, +4 -00: -1, -1, 0, 0, 0, 0, +1, +1 01: -2, -1, -1, 0, 0, +1, +2, +3 11: -4, -3, -1, 0, 0, +1, +2, +3 11: -4, -3, -1, 0, 0, +1, +2, +3 11: -4, -3, -1, 0, 0, +1, +3, +4 -00: -1, -1, 0, 0, 0, 0, +1, +1 01: -2, -1, -1, 0, 0, 0, +1, +1 01: -2, -1, -1, 0, 0, +1, +1, +2 10: -3, -2, -1, 0, 0, +1, +2, +3	<00> <00>
Type - [7:6] [5:4] [1:0]	Buck4 PFM AM Buck3 PFM AM Buck2 PFM AM Buck1 PFM AM	Buck4 spread spectrum modulation amplitude in PFM mode Buck3 spread spectrum modulation amplitude in PFM mode Buck2 spread spectrum modulation amplitude in PFM mode Buck1 spread spectrum modulation amplitude in PFM mode	01: -2, -1, -1, 0, 0, +1, +1, +2 10: -3, -2, -1, 0, 0, +1, +2, +3 11: -4, -3, -1, 0, 0, +1, +3, +4 -00: -1, -1, 0, 0, 0, 0, +1, +1 01: -2, -1, -1, 0, 0, +1, +1, +2 10: -3, -2, -1, 0, 0, +1, +2, +3 11: -4, -3, -1, 0, 0, +1, +3, +4 -00: -1, -1, 0, 0, 0, 0, +1, +1 01: -2, -1, -1, 0, 0, +1, +2, +3 11: -4, -3, -1, 0, 0, +1, +2, +3 11: -4, -3, -1, 0, 0, +1, +2, +3 11: -4, -3, -1, 0, 0, +1, +3, +4 -00: -1, -1, 0, 0, 0, 0, +1, +1 01: -2, -1, -1, 0, 0, 0, +1, +1 01: -2, -1, -1, 0, 0, +1, +1, +2 10: -3, -2, -1, 0, 0, +1, +2, +3	<00> <00>

_	ster Name - Shutdown Co e - (RW, EEPROM)	nfig		0x02 /
[7:3]	not used			<00000
[2]	Shutdown Option LDO	Config the shutdown options for all LDOs	Shut down with discharge resistors using Shut Down SR Shut down with discharge resistors, discharge rate set by RC	<0>
[1:0]	Shutdown Option Buck	Config the shutdown options for all buck regulators	00: Shut down in forced PWM using Shut Down SR 01: Shut down in PFM/PWM using Shut Down SR 10: Shut down with discharge resistors using Shut Down SR 11: Shut down with discharge resistors, discharge rate set by RC	<10>
	ster Name - MPIO0 Config - (RW, EEPROM)	<u> </u>	<u> </u>	0x0D /
[7:6]	not used			<00>
[5]	MPIO0 Invert	Configure the polarity of MPIO0	0: Active low 1: Active high	<0>
[4:3]	MPIO0 Type	If bits[4:3] = 00, then the respective MPIOx pin is high impedance, and the device will still use the MPIOx power on/off delays if bits[2:0] are not set to 3'b000		<01>
[2:0]	MPIO0 Function		000: Disabled 001: Disabled 010: External VR PGood input 011: Input to I2C register 100: PGood output 101: Reset output 110: External VR EN output 111: Output from I2C output	<101:
	ster Name - MPIO1 Config - (RW, EEPROM)	3		0x0D /
[7:6]	not used			<00>
[5]	MPIO1 Invert	Configure the polarity of MPIO1	0: Active low 1: Active high	<0>
[4:3]	MPIO1 Type	If bits[4:3] = 00, then the respective MPIOx pin is high impedance, and the device will still use the MPIOx power on/off delays if bits[2:0] are not set to 3'b000		<01>
[2:0]	MPIO1 Function	1 '	000: Disabled 001: Disabled 010: External VR PGood input 011: Input to I2C register 100: PGood output 101: Reset output 110: External VR EN output	<101>

ı ype - (ı	Register Name - MPIO2 Config Type - (RW, EEPROM)					
[7:6]	not used			<00		
[5]	MPIO2 Invert	Configure the polarity of MPIO2	0: Active low 1: Active high	<1:		
[4:3]	MPIO2 Type	If bits[4:3] = 00, then the respective MPIOx pin is high impedance, and the device will still use the MPIOx power on/off delays if bits[2:0] are not set to 3'b000		<01		
[2:0]	MPIO2 Function	· ·	000: Disabled 001: 32K_CLK 010: External VR PGood input 011: Input to I2C register 100: PGood output 101: Reset output 110: External VR EN output 111: Output from I2C output	<100		
	r Name - MPIO3 Conf RW, EEPROM)	ig		0x20		
[7:6]	not used			<00		
[5]	MPIO3 Invert	Configure the polarity of MPIO3	0: Active low 1: Active high	<1		
[4:3]	MPIO3 Type	If bits[4:3] = 00, then the respective MPIOx pin is high impedance, and the device will still use the MPIOx power on/off delays if bits[2:0] are not set to 3'b000		<00		
[2:0]	MPIO3 Function	- 1 /	000: Disabled 001: SLEEP# 010: External VR PGood input 011: Input to I2C register 100: PGood output 101: Reset output 110: External VR EN output 111: Output from I2C output	<00		
	I r Name - MPIO4 Conf RW, EEPROM)	ig	I .	0x00		
[7:6]	not used			<00		
[5]	MPIO4 Invert	Configure the polarity of MPIO4	0: Active low 1: Active high	<0:		
[4:3]	MPIO4 Type	if bits[4:3] = 00, then the respective MPIOx pin is high impedance, and the device will still use the MPIOx power on/off delays if bits[2:0] are not set to 3'b000		<00		
[2:0]	MPIO4 Function		000: Disabled 001: WDT_RST# 010: External VR PGood input 011: Input to I2C register	<000		

0x8F	Register Name - MPIO5 Config Type - (RW, EEPROM)						
	[7:6]	[7:6] hot used					
	[5]	MPIO5 Invert	Configure the polarity of MPIO5 0: Active low 1: Active high				
	[4:3]	MPIO5 Type	If bits[4:3] = 00, then the respective MPIOx pin is high impedance, and the device will still use the MPIOx power on/off delays if bits[2:0] are not set to 3'b000		<00>		
	[2:0]	MPIO5 Function		000: Disabled 001: CRST_IN# 010: External VR PGood input 011: Input to I2C register 100: PGood output 101: Reset output 110: External VR EN output 111: Output from I2C output	<001>		
0x90	Register Name - PWRON Polarity Config Type - (RW, EEPROM)						
	[7:1]	not used			<0000000		
	[0]	PWRON Polarity	Select the polarity of the PWRON input in both on/off switch and push button modes		<1>		
			, , , , , , , , , , , , , , , , , , , ,	I I I I I I I I I I I I I I I I I I I			
0x95		r Name - System Con RW, Non EEPROM)	·		0x00 / 0		
0x95	Type - (·	ITIAI			
0x95	Type - (RW, Non EEPROM)	·	HAL			
0x95	Type - (RW, Non EEPROM)	trol	0: Unlock the MPIOx Config registers at 0x8A - 0x8F 1: Lock the MPIOx Config registers at 0x8A - 0x8F	<000000		
0x95 0xAD	Type - ([7:2] [1] [0]	not used	To prevent user from accidentally changing the MPIOx configurations. Once this bit is set to '1', it cannot be set back to '0' until POR	0: Unlock the MPIOx Config registers at 0x8A - 0x8F 1: Lock the MPIOx Config registers	<000000		
	Type - ([7:2] [1] [0] Reserve	not used reserved MPIO Config Lock	To prevent user from accidentally changing the MPIOx configurations. Once this bit is set to '1', it cannot be set back to '0' until POR	0: Unlock the MPIOx Config registers at 0x8A - 0x8F 1: Lock the MPIOx Config registers	<000000 <0> <0>		
0xAD	Type - ([7:2] [1] [0] Reserve	not used reserved MPIO Config Lock ed for Renesas Internation	To prevent user from accidentally changing the MPIOx configurations. Once this bit is set to '1', it cannot be set back to '0' until POR	0: Unlock the MPIOx Config registers at 0x8A - 0x8F 1: Lock the MPIOx Config registers	<0000000 <0> <0>		
0xAD	Type - ([7:2] [1] [0] Reserve Register Type - ([7:0]	not used reserved MPIO Config Lock ed for Renesas Internations r Name - EEPROM ID RW, EEPROM)	To prevent user from accidentally changing the MPIOx configurations. Once this bit is set to '1', it cannot be set back to '0' until POR al Use The EEPROM data is considered valid when EEPROM ID 1 or EEPROM ID 2 is programmed to non-zero value	0: Unlock the MPIOx Config registers at 0x8A - 0x8F 1: Lock the MPIOx Config registers	<0000000		
0xAD 0xB0	Type - ([7:2] [1] [0] Reserve Register Type - ([7:0]	not used reserved MPIO Config Lock ed for Renesas Internation Renesas Internation Renewal Internation (International International Internation	To prevent user from accidentally changing the MPIOx configurations. Once this bit is set to '1', it cannot be set back to '0' until POR al Use The EEPROM data is considered valid when EEPROM ID 1 or EEPROM ID 2 is programmed to non-zero value	0: Unlock the MPIOx Config registers at 0x8A - 0x8F 1: Lock the MPIOx Config registers	<0000000 <0> <0> <0> 0x01 / 3		
0xAD 0xB0	Type - ([7:2] [1] [0] Reserve Register Type - ([7:0] Register Type - (not used reserved MPIO Config Lock ed for Renesas Internation of the second of the sec	To prevent user from accidentally changing the MPIOx configurations. Once this bit is set to '1', it cannot be set back to '0' until POR al Use 1 The EEPROM data is considered valid when EEPROM ID 1 or EEPROM ID 2 is programmed to non-zero value 2 The EEPROM data is considered valid when EEPROM ID 1 or EEPROM ID 2 is	0: Unlock the MPIOx Config registers at 0x8A - 0x8F 1: Lock the MPIOx Config registers	<0000000 <0> <0> <0>		

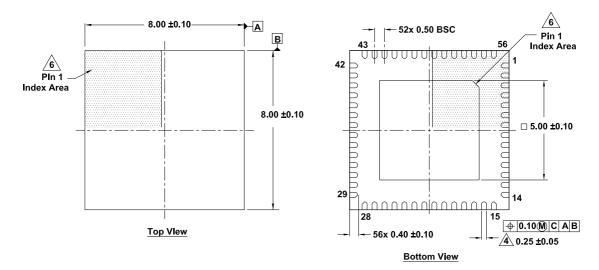
	er Name - HW REV (Read-Only)			0x12 / 1
[7:4]	Major Rev	4-bit Major Revision	0x0 = x 0x1 = Rev A 0x2 = Rev B 0x3 = Rev C	<0001>
[3:0]	Minor Rev	4-bit Minor Revision	0x0 = x 0x1 = 1st tape-out within a major revision 0x2 = 2nd tape-out within a major revision 0x3 = 3rd tape-out within a major revision	<0010>
	er Name - EEPRON (RW, Non EEPRO			0x00 /
[7:4]	not used			<0000>
[3]	reserved reserved			
[2]				
[2]	Write EEPROM tomer	1 Cus-Write all customer registers to EEPROM	Do Nothing Write reg data to EEPROM (customer banks), set bit LOW after write done	<0>

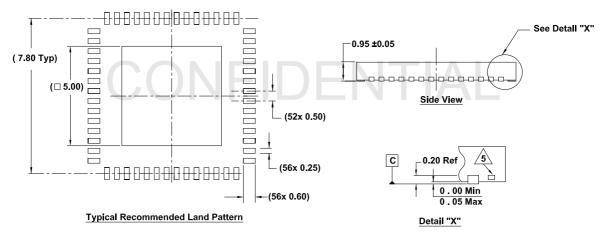
13. Package Outline Drawing

For the most recent package outline drawing, see L56.8x8l.

L56.8x8I

56 Lead Quad Flat No-lead Plastic Package (5x5mm Exposed Paddle) Rev 0, 11/20





Notes:

- Dimensions are in millimeters.
 Dimensions in () for reference only.
- 2. Dimensioning and tolerancing conform to ASME Y14.5m-1994.
- 3. Unless otherwise specified, tolerance: Decimal ±0.05
- <u>A.</u> Dimension applies to the metallized terminal and is measured between 0.15mm and 0.30mm from the terminal tip.
- 5. Tiebar shown (if present) is a non-functional feature.
- h The configuration of the pin #1 Identifier Is optional, but must be located within the zone indicated. The pin #1 Identifier Is either a mold or mark feature.

14. Part Number Differences

This document describes the base RAA215300A2GNP#HA0 device. The other part numbers have default, or other implementation *differences relative to this base part*. The detailed differences are outlined in the following sections.

14.1 RAA215300A2GNP#HA1

14.1.1 Register Map Detail

Summary of differences:

PWRON Configuration: On/Off Switch

Register Pointer	Register Bit(S)	Bit(s)/Function Name	Description	Setting/Range	Default
0x6F	Register Na Type - (RW,	me - Config 1 EEPROM)	_		0xFA / 250
	[0]	PWRON Config	Set the PWRON configuration	0: On/off switch 1: Long push button	<0>

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15. Ordering Information

Part Number ^{[1][2]}	Part Marking	Package Description (RoHS Compliant)	Pkg. Dwg.#	Carrier Type ^[3]	Temp. Range	Summary of Part Differences ^[4]
RAA215300A2GNP#HA0	215300B00	56 Lead, 8.8mm QFN	L56.8x8I	Reel, 1k	-40 to +105°C	PWRON Config: Long Push Button
RAA215300A2GNP#HA1	215300B01	0.0111111 Q1 11				PWRON Config: On/Off Switch
RTKA215300DE0000BU	Evaluation board for RAA215300A2GNP#HA0					
RTKA215300E00000BU Socket board						

- 1. These Pb-free plastic packaged products employ special Pb-free material sets, molding compounds/die attach materials, and 100% matte tin plate plus anneal (e3 termination finish, which is RoHS compliant and compatible with both SnPb and Pb-free soldering operations). Pb-free products are MSL classified at Pb-free peak reflow temperatures that meet or exceed the Pb-free requirements of IPC/JEDEC J-STD-020.
- 2. For Moisture Sensitivity Level (MSL), see the RAA215300 product page. For more information about MSL, see TB363.
- 3. See TB347 for details about reel specifications.
- 4. For a full detailed list of differences between parts, see Part Number Differences.

16. Revision History

Revision	Date	Description			
		Added description for VREFIN pin in the Pin Descriptions table and the Device Specific Layout Guidelines table. Updated Figures 9, 10, 11, 12 in section I2C Write Operation and I2C Read Operation. Added description in section {RESET}. Added description in section Output Discharge.			
1.01	Mar 20, 2023	Added description in section Unused Buck. Added description in section Unused LDOx. Updated VTTREF section. Added a figure and updated the description in section VREFIN UVLO. Updated External VR PGOOD Input section. Minor updates to the register map details table.			
1.00	Sep 28, 2022	Initial release			

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